軍商兩用貨品及技術出口管制清單及一般軍用貨品清單
新、舊版修正對照與翻譯

編列說明

1. 軍商兩用貨品及技術出口管制清單列入第一項，一般軍用貨品清單列入第二項。
2. 本對照表列出下列情況：
   a. 有增/刪語詞，變更標點符號，且意義有所變更者；
   b. 舊版無、新版新增之內容；
   c. 舊版有、新版刪除之內容。
3. 本對照表未列出下列情況，但已於檔案中進行修正，與現行公布英文版本一致：
   a. 英文編輯改變，未改變原有內容意義者；
   b. 排版方式變更，未改變原有內容意義者；
   c. 既有版本的錯字與誤植。

目錄

第一項：軍商兩用貨品及技術出口管制清單修正對照表

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
一般註解	無	增加網址無須翻譯	-	(1)https://www.wassenaar.org/ (2)http://mtcr.info/?lang=fr (3)http://www.nuclearsuppliersgroup.org/index.php?lang=en (4)http://www.australiagroup.net/en/index.html
核能軟體註解	無	核能軟體註解 (本註解優先於任何第0類第D節中之管制) 本清單第0類D節不管制用於已獲得出口許可貨品之安裝、操作、維護(檢查)及修理等最低限度〝目標碼〞之〝軟體〞。 核准管制貨品出口，亦同時授權給該最終使用者安裝、操作、維護(檢查)與修理該貨品所需之最低限度〝目標碼〞。 說明：核能軟體註解未豁免第5類第2部分(〝資訊安全〞)所管制之〝軟體〞。	-	NUCLEAR SOFTWARE NOTE (NSN) (This note overrides any control within section D of Category 0) Section D of Category 0 of this list does not control "software" which is the minimum necessary "object code" for the installation, operation, maintenance (checking) or repair of those items whose export has been authorised. The approval of goods for export also authorises the export to the same end-user of the minimum necessary "object code" for the installation, operation, maintenance (checking) or repair of the goods. Note: The Nuclear Software Note does not release "software" specified in Category 5 - Part 2 ("Information Security").

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
一般軟體註解	一般軟體註解 (本註解優先於任何第 0 類至第 9 類第 D 節中之管制) 本清單第 0 類至第 9 類不管制〝軟體〞具下列任一特性：	一般軟體註解 (本註解優先於任何第 1 類至第 9 類第 D 節中之管制) 本清單第 1 類至第 9 類不管制〝軟體〞具下列任一特性：	GENERAL SOFTWARE NOTE (GSN) (This note overrides any control within section D of Categories 0 to 9.) Categories 0 to 9 of this list do not control "software" which is any of the following:	GENERAL SOFTWARE NOTE (GSN) (This note overrides any control within section D of Categories 1 to 9.) Categories 1 to 9 of this list do not control "software" which is any of the following:
字首集合字與縮寫	無	區域衛星導航系統	-	RNSS/ Regional Navigation Satellite System
	簡易可程式邏輯元件	刪除	SPLD/Simple Programmable Logic Device	-
	無	原子質量單位	-	u
專用術語定義	〝自動目標追蹤〞(第 6 類)	刪除	"Automatic target tracking" (6)	-
	〝碳纖維預製品〞(第 1 類)	刪除	"Carbon fibre preforms" (1)	-
	〝混合〞(第 1 類)	刪除	"Commingled" (1)	-
	〝磨碎〞(第 1 類)	刪除	"Comminution" (1)	-
	〝補償系統〞(第 6 類)主要由非向量感測器與 1 個或以上參考感測器(如向量磁力計)所組成，同時配有可減輕平台上剛體旋轉噪音之軟體。	〝補償系統〞(第 6 類)主要由非向量感測器與 1 個或以上參考感測器(如〝向量磁力計〞)所組成，同時配有可減輕平台上剛體旋轉噪音之軟體。	"Compensation systems" (6) consist of the primary scalar sensor, one or more reference sensors (e.g., vector magnetometers) together with software that permit reduction of rigid body rotation noise of the platform.	"Compensation systems" (6) consist of the primary scalar sensor, one or more reference sensors (e.g., vector "magnetometers") together with software that permit reduction of rigid body rotation noise of the platform.
	〝複合迴轉工作台〞	刪除	"Compound rotary table" (2)	-
	密碼啟用〞(第 5 類)指任何啟動或	〝密碼啟用〞(第 5 類)指任何專門	"Cryptographic activation" (5)	"Cryptographic activation" (5) means any

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	啟用一項目密碼之技術，透過該項目製造商之安全機制實現，該安全機制之單一範圍如後任一者：	為啟動或啟用一項目密碼之技術，透過該項目製造商之機制實現，該安全機制之單一範圍如後任一者：	means any technique that activates or enables cryptographic capability of an item, by means of a secure mechanism implemented by the manufacturer of the item, where this mechanism is uniquely bound to any of the following:	technique that specifically activates or enables cryptographic capability of an item, by means of a mechanism implemented by the manufacturer of the item, where this mechanism is uniquely bound to any of the following:
	〝可變形鏡面〞	刪除	"Deformable mirrors" (6)	-
	〝直接作用液壓成形〞	刪除	"Direct-acting hydraulic pressing" (2)	-
	〝電子操控相位陣列天線〞	刪除	"Electronically steerable phased array antenna" (5 6)	-
	〝飛行控制光學感應器陣列〞	刪除	"Flight control optical sensor array" (7)	-
	〝最佳飛行路徑〞	刪除	"Flight path optimisation" (7)	-
	〝頻率遮罩觸發〞	刪除	"Frequency mask trigger" (3)	-
	〝頻率合成器〞	刪除	"Frequency synthesiser" (3)	-
	〝氣體霧化〞	刪除	"Gas Atomisation" (1)	-
	〝地理分散〞	刪除	"Geographically dispersed" (6)	-
	〝熱均壓緻密化〞	刪除	"Hot isostatic densification" (2)	-
	無	〝交錯式類比－數位轉換器(ADC)〞(第 3 類)係指具有多個 ADC 單元之設備，其可在不同時間內對相同的類比訊號輸入進行	-	"Interleaved Analogue-to-Digital Converter (ADC)" (3) means devices that have multiple ADC units that sample the same analogue input at different times such that when the outputs are

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		採樣，當彙總輸出時，類比輸入被更有效的採樣與以更高採樣率轉換。		aggregated, the analogue input has been effectively sampled and converted at a higher sampling rate.
	說明：參照：〝化學雷射〞；〝超高功率雷射〞；〝連續波雷射〞；〝脈衝雷射〞；〝移轉雷射〞。	說明：參照：〝化學雷射〞；〝連續波雷射〞；〝脈衝雷射〞；〝超高功率雷射〞。	N.B. See also "Chemical laser"; "CW laser"; "Pulsed laser"; "Super High Power Laser"; "Transfer laser".	N.B. See also "Chemical laser"; "CW laser"; "Pulsed laser"; "Super High Power Laser".
	〝資料庫〞	刪除	"Library" (1)	-
	〝主儲存體〞	刪除	"Main storage" (4)	-
	〝機械合金法〞	刪除	"Mechanical Alloying" (1)	-
	〝熔融抽取〞	刪除	"Melt Extraction" (1)	-
	〝熔融紡絲〞	刪除	"Melt Spinning" (1)	-
	無	〝多頻道類比－數位轉換器(ADC)〞(第3類)係指整合超過1個ADC之設備，其設計使每個ADC具有單獨的類比輸入。	-	"Multiple channel Analogue-to-Digital Converter (ADC)" (3) means devices that integrate more than one ADC, designed so that each ADC has a separate analogue input.
	〝類神經電腦〞	刪除	"Neural computer" (4)	-
	〝光學電腦〞	刪除	"Optical computer" (4)	-
	〝電漿霧化〞	刪除	"Plasma atomisation" (1)	-
	〝功率管理〞	刪除	"Power management" (7)	-
	〝預先分離〞(第0、1類)係指為增加同位素濃度之先期處理程序。	〝預先分離〞(第1類)係指任何為增加同位素濃度之先期處理程序。	"Previously separated" (0 1) means the application of any process intended to increase the	"Previously separated" (1) is the application of any process intended to increase the concentration of the controlled isotope.

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			concentration of the controlled isotope.	
	〝主飛行控制〞	刪除	"Primary flight control" (7)	-
	〝即時頻寬〞	刪除	"Real-time bandwidth" (3)	-
	〝旋轉霧化〞	刪除	"Rotary atomisation" (1)	-
	無	〝採樣率〞(第3類)在類比－數位轉換器(ADC)中指1秒時間中類比輸入所量測到之最大採樣數,除超量採樣 ADCs 之外。對於超量採樣 ADCs 而言，〝採樣率〞被視為輸出字速率。〝採樣率〞也被稱為採樣速率，通常以每秒兆採樣數(MSPS)或每秒千兆採樣數(GSPS)，或赫茲(Hz)轉換速率加以說明。	-	"Sample rate" (3) for an Analogue-to-Digital Converter (ADC) means the maximum number of samples that are measured at the analogue input over a period of one second, except for oversampling ADCs. For oversampling ADCs the "sample rate" is taken to be its output word rate. "Sample rate" may also be referred to as sampling rate, usually specified in Mega Samples Per Second (MSPS) or Giga Samples Per Second (GSPS), or conversion rate, usually specified in Hertz (Hz).
	〝穩定時間〞	刪除	"Settling time" (3)	-
	無	〝穩態模式〞(第9類)定義引擎運轉條件,當引擎進氣口處周圍空氣與壓力恆定時，引擎參數如推力/功率、轉速及其他等沒有明顯的波動。	-	"Steady State Mode" (9) defines engine operation conditions, where the engine parameters, such as thrust/power, rpm and others, have no appreciable fluctuations, when the ambient air temperature and pressure at the engine inlet are constant.
	〝噴濺急冷〞	刪除	"Splat Quenching" (1)	-

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		刪除	"Systolic array computer"	-
	無	〝穩定狀態時間〞(第 6 類)(亦被稱為重力儀響應時間)為受平台干擾影響之時間，誘發加速(高頻率雜訊)之降低。	-	"Time-to-steady-state registration" (6) (also referred to as the gravimeter's response time) is the time over which the disturbing effects of platform induced accelerations (high frequency noise) are reduced.
	〝脈動陣列電腦〞	刪除	"Transfer laser" (6)	-
	〝真空霧化〞	刪除	"Vacuum Atomisation" (1)	-
	〝可變幾何機翼〞	刪除	"Variable geometry airfoils" (7)	-
1A002	1A002 〝複合〞結構或積層板，且具下列任一特性： 說明：參照 1A202、9A010 及 9A110。 a. 由 1C010.c.、1C010.d.或 1C010.e.所述之有機〝基質〞與材料構成；或 b. 由一金屬或碳〝基質〞構成，且具下列任一者： 1. 碳〝纖維狀或絲狀材料〞且具下列所有特性： a. 〝比模數〞超過 10.15 × 10^6 m；及 b. 〝比抗拉強度〞超過 17.7 × 10^4 m；或	1A002 〝複合〞結構或積層板，如下： 說明：參照 1A202、9A010 及 9A110。 a. 由以下任一材料構成： 1. 1C010.c.、1C010.d.所述之有機〝基質〞與〝纖維狀或絲狀材料〞；或 2. 1C010.e.所述之預浸體或預製體； b. 由金屬或碳〝基質〞構成，且具下列任一者： 1. 碳且具下列所有特性： a. 〝比模數〞超過 10.15 × 10^6 m；及	1A002 "Composite" structures or laminates, having any of the following: N.B. SEE ALSO 1A202, 9A010 and 9A110 a. Consisting of an organic "matrix" and materials specified in 1C010.c., 1C010.d. or 1C010.e.; or b. Consisting of a metal or carbon "matrix", and any of the following: 1. Carbon "fibrous or filamentary materials" having all of the following: a. A "specific modulus" exceeding	1A002 "Composite" structures or laminates, as follows: N.B. SEE ALSO 1A202, 9A010 and 9A110 a. Made from any of the following: 1. An organic "matrix" and "fibrous or filamentary materials" specified in 1C010.c. or 1C010.d.: or 2. Prepregs or preforms specified in 1C010.e.; b. Made from a metal or carbon "matrix", and any of the following: 1. Carbon "fibrous or filamentary materials" having all of the following: a. A "specific modulus" exceeding 10,15 × 10^6 m; and b. A "specific tensile strength" exceeding 17,7

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	2. 1C010.c.所述之材料。	b. 〝比抗拉強度〞超過 17.7 × 10^4 m；或 2. 1C010.c.所述之材料。	10,15 × 10^6 m; and b. A "specific tensile strength" exceeding 17,7 × 10^4 m; or 2. Materials specified in 1C010.c.	× 10^4 m; or 2. Materials specified in 1C010.c.
1B117	1B117 可在 0 至 13,326 kPa 範圍之真空狀態下進行混合，且其混合槽具有溫度控制性能之批次混合器，且具下列所有特性，及為其特別設計之零件： a. 總體積容量為 110 公升或以上；及 b. 具有至少一個安裝偏離中心之〝混合/揉拌軸〞。 註解：1B117.b.所述之〝混合/捏揉軸〞，並非指粉碎機或刀軸。	1B117 批次混合器具下列所有特性，及特別為其設計之零件： a. 設計或改裝可在 0 至 13,326 kPa 範圍之真空狀態下進行混合； b. 混合槽具有溫度控制能力； c. 體積容量為 110 公升或以上；及 d. 具有至少一個偏離中心安裝之〝混合/揉拌軸〞。 註解：1B117.d.所述之〝混合/捏揉軸〞，並非指粉碎機或刀軸。	1B117 Batch mixers with provision for mixing under vacuum in the range of zero to 13,326 kPa and with temperature control capability of the mixing chamber and having all of the following, and specially designed components therefor: a. A total volumetric capacity of 110 litres or more; and b. At least one 'mixing/kneading shaft' mounted off centre. Note: In 1B117.b. the term 'mixing/kneading shaft' does not refer to deagglomerators or knife-spindles.	1B117 Batch mixers having all of the following, and specially designed components therefor: a. Designed or modified for mixing under vacuum in the range of zero to 13,326 kPa: b. Capable of controlling the temperature of the mixing chamber; c. A total volumetric capacity of 110 litres or more; and d. At least one 'mixing/kneading shaft' mounted off centre. Note: In 1B117.d. the term 'mixing/kneading shaft' does not refer to deagglomerators or knife-spindles.
1B118	1B118 可在 0 至 13,326 kPa 範圍之真空狀態下進行混合，且其混合槽具有溫度控制性能之連續混合器，且具下列任一特性，及特別為其設計之零件：	1B118 連續混合器具下列任一特性，及特別為其設計之零件： a. 設計或改裝可在 0 至 13,326 kPa 範圍之真空狀態下進行混合； b. 混合槽具有溫度控制能力；	1B118 Continuous mixers with provision for mixing under vacuum in the range of zero to 13,326 kPa and with a temperature control capability of the mixing chamber	1B118 Continuous mixers having all of the following, and specially designed components therefor: a. Designed or modified for mixing under vacuum in the range of zero to 13,326 kPa;

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	a. 具有 2 個或以上之混合/揉拌軸；或 b. 具有可振盪之單一旋轉軸，且軸上及混合槽內壁均有揉拌齒/螺栓。	c. 具下列任一者： 1. 具 2 個或以上之混合/揉拌軸；或 2. 具下列全部者： a. 具有可振盪之單一旋轉軸，其有揉拌齒/螺栓；及 b. 混合槽內壁有揉拌齒/螺栓。	and having any of the following, and specially designed components therefor: a. Two or more mixing/kneading shafts; or b. A single rotating shaft which oscillates and having kneading teeth/pins on the shaft as well as inside the casing of the mixing chamber.	b. Capable of controlling the temperature of the mixing chamber; c. any of the following,: 1. Two or more mixing/kneading shafts; or 2. All of the following: a. A single rotating and oscillating shaft with kneading teeth/pins ; and b. Kneading teeth/pins inside the casing of the mixing chamber.
1B228.c	c. 由下列任一材料建構而成： 1.300 系列不銹鋼，具低含硫量，且其沃斯田(austenitic)美國材料試驗學會(ASTM)(或等效標準)之晶粒大小為 5 號或以上者；或 2. 兼具低溫且與氫氣相容之同等材料；及	c. 由下列任一材料建構而成： 1. 國際汽車工程師協會(SAE)之 300 系列不銹鋼，具低含硫量，且其沃斯田(austenitic)美國材料試驗學會(ASTM)(或等效標準)之晶粒大小為 5 或以上者；或 2. 兼具低溫且與氫氣(H2)相容之同等材料；及	c. Constructed of either: 1. Stainless steel of the 300 series with low sulphur content and with an austenitic ASTM (or equivalent standard) grain size number of 5 or greater; or 2. Equivalent materials which are both cryogenic and H 2 -compatible; and	c. Constructed of either: 1. Stainless steel of the Society of Automotive Engineers International (SAE) 300 series with low sulphur content and with an austenitic ASTM (or equivalent standard) grain size number of 5 or greater; or 2. Equivalent materials which are both cryogenic and hydrogen (H 2)-compatible; and
1B229	1B229	刪除	1B229	-
1B234.a	a. 設計為全部含有相當於 2 kg 重 TNT 爆炸威力或以上；及	a. 設計為全部含有相當於 2 公斤重黃色炸藥(三硝基甲苯/TNT)爆炸威力或以上；及	a. Designed to fully contain an explosion equivalent to 2 kg of TNT or greater; and	a. Designed to fully contain an explosion equivalent to 2 kg of trinitrotoluene (TNT) or greater; and
1B235	無	1B235　用於生產氚的組件與零	-	1B235 Target assemblies and components for the

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		件，如下： a. 含有或由鋰-6 同位素製成之組件，特別設計用於透過放射生產氚，包括插入核子反應器； b. 為 1B235.a.所述之組件特別設計之零件。 技術註解： 為用於生產氚的組件所特別設計之零件，可能包括鋰顆粒、氚吸氣劑與特別塗層襯套。		production of tritium as follows: a. Target assemblies made of or containing lithium enriched in the lithium-6 isotope specially designed for the production of tritium through irradiation, including insertion in a nuclear reactor; b. Components specially designed for the target assemblies specified in 1B235.a. Technical Note: Components specially designed for target assemblies for the production of tritium may include lithium pellets, tritium getters, and specially-coated cladding.
1C001	1C001　特別設計用於吸收電磁波，或本質上即為導電性聚合物材料，如下：	1C001　特別設計用於吸收電磁輻射，或本質上即為導電性聚合物材料，如下：	1C001 Materials specially designed for use as absorbers of electromagnetic waves, or intrinsically conductive polymers, as follows:	1C001 Materials specially designed for absorbing electromagnetic radiation, or intrinsically conductive polymers, as follows:
1C001.b	b. 吸收頻率超過 1.5 × 10^{14} Hz，但小於 3.7 × 10^{14} Hz 之材料，且對可見光不具穿透性者；	b. 對可見光而言為不透明之材料，其特別設計用於吸收波長超過 810 nm 但小於 2,000 nm(頻率超過 150 THz 但小於 370 THz)的近紅外線輻射；	b. Materials for absorbing frequencies exceeding 1,5 × 10^{14} Hz but less than 3,7 × 10^{14} Hz and not transparent to visible light;	b. Materials not transparent to visible light and specially designed for absorbing near-infrared radiation having a wavelength exceeding 810 nm but less than 2 000 nm (frequencies exceeding 150 THz but less than 370 THz);
1C002.c.2	2. 在受控制之環境中，以下列任	2. 在受控制之環境中，以下列任	2. Made in a controlled environment	2. Made in a controlled environment by any of the

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	一程序製造： a. 〝真空霧化〞； b. 〝氣體霧化〞； c. 〝旋轉霧化〞； d. 〝噴濺急冷〞； e. 〝熔融紡絲〞及〝磨碎〞； f. 〝熔融抽取〞及〝磨碎〞； g. 〝機械合金法〞；或 h. 〝電漿霧化〞；及	一程序製造： a. ｀真空霧化｀； b. ｀氣體霧化｀； c. ｀旋轉霧化｀； d. ｀噴濺急冷｀； e. ｀熔融紡絲｀及｀磨碎｀； f. ｀熔融抽取｀及｀磨碎｀； g. ｀機械合金法｀；或 h. ｀電漿霧化｀；及	by any of the following processes: a. "Vacuum atomisation"; b. "Gas atomisation"; c. "Rotary atomisation"; d. "Splat quenching"; e. "Melt spinning" and "comminution"; f. "Melt extraction" and "comminution"; g. "Mechanical alloying"; or h. "Plasma atomisation"; and	following processes: a. 'Vacuum atomisation'; b. 'Gas atomisation'; c. 'Rotary atomisation'; d. 'Splat quenching'; e. 'Melt spinning' and 'comminution'; f. 'Melt extraction' and 'comminution'; g. 'Mechanical alloying'; or h. 'Plasma atomisation'; and
1C002.D.3	3. 在受控制之環境中，以下列任一程序製造： a. 〝噴濺急冷〞； b. 〝熔融紡絲〞；或 c. 〝熔融抽取〞。	3. 在受控制之環境中，以下列任一程序製造： a. ｀噴濺急冷｀； b. ｀熔融紡絲｀；或 c. ｀熔融抽取｀。	3. Produced in a controlled environment by any of the following: a. "Splat quenching"; b. "Melt spinning"; or c. "Melt extraction".	3. Produced in a controlled environment by any of the following: a. 'Splat quenching'; b. 'Melt spinning'; or c. 'Melt extraction'.
1C002 技術註解	無	技術註解： 1. ｀真空霧化｀係指迅速釋放溶解之氣體，使其暴露於真空裝置中，而將熔融流動之金屬變為粒狀熔滴直徑 500 微米或以下之處理程序。 2. ｀氣體霧化｀係指以高壓氣流	-	Technical Notes: 1. 'Vacuum atomisation' is a process to reduce a molten stream of metal to droplets of a diameter of 500 μm or less by the rapid evolution of a dissolved gas upon exposure to a vacuum. 2. 'Gas atomisation' is a process to reduce a molten stream of metal alloy to droplets of 500

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		將熔流之金屬合金變為微粒直徑500微米或以下之處理程序。 3.〝旋轉霧化〞係指以離心力將一束或一池液態金屬減為粒狀熔滴直徑500微米或以下之處理程序。 4.〝噴濺急冷〞係指將金屬熔流衝擊冷凍塊而〝快速凝固〞使形成片狀產品之處理程序。 5.〝熔融紡絲〞係指以金屬熔液流衝擊旋轉之冷凍塊，形成片狀、帶狀或棒狀產物之〝快速凝固〞處理程序。 6.〝磨碎〞指利用壓碎或研磨方式將物質縮小成為粒子之處理程序。 7.〝熔融抽取〞係指〝快速凝固〞及抽取帶狀合金產物之處理程序，將一小截冷凍〞塊旋轉插入熔融金屬合金槽以抽取帶狀合金。 8.〝機械合金法〞係指由機械衝擊方式將元素及主體合金粉末，經過結合、破碎及再結合之合金處理程序。藉由添加適當的粉末，非金		μm diameter or less by a high pressure gas stream. 3.'Rotary atomisation' is a process to reduce a stream or pool of molten metal to droplets to a diameter of 500 μm or less by centrifugal force. 4.'Splat quenching' is a process to 'solidify rapidly' a molten metal stream impinging upon a chilled block, forming a flake-like product. 5.'Melt spinning' is a process to 'solidify rapidly' a molten metal stream impinging upon a rotating chilled block, forming a flake, ribbon or rod-like product. 6.'Comminution' is a process to reduce a material to particles by crushing or grinding. 7.'Melt extraction' is a process to 'solidify rapidly' and extract a ribbon-like alloy product by the insertion of a short segment of a rotating chilled block into a bath of a molten metal alloy. 8.'Mechanical alloying' is an alloying process resulting from the bonding, fracturing and rebonding of elemental and master alloy powders by mechanical impact. Non-metallic particles may be incorporated in the alloy by addition of the

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		屬粒子可結合至合金中。 9. ｀電漿原子化｀係指在惰性氣體環境中利用電漿炬將熔融或固態金屬減低成為500μm或以下之微滴之處理程序。 10. ｀快速凝固｀係指在冷卻率超過1,000K/s下，使熔態物質凝固之處理程序。		appropriate powders. 9. 'Plasma atomisation' is a process to reduce a molten stream or solid metal to droplets of 500 μm diameter or less, using plasma torches in an inert gas environment. 10. 'Solidify rapidly' is a process involving the solidification of molten material at cooling rates exceeding 1 000 K/sec.
1C010.d	d. 〝纖維或絲狀材料〞： 1. 由下列任一者組成： a. 1C008.a.所述之聚醚醯亞胺；或 b. 1C008.d.至1C008.f.所述之材料；或； 2. 由1C010.d.1.a.或1C010.d.1.b.所述之材料所組成，且與1C010.a.、1C010.b.或1C010.c.所述之其他纖維〝混合〞者；	d. 〝纖維或絲狀材料〞： a. 1C008.a.所述之聚醚醯亞胺；或 b. 1C008.d.至1C008.f.所述之材料；或； 2. 由1C010.d.1.a.或1C010.d.1.b.所述之材料所組成，且與1C010.a.、1C010.b.或1C010.c.所述之其他纖維｀混合｀者； 技術註解： 〝混合〞指熱塑性纖維絲與強化纖維絲之混合，以生產完全纖維型態之強化纖維〝基質〞混合物。	d. "Fibrous or filamentary materials", having any of the following: 1. Composed of any of the following: a. Polyetherimides specified in 1C008.a.; or b. Materials specified in 1C008.d. to 1C008.f.; or 2. Composed of materials specified in 1C010.d.1.a. or 1C010.d.1.b. and "commingled" with other fibres specified in 1C010.a., 1C010.b. or 1C010.c.;	d. "Fibrous or filamentary materials", having any of the following: 1. Composed of any of the following: a. Polyetherimides specified in 1C008.a.; or b. Materials specified in 1C008.d. to 1C008.f.; or 2. Composed of materials specified in 1C010.d.1.a. or 1C010.d.1.b. and 'commingled' with other fibres specified in 1C010.a., 1C010.b. or 1C010.c.; Technical Note: 'Commingled' is filament to filament blending of thermoplastic fibres and reinforcement fibres in order to produce a fibre reinforcement "matrix" mix in total fibre form.
1C010.e	e. 完全或部分以樹脂浸漬或以瀝	e. 完全或部分以樹脂浸漬或以瀝	e. Fully or partially	e. Fully or partially resin-impregnated or

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	青浸漬之〝纖維或絲狀材料〞(預浸體)、鍍金屬或鍍碳之〝纖維狀或絲狀材料〞 (預製品)以及〝碳纖維預製品〞，符合下列所有條件：	青浸漬之〝纖維或絲狀材料〞(預浸體)、鍍金屬或鍍碳之〝纖維狀或絲狀材料〞 (預製品)以及〝碳纖維預製品〞，符合下列所有條件：	resin-impregnated or pitch-impregnated "fibrous or filamentary materials" (prepregs), metal or carbon-coated "fibrous or filamentary materials" (preforms) or "carbon fibre preforms", having all of the following:	pitch-impregnated "fibrous or filamentary materials" (prepregs), metal or carbon-coated "fibrous or filamentary materials" (preforms) or 'carbon fibre preforms', having all of the following:
1C010.e.2.註解1	註解1：鍍金屬或鍍碳之〝纖維狀或絲狀材料〞(預製品)和非樹脂或瀝青浸漬之〝碳纖維預製品〞，由1C010.a.、1C010.b.及1C010.c.所述之〝纖維狀或絲狀材料〞說明；	註解1：鍍金屬或鍍碳之〝纖維狀或絲狀材料〞(預製品)和非樹脂或瀝青浸漬之〝碳纖維預製品〞，由1C010.a.、1C010.b.及1C010.c.所述之〝纖維狀或絲狀材料〞說明；	Note 1: Metal or carbon-coated "fibrous or filamentary materials" (preforms) or "carbon fibre preforms", not impregnated with resin or pitch, are specified by "fibrous or filamentary materials" in 1C010.a., 1C010.b. or 1C010.c.	Note 1: Metal or carbon-coated "fibrous or filamentary materials" (preforms) or 'carbon fibre preforms', not impregnated with resin or pitch, are specified by "fibrous or filamentary materials" in 1C010.a., 1C010.b. or 1C010.c.
1C010.e.技術註解	技術註解： 1C010.e.所述材料的〝動態機械性分析玻璃轉換溫度(DMA Tg)〞，需採用 ASTM D 7028-07 所述方法，或等效國家標準，使用乾燥測試樣本進行測定。若為熱固性材料，該乾燥測試樣本之固化程度至少達到 ASTM E 2160-04 或等效國家標準所定義之 90%。	技術註解： 1.〝碳纖維預製品〞指在〝基質〞導入形成〝複合材料〞之前，佈或未塗佈之纖維為了組成一個架構之有序整齊排列。 2.1C010.e.所述材料的〝動態機械性分析玻璃轉換溫度(DMA Tg)〞，需採用 ASTM D 7028-07 所述方法，或等效國家標準，使用	Technical Note: The 'Dynamic Mechanical Analysis glass transition temperature (DMA T g)' for materials specified by 1C010.e. is determined using the method described in ASTM D 7028-07, or equivalent national standard, on a dry test specimen. In the case of thermoset materials, degree of	Technical Notes: 1. 'Carbon fibre preforms' are an ordered arrangement of uncoated or coated fibres intended to constitute a framework of a part before the "matrix" is introduced to form a "composite". 2. The 'Dynamic Mechanical Analysis glass transition temperature (DMA T g)' for materials specified in 1C010.e. is determined using the

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		乾燥測試樣本進行測定。若為熱固性材料，該乾燥測試樣本之固化程度至少達到 ASTM E 2160-04 或等效國家標準所定義之 90%。	cure of a dry test specimen shall be a minimum of 90% as defined by ASTM E 2160-04 or equivalent national standard.	method described in ASTM D 7028-07, or equivalent national standard, on a dry test specimen. In the case of thermoset materials, degree of cure of a dry test specimen shall be a minimum of 90 % as defined by ASTM E 2160-04 or equivalent national standard.
1C111.a.4.c	c. N,N 二烯丙基聯胺(CAS 5164-11-4)；	c. N,N-二烯丙基聯胺(CAS 5164-11-4)；	c. N,N diallylhydrazine (CAS 5164-11-4);	c. N,N-Diallylhydrazine (CAS 5164-11-4);
1C111.c.7	無	7. 除軍用貨品管制以外之 4,5 二疊氮甲基-2-甲基-1,2,3-三唑(iso-DAMTR)；	-	7. 4,5 diazidomethyl-2-methyl-1,2,3-triazole (iso-DAMTR), other than that specified in the Military Goods Controls.
1C111.d	無	d. 除軍用貨品管制以外之「凝膠推進劑」，其專門配置用於「飛彈」。 技術註解： 1. 1C111.d.中之「凝膠推進劑」指燃料或氧化劑配方使用凝膠劑，如矽酸鹽、高嶺土(黏土)、碳或任何聚合型凝膠。 2. 在 1C111.d.所定義之「飛彈」，是指航程或射程超過 300 km 的完整火箭系統及無人飛行載具系統。	-	d. 'Gel propellants', other than that specified in the Military Goods Controls, specifically formulated for use in 'missiles'. Technical Notes: 1. In 1C111.d. a 'gel propellant' is a fuel or oxidiser formulation using a gellant such as silicates, kaolin (clay), carbon or any polymeric gellant. 2. In 1C111.d. a 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km.
1C118.a	a. 具下列所有特性：	a. 具下列所有特性：	a. Having all of the following	a. Having all of the following characteristics:

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	1. 含鉻重量百分比為 17.0％至 23.0％，及含鎳重量百分比為 4.5％至 7.0％； 2. 含鈦重量百分比為 0.10％以上；及 3. 鐵素體-奧氏體鋼微結構(亦稱雙相微結構)，其中含奧氏體鋼之體積百分比至少為 10％(依 ASTM 標準 E-1181-87 或等效國家標準)；及	1. 含鉻重量百分比為 17%至 23.0％，及含鎳重量百分比為 4.5％至 7.0％； 2. 含鈦重量百分比為 0.10％以上；及 3. 鐵素體-奧氏體鋼微結構(亦稱雙相微結構)，其中體積百分比至少為 10％(依 ASTM 標準 E-1181-87 或等效國家標準)為奧氏體鋼之；及	characteristics: 1. Containing 17,0 - 23,0 weight percent chromium and 4,5 - 7,0 weight percent nickel; 2. Having a titanium content of greater than 0,10 weight percent; and 3. A ferritic-austenitic microstructure (also referred to as a two-phase microstructure) of which at least 10 percent is austenite by volume (according to ASTM E-1181-87 or national equivalents); and	1. Containing 17,0 - 23,0 % by weight of chromium and 4,5 - 7,0 % by weight of nickel; 2. Having a titanium content of greater than 0,10 % by weight; and 3. A ferritic-austenitic microstructure (also referred to as a two-phase microstructure) of which at least 10 % by volume (according to ASTM E-1181-87 or national equivalents) is austenite; and
1C350.64	無	64. 二乙胺(109-89-7)；	-	64. Diethylamine (109-89-7);
1C350.65	無	65. N,N-二異丙基胺基乙硫醇酸鹽(41480-75-5)。	-	65. N,N-Diisopropylaminoethanethiol hydrochloride (41480-75-5).
1C350 註解	註解 1：對出口至〝聯合國禁止化學武器公約之非會員國〞，1C350 不管制含有 1 種或以上 1C350.1、.3、.5、.11、.12、.13、.17、.18、 ..21、.22、.26、.27、.28、.31、.32、.33、.34、.35、.36、.54、.55、.56、.57 及.63 所述	註解 1：對出口至〝聯合國禁止化學武器公約之非會員國〞，1C350 不管制含有 1 種或以上 1C350.1、.3、.5、.11、.12、.13、.17、.18、 ..21、.22、.26、.27、.28、.31、.32、.33、.34、.35、.36、.54、.55、.56、.57、.63 及.65	Note 1: For exports to "States not Party to the Chemical Weapons Convention", 1C350 does not control "chemical mixtures" containing one or more of the chemicals specified in entries 1C350.1, .3, .5, .11, .12, .13,	Note 1: For exports to "States not Party to the Chemical Weapons Convention", 1C350 does not control "chemical mixtures" containing one or more of the chemicals specified in entries 1C350.1, .3, .5, .11, .12, .13, .17, .18, .21, .22, .26, .27, .28, .31, .32, .33, .34, .35, .36, .54, .55, .56, .57, 63 and .65 in which

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	化學品之〝化學品混合物〞，惟化學品混合物中所含上列管制化學品個別成分之重量百分比不超過10％。 註解2：對出口至〝聯合國禁止化學武器公約之會員國〞，1C350不管制含有1種或以上1C350.1、.3、.5、.11、.12、.13、.17、.18、.21、 ..22、.26、.27、.28、.31、.32、.33、.34、.35、.36、.54、.55、.56、.57及.63所述化學品之〝化學品混合物〞，惟化學品混合物中所含上列管制化學品個別成分之重量百分比不超過30％。	所述化學品之〝化學品混合物〞，惟化學品混合物中所含上列管制化學品個別成分之重量百分比不超過10％。 註解2：對出口至〝聯合國禁止化學武器公約之會員國〞，1C350不管制含有1種或以上1C350.1、.3、.5、.11、.12、.13、.17、.18、.21、 .22、.26、.27、.28、.31、.32、.33、.34、.35、.36、.54、.55、.56、.57、.63及.65所述化學品之〝化學品混合物〞，惟化學品混合物中所含上列管制化學品個別成分之重量百分比不超過30％。	.17, .18, .21, .22, .26, .27, .28, .31, .32, .33, .34, .35, .36, .54, .55, .56, .57 and .63 in which no individually specified chemical constitutes more than 10% by the weight of the mixture. Note 2: For exports to "States Party to the Chemical Weapons Convention", 1C350 does not control "chemical mixtures" containing one or more of the chemicals specified in entries 1C350.1, .3, .5, .11, .12, .13, .17, .18, .21, .22, .26, .27, .28, .31, .32, .33, .34, .35, .36, .54, .55, .56, .57, .63 and .65 in which no individually specified chemical constitutes more than 30% by the weight of the mixture.	no individually specified chemical constitutes more than 10 % by the weight of the mixture. Note 2: For exports to "States Party to the Chemical Weapons Convention", 1C350 does not control "chemical mixtures" containing one or more of the chemicals specified in entries 1C350.1, .3, .5, .11, .12, .13, .17, .18, .21, .22, .26, .27, .28, .31, .32, .33, .34, .35, .36, .54, .55, .56, .57, .63 and .65 in which no individually specified chemical constitutes more than 30 % by the weight of the mixture.
1C351.c.19 註解	無	註解：志賀毒素大腸桿菌(STEC)別名包括腸出血性大腸桿菌(EHEC)、產志賀毒素大腸桿菌(VTEC)或志賀樣毒素大腸桿菌(VTEC)。	-	Note: Shiga toxin producing Escherichia coli (STEC) includes inter alia enterohaemorrhagic E. coli (EHEC), verotoxin producing E. coli (VTEC) or verocytotoxin producing E. coli (VTEC).

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
1C352	1C352	刪除	1C352	-
1C353	1C353 遺傳因子及經基因改造之有機體，如下： a. 經基因改造之有機體或遺傳因子，含有與致病性有關之核酸序列，且該致病性係源自於1C351.a.、1C351.c.、1C351.e.或1C354所述之有機體； b. 經基因改造之有機體或遺傳因子，含1C351.d.所述〝毒素〞或其〝毒素次單位〞之核酸序列編碼。 技術註解： 1. 基因改造生物體，包括遺傳物質(核酸序列)已被改變之生物體，其非通過天然存在的方式如交配或自然重組，及包括全部或部分由人為產生者； 1C353 (續) 2. 遺傳因子包括染色體、基因體組、質體、轉位子及載體，不論其為經改造或未經改造者，或全部或部分化學合成者。 3. 與1C351.a.、1C351.c.、1C351.e.或1C354所述微生物之致病性有	1C353 ｀遺傳因子＇及經｀基因改造之有機體＇，如下： a. 任何｀基因改造之有機體＇含有，或｀遺傳因子＇為其編碼下列任一者： 1. 1C351.a. 或1C354.a.中任何病毒之基因。 2. 1C351.c. 或1C354.b.中之任何細菌之基因，或1C351.e.或1C354.c.中任何真菌之基因，其具下列任一特性： a. 自身或通過轉譯或轉譯產品重現對人類、動物或植物健康的顯著傷害，或； b. 能夠｀賦予或增強致病性＇，或 3. 任何1C351.d.中之〝毒素〞或其〝毒素次單位〞。 技術註解： 1. ｀基因改造之有機體＇包括通過特意之分子操作產生或改變核酸序列的有機體。 2. ｀遺傳因子＇包括染色體，基	1C353 Genetic elements and genetically modified organisms, as follows: a. Genetically modified organisms or genetic elements that contain nucleic acid sequences associated with pathogenicity of organisms specified in 1C351.a., 1C351.c., 1C351.e. or 1C354; b. Genetically modified organisms or genetic elements that contain nucleic acid sequences coding for any of the "toxins" specified in 1C351.d. or "sub-units of toxins" thereof. Technical Notes: 1. Genetically-modified organisms includes organisms in which the genetic material (nucleic acid sequences) has been altered in a way that does not occur naturally by mating and/or natural recombination, and encompasses	1C353 'Genetic elements' and 'genetically-modified organisms', as follows: a. Any 'genetically-modified organism' which contains, or 'genetic element' that codes for, any of the following: 1. Any gene or genes specific to any virusspecified in 1C351.a. or 1C354.a. 2. Any gene or genes specific to bacterium specified in 1C351.c. or 1C354.b. or fungus specified in 1C351.e. or 1C354.c., and which is any of the following: a. In itself or through its transcribed or translated products represents a significant hazard to human, animal or plant health, or b. Could 'endow or enhance pathogenicity', or 3. Any “toxins” specified in 1C351.d. or "sub-units of toxins" therefor. Technical Notes: 1. 'Genetically-modified organisms' include organisms in which the nucleic acid sequences have been created or altered by deliberate molecular manipulation. 2. 'Genetic elements' include inter alia

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	關核酸序列，係指清單所列〝微生物〞之特定序列，而該序列： a. 本身或透過其轉錄或轉譯之產品對人類、動物或植物健康會構成顯著危害；或 b. 已知可增強受管制微生物、以嵌入或其他方式與受管制微生物結合之其他有機體之能力，以致對人類、動物或植物健康造成嚴重損害。 註解:除類志賀毒素或其子單位之核酸序列外，1C353 不管制與腸出血性大腸桿菌、O157 血清型及其他產生類志賀毒素之血清型之致病性有關之核酸序列。	因組，質體，轉座子，載體和含有可修復的核酸片段的非活化有機體，無論其經基因改造或是未改造，或是全部或部分由化學合成。就控制遺傳因子目的而言，由非活化有機體而來的核酸、病毒或樣品，若非活化與製備材料為預期或已知可促進核酸的分離，純化，擴增，檢測或鑑定，則可認定其為可回收。 3. ｀賦予或增強致病性´之定義為插入或整合核酸序列可能刻意引發有機物受體疾病或死亡的能力。其可能包括以下方面的轉變：病毒性、傳播性、穩定性、感染途徑、寄主範圍、再現性、逃避或抑制宿主免疫力之能力，以及對於醫學防疫措施或檢測的抵抗力。 註解：1C353 不管制血清型志賀毒素大腸桿菌 O26、O45、O103、O104、O111、O121、O145、O157，以及其他與腸出血性大腸桿菌、O157 血清型及其他產生類志賀毒素之血清型之致病性有關之核酸	those produced artificially in whole or in part. 2. Genetic elements include inter alia chromosomes, genomes, plasmids, transposons, and vectors whether genetically modified or unmodified, or chemically synthesized in whole or in part. 3. Nucleic acid sequences associated with the pathogenicity of any of the "microorganisms" specified in 1C351.a., 1C351.c., 1C351.e. or 1C354 means any sequence specific to the specified "microorganism" that: a. In itself or through its transcribed or translated products represents a significant hazard to human, animal or plant health; or b. Is known to enhance the ability of a specified "microorganism", or any other organism into which it may be inserted or otherwise integrated, to cause serious harm	chromosomes, genomes, plasmids, transposons, vectors and inactivated organisms containing recoverable nucleic acid fragments, whether genetically modified or unmodified, or chemically synthesized in whole or in part. For the purposes of the genetic elements control, nucleic acids from an inactivated organism, virus, or sample are considered recoverable if the inactivation and preparation of the material is intended or known to facilitate isolation, purification, amplification, detection, or identification of nucleic acids. 3. 'Endow or enhance pathogenicity' is defined as when the insertion or integration of the nucleic acid sequence or sequences is/are likely to enable or increase a recipient organism' sability to be used to deliberately cause disease or death. This might include alterations to, inter alia: virulence, transmissibility, stability, route of infection, host range, reproducibility, ability to evade or suppress host immunity, resistance to medical countermeasures, or detectability. Note: 1C353 does not control nucleic acid

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		序列。	to humans, animals or plant health. Note: 1C353 does not control nucleic acid sequences associated with the pathogenicity of enterohaemorrhagic Escherichia coli, serotype 0157 and other verotoxin producing strains, other than those coding for the verotoxin, or for its sub-units.	sequences of shiga toxin producing Escherichia coli of serogroups 026, 045, 0103, 0104, 0111, 0121, 0145, 0157, and other shiga toxin producing serogroups, other than those genetic elements coding forshiga toxin, or for its subunits.
1C.450.b.6	6.N,N-二烷基[甲基、乙基或丙基(正構或異構)]胺基乙硫醇及其質子化鹽類，但 1C350 所述之 N,N-二異丙基-β-胺基乙硫醇除外；	6.N,N-二烷基[甲基、乙基或丙基(正構或異構)]胺基乙硫醇及其質子化鹽類，但 1C350 所述之 N,N-二異丙基-β-胺基乙硫醇(5842-07-9)與 N,N-二異丙基胺基乙硫醇酸鹽(41480-75-5)除外；	6. N,N-Dialkyl [methyl, ethyl or propyl (normal or iso)] aminoethane-2-thiols and corresponding protonated salts, other than N,N-Diisopropyl-(beta)-aminoethane thiol which is specified in 1C350;	6. N,N-Dialkyl [methyl, ethyl or propyl (normal or iso)] aminoethane-2-thiols and corresponding protonated salts, other than N,N-Diisopropyl-(beta)-aminoethane thiol (5842-07-9) and N,N-Diisopropylaminoethanethiol hydrochloride (41480-75-5) which are specified in 1C350;
2A001 註解	註解：2A001 不管制經製造商依 ISO 3290 標示之公差為等級 5 或較次級之滾珠。	註解：2A001 不管制經製造商依 ISO 3290 標示之公差為等級 5(或其他等效國家標準)，或較次級之滾珠。	Note: 2A001 does not control balls with tolerances specified by the manufacturer in accordance with ISO 3290 as grade 5 or worse.	Note: 2A001 does not control balls with tolerances specified by the manufacturer in accordance with ISO 3290 as grade 5 (or national equivalents) or worse.
2B001.a 註解 2	註解 2：2B001.a. 不管制僅限棒材直通進料加工，其可加工之棒材最大直徑小於或等於 42 mm，且不	註解 2：2B001.a. 不管制僅限棒材直通進料加工，其可加工之棒材最大直徑小於或等於 42 mm，且不	Note 2: 2B001.a. does not control bar machines (Swissturn), limited to machining only bar feed thru, if	Note 2: 2B001.a. does not control bar machines (Swissturn), limited to machining only bar feed thru, if maximum bar diameter is equal to or less

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	具加裝夾頭能之走心式車床(Swissturn)。此類機器可能具有加工零件直徑小於 42 mm 之鑽孔及/或銑削功能。	具加裝夾頭能之走心式車床(Swissturn)。此類機器可能具有加工零件直徑小於 42 mm 之鑽孔或銑削功能。	maximum bar diameter is equal to or less than 42 mm and there is no capability of mounting chucks. Machines may have drilling and/or milling capabilities for machining parts with diameters less than 42 mm.	than 42 mm and there is no capability of mounting chucks. Machines may have drilling or milling capabilities for machining parts with diameters less than 42 mm.
2B001.c.1.b	b.3 個或 3 個以上之軸可同時協調進行〝輪廓控制〞；或	b.3 個或 4 個軸可同時協調進行〝輪廓控制〞；或	b. Three or more axes which can be coordinated simultaneously for "contouring control"; or	b. Three or four axes which can be coordinated simultaneously for "contouring control"; or
2B006	2B006 尺度檢驗或測量系統、設備與〝電子組件〞，如下： a. 電腦控制或〝數值控制〞之座標測量機具(CMM)，依據 ISO 10360-2 (2009)標準測試，在該機具操作範圍內之任何一點進行測試時(亦即在軸的長度以內)，其 3 維(體積)最大可容許長度量測誤差(E0,MPE)等於或小於(優於)(1.7＋L/1,000) μm(L 係以 mm 為單位之可量測長度)； 技術註解： 製造商規格上所訂定最精確座標測量機具(CMM)組態（如下列項	2B006 尺度檢驗或測量系統、設備、定為回饋單元及〝電子組件〞，如下： a. 電腦控制或〝數值控制〞之座標測量機具(CMM)，依據 ISO 10360-2:2009 標準測試，在該機具操作範圍內之任何一點進行測試時(亦即在軸的長度以內)，其 3 維(體積)最大可容許長度量測誤差(E0,MPE)等於或小於(優於)(1.7＋L/1,000) μm(L 係以 mm 為單位之可量測長度)； 技術註解： 製造商規格上所訂定最精確座標	2B006 Dimensional inspection or measuring systems, equipment and "electronic assemblies", as follows: a. Computer controlled or "numerically controlled" Coordinate Measuring Machines (CMM), having a three dimensional (volumetric) maximum permissible error of length measurement (E 0,MPE) at any point within the operating range of the machine (i.e., within the length of axes) equal to or less (better) than (1,7	2B006 Dimensional inspection or measuring systems, equipment, position feedback units and "electronic assemblies", as follows: a. Computer controlled or "numerical controlled" Coordinate Measuring Machines (CMM), having a three dimensional (volumetric) maximum permissible error of length measurement (E 0,MPE) at any point within the operating range of the machine (i.e., within the length of axes) equal to or less (better) than (1,7 + L/1 000) μm (L is the measured length in mm), according to ISO 10360-2:2009; Technical Note: The E 0,MPE of the most accurate configuration

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	目之最佳者：探針、針頭長度、運動參數及環境），並具有〝所有可補償機制〞者，其最大可容許長度量測誤差(E0,MPE)須達到1.7+L/1,000 μm之門檻。 說明：參照2B206。 b. 直線位移及角位移測量儀器，如下所列： 1. 具下列任一特性之〝直線位移〞測量儀器： 註解：內含有〝雷射〞之干涉儀與光編碼器位移測量系統僅由2B006.b.1.c.與2B206.c.管制。 技術註解： 2B006.b.1.所述之〝直線位移〞係指測量探針和被測量物之間距離之變動。 a. 量測範圍在0.2 mm以內時，〝解析度〞等於或小於(優於)0.2 μm之非接觸式測量系統； b. 具下列所有特性之線性電壓差動轉換器(LVDT)系統： 1. 具有下列任一者： a. LVDTs其〝全部作業範圍〞至	測量機具(CMM)組態（如下列項目之最佳者：探針、針頭長度、運動參數及環境），並具有〝所有可補償機制〞者，其最大可容許長度量測誤差(E0,MPE)須達到1.7+L/1,000 μm之門檻。 說明：參照2B206。 b. 線性位移測量儀器或系統、線性定位回饋單元及〝電子組件〞，如下： 註解：內含有〝雷射〞之干涉儀與光編碼器位移測量系統僅由2B006.b.3.與2B206.c.管制。 1. 量測範圍達到0.2 mm時，〝解析度〞等於或小於(優於)0.2 μm之〝非接觸式測量系統〞； 技術註解： 2B006.b.1.所述之〝非接觸式測量系統〞，其設計用於測量探針或被測量物在運動時，兩者沿著單一向量之間的距離。 2. 總〝準確度(或稱〝精度〞)〞小於(優於)(800＋(600 × L/1,000)) nm(L等於以mm為單位之可量測	+ L/1 000) μm (L is the measured length in mm), according to ISO 10360-2 (2009); Technical Note: The E 0,MPE of the most accurate configuration of the CMM specified by the manufacturer (e.g., best of the following: probe, stylus length, motion parameters, environment) and with "all compensations available" shall be compared to the 1,7 + L/1 000 μm threshold. N.B. SEE ALSO 2B206. b. Linear and angular displacement measuring instruments, as follows: 1. 'Linear displacement' measuring instruments having any of the following: Note: Interferometer and optical-encoder displacement measuring systems containing a "laser" are only controlled in 2B006.b.1.c. and 2B206.c.	of the CMM specified by the manufacturer (e.g., best of the following: probe, stylus length, motion parameters, environment) and with "all compensations available" shall be compared to the 1,7+L/1 000 μm threshold. N.B. SEE ALSO 2B206. b. Linear displacement measuring instruments or systems, linear position feedback units, and "electronic assemblies", as follows: Note: Interferometer and optical-encoder measuring systems containing a "laser" are only specified in 2B006.b.3 and 2B206.c. 1. 'Non-contact type measuring systems' with a "resolution" equal to or less (better) than 0,2 μm within a measuring range up to 0,2 mm; Technical Note: For the purposes of 2B006.b.1.'non-contact type measuring systems' are designed to measure the distance between the probe and measured object along a single vector, where the probe or measured object is in motion. 2. Linear position feedback units specially designed for machine tools and having an overall "accuracy" less (better) than (800 + (600 × L/1

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	多且包含±5 mm 時，量測 0 至｀全部作業範圍´，其〝線性度〞等於或小於(優於)0.1 %；或 b. LVDTs 其｀全部作業範圍´大於±5 mm 時，量測 0 至 5 mm，其〝線性度〞等於或小於(優於)0.1 %；及 2. 在標準周圍環境測試室溫±1 K 下，每日之漂移等於或小於(優於) 0.1%； 技術註解： 就 2B006.b.1.b.目的，｀全部作業範圍´為 LVDT 全部可能之直線位移的一半。舉例來說，LVDTs 其｀全部作業範圍´至多且包含±5 mm 時，能量測之全部可能直線位移為 10 mm。 2B006 (續) c. 如下之測量系統： 1. 含有一〝雷射〞；及 2. 整個量測範圍內之〝解析度〞為 0.2 nm 或以下(較優)；及 3.在 20 ±0.01 ℃溫度下測量 30 秒，經補償空氣折射率後，在量測	長度)之線性定位回饋單元； 3. 測量系統具下列全部特性： a. 含有一〝雷射〞； b. 整個量測範圍內之〝解析度〞為 0.2 nm 或以下(優於)；及 c.在 20 ±0.01 ℃溫度下測量 30 秒，經補償空氣折射率後，在量測範圍內的任何一點，能實現〝量測不準度〞等於或小於(優於)(1.6 + L/2,000) nm (L 係以 mm 為單位測得之長度)；或 4. 為提供 2B006.b.3.所列系統回饋能力而特別設計之〝電子組件〞； c. 特別為機械工具或角度位移測量儀器設計之旋轉定位回饋單元，具有角度位置〝準確度(或稱〝精度〞)〞小於(優於) 0.9 arcsec 者； 註解：2B006.c.不管制光學儀器，如自動準直儀使用準直光(例如〝雷射〞光)用於偵測鏡面角度位移。 d. 藉由測量光散射以測量表面粗	Technical Note: For the purpose of 2B006.b.1. 'linear displacement' means the change of distance between the measuring probe and the measured object. a. Non-contact type measuring systems with a "resolution" equal to or less (better) than 0,2 μm within a measuring range up to 0,2 mm; b. Linear Variable Differential Transformer (LVDT) systems having all of the following: 1. Having any of the following: a. "Linearity" equal to or less (better) than 0,1 % measured from 0 to the 'full operating range', for LVDTs with a 'full operating range' up to and including ± 5 mm; or b. "Linearity" equal to or less (better) than 0,1 % measured from 0 to 5 mm for LVDTs with a 'full	000)) nm (L equals effective length in mm); 3. Measuring systems having all of the following: a. Containing a "laser"; b. A "resolution" over their full scale of 0,200 nm or less (better); and c. Capable of achieving a "measurement uncertainty" equal to or less (better) than (1,6 + L/2 000) nm (L is the measured length in mm) at any point within a measuring range, when compensated for the refractive index of air and measured over a period of 30 seconds at a temperature of 20± 0,01 °C; or 4. "Electronic assemblies" specially designed to provide feedback capability in systems specified in 2B006.b.3.; c. Rotary position feedback units specially designed for machine tools or angular displacement measuring instruments, having an angular position "accuracy" equal to or less (better) than 0,9 second of arc; Note: 2B006.c. does not control optical instruments, such as autocollimators, using collimated light (e.g. "laser" light) to detect angular displacement of a mirror.

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	範圍內的任何一點，能實現〝量測不準度〞等於或小於(優於)(1.6 + L/2,000) nm (L 係以 mm 為單位測得之長度)；或 d. 為提供 2B006.b.1.c.所列系統回授能力而特別設計之〝電子組件〞； 註解：2B006.b.1.不管制測量干涉儀系統，其具有不使用回授技術之自動控制系統，並利用〝雷射〞以測量工具機、尺度檢驗機具或類似設備之滑動誤差。 2. 角度位置〝準確度(或稱〝精度〞)〞等於或小於(優於)0.00025° 之角位移測量儀器； 註解：2B006.b.2.不管制如自動準直儀之光學儀器，該儀器乃利用準直光(如〝雷射〞光)偵測鏡子之角位移。 c. 藉由測量不同角度之光散射以量測表面粗糙度(包括表面缺陷) ，且其靈敏度為 0.5nm 或以下(更優)者。 註解：2B006 包含除 2B001 管制	糙度(包括表面缺陷) ，其靈敏度為 0.5nm 或以下(優於)者。 註解：2B006 包含除 2B001 管制外之可用作測量機具之工具機，其規格如符合或超過測量機具功能所列之標準，即受管制。	operating range' greater than ± 5 mm; and 2. Drift equal to or less (better) than 0,1 % per day at a standard ambient test room temperature ±1 K; Technical Note: For the purposes of 2B006.b.1.b., 'full operating range' is half of the total possible linear displacement of the LVDT. For example, LVDTs with a 'full operating range' up to and including ± 5 mm can measure a total possible linear displacement of 10 mm. c. Measuring systems having all of the following: 1. Containing a "laser"; 2. A "resolution" over their full scale of 0,200 nm or less (better); and 3. Capable of achieving a "measurement uncertainty" equal to or less (better) than (1,6 + L/2	d. Equipment for measuring surface roughness (including surface defects), by measuring optical scatter with a sensitivity of 0,5 nm or less (better). Note: 2B006 includes machine tools, other than those specified in 2B001, that can be used as measuring machines if they meet or exceed the criteria specified for the measuring machine function.

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	外之可用作測量機具之工具機，其規格如符合或超過測量機具功能所列之標準，即受管制。		000) nm (L is the measured length in mm) at any point within a measuring range, when compensated for the refractive index of air and measured over a period of 30 seconds at a temperature of 20 ± 0,01 °C; or d. "Electronic assemblies" specially designed to provide feedback capability in systems specified in 2B006.b.1.c.; Note: 2B006.b.1. does not control measuring interferometer systems, with an automatic control system that is designed to use no feedback techniques, containing a "laser" to measure slide movement errors of machine-tools, dimensional inspection machines or similar equipment. 2. Angular displacement measuring instruments having an angular position "accuracy" equal to or less (better) than 0,00025 o ;	

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			Note: 2B006.b.2. does not control optical instruments, such as autocollimators, using collimated light (e.g., "laser" light) to detect angular displacement of a mirror. c. Equipment for measuring surface roughness (including surface defects), by measuring optical scatter with a sensitivity of 0,5 nm or less (better). Note: 2B006 includes machine tools, other than those specified by 2B001, that can be used as measuring machines if they meet or exceed the criteria specified for the measuring machine function.	
2B007.a	a. 於全3維影像處理或全3維｀背景分析｀時,可即時產生或修改〝程式〞,或可產生或修改數值程式資料;	a. 刪除;	a. Capable in real time of full three-dimensional image processing or full three-dimensional 'scene analysis' to generate or modify "programs" or to generate or modify numerical program data;	a. Not used;

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2B008	2B008　專為工具機或尺度檢驗或測量系統及設備所特別設計之組件或單元，如下： a. 總〝準確度(或稱〝精度〞)〞小於(優於)(800＋(600 × L/ 1,000)) nm(L 等於以 mm 為單位之可量測長度)之線性定位回饋單元； 說明：〝雷射〞系統，參照 2B006.b.1.c.、2B006.b.1.d.與 2B206.c.之註解。 b. 〝準確度(或稱〝精度〞)〞小於(優於)0.00025°之旋轉定位回饋單元； 說明:〝雷射〞系統,參照 2B006.b.2.註解。 註解：2B008.a.與 2B008.b.管制項目,其設計為回饋控制測定之位置資訊，包括感應式元件、刻度尺、紅外線系統或〝雷射〞系統。 c. 依據製造商之規範，能提升工具機等級達到或超越 2B 指定等級之〝複合迴轉工作台〞及〝擺動式主軸〞。	2B008　專為工具機特別設計之〝複合迴轉工作台〞及〝擺動式主軸〞，如下： a. 刪除； b. 刪除； c. 〝複合迴轉工作台〞具下列所有特性： 1. 設計用於機械工具車削、銑削或研磨；及 2. 具 2 個旋轉軸設計用於同時協調進行〝輪廓控制〞； 技術註解： 〝複合迴轉工作台〞指可使工作物件在 2 個非平行軸線上旋轉與傾斜之工作台。 d. 〝擺動式主軸〞具下列所有特性： 1. 設計用於機械工具車削、銑削或研磨；及 2. 設計用於同時協調進行〝輪廓控制〞；	2B008 Assemblies or units, specially designed for machine tools, or dimensional inspection or measuring systems and equipment, as follows: a. Linear position feedback units having an overall "accuracy" less (better) than (800 + (600 × L/1 000)) nm (L equals the effective length in mm); N.B. For "laser" systems see also 2B006.b.1.c., 2B006.b.1.d. and 2B206.c. b. Rotary position feedback units having an "accuracy" less (better) than 0,00025 o ; N.B. For "laser" systems see also Note to 2B006.b.2. Note: 2B008.a. and 2B008.b. control units, which are designed to determine the positioning information for feedback control, such as inductive type devices, graduated scales, infrared systems	2B008 'Compound rotary tables' and "tilting spindles", specially designed for machine tools, as follows: a. Not used; b. Not used; c. 'Compound rotary tables' having all of the following: 1. Designed for machine tools for turning, milling or grinding; and 2. Two rotary axes designed to be coordinated simultaneously for "contouring control"; Technical Note: A 'compound rotary table' is a table allowing the workpiece to rotate and tilt about two non-parallel axes d. "Tilting spindles" having all of the following: 1. Designed for machine tools for turning, milling or grinding; and 2. Designed to be coordinated simultaneously for "contouring control".

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			or "laser" systems. c. "Compound rotary tables" and "tilting spindles", capable of upgrading, according to the manufacturer's specifications, machine tools to or above the levels specified in 2B.	
2B109	2B109　除2B009所述以外之流動成型機，及特別設計之零件，如下： 說明：參照2B209。 a. 具下列所有特性之流動成型機： 1. 依據製造商的技術規格，可裝置〝數值控制〞單元或電腦控制單元，甚至並未裝置此等控制單元者；及 2. 具有2個軸以上，且可同時協調進行〝輪廓控制〞。	2B109　除2B009所述以外之流動成型機，其可〝生產〞用於〝飛彈〞之推進器零件及設備(例如馬達殼體、級間結構)，及特別設計之零件，如下： 說明：參照2B209。 a. 具下列所有特性之流動成型機： 1. 本身已配備，或依據製造商的技術規格，其可裝置〝數值控制〞單元或電腦控制單元；及 2. 具有2個軸以上，且可同時協調進行〝輪廓控制〞。	2B109 Flow-forming machines, other than those specified in 2B009, and specially designed components as follows: N.B. SEE ALSO 2B209. a. Flow-forming machines having all of the following: 1. According to the manufacturer's technical specification, can be equipped with "numerical control" units or a computer control, even when not equipped with such units; and 2. With more than two axes which can be coordinated simultaneously for "contouring control".	2B109 Flow-forming machines, other than those specified in 2B009, usable in the "production" of propulsion components and equipment (e.g. motor cases and interstages) for "missiles", and specially designed components as follows: N.B. SEE ALSO 2B209. a. Flow-forming machines having all of the following: 1. Equipped with, or according to the manufacturer's technical specification are capable of being equipped with "numerical control" units or computer control; and 2. More than two axes which can be coordinated simultaneously for "contouring control".
2B120.a	a.2軸或以上；	a.2個或2個以上的軸；	a. Two axes or more;	a. Two or more axes;

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2B121.a	a. 2 軸或以上；及	a.2 個或 2 個以上的軸；及	a. Two axes or more; and	a. Two or more axes; and
2B122	2B122 能提供加速度超過 100 g 之離心機，設計或改裝能容納滑環或積體非接觸設備，能傳輸電力及訊號資訊，或同時傳輸兩者。	2B122 能提供加速度大於 100 g 之離心機，設計或改裝能容納滑環或積體非接觸設備，能傳輸電力及訊號資訊，或同時傳輸兩者。	2B122 Centrifuges capable of imparting accelerations above 100 g and designed or modified to incorporate slip rings or integrated non-contact devices capable of transferring electrical power, signal information, or both.	2B122 Centrifuges capable of imparting accelerations greater than 100 g and designed or modified to incorporate slip rings or integrated non-contact devices capable of transferring electrical power, signal information, or both.
2B201 技術註解	技術註解： 工具機機型之定位精度聲明級等可用以下程序遵照 ISO 230-2:1988 ，或同效之國家標準(若有提供)並經國家權責單位同意下，以取代個別之機器測試。測定定位精度方法如下： a.選擇同型號之機器 5 台進行評量； b.依 ISO 230-2:1988 (1)測量線性軸； c.測定每一台機器之定位精度(A)。計算精度值之方式記載於 ISO 230-2:1988 (1) 標準內； d.測定每一軸之平均定位精度	技術註解： 工具機機型之定位精度聲明等級可用以下程序遵照 ISO 230-2:1988 ，或同效之國家標準(若有提供)並經國家權責單位同意下，以取代個別之機器測試。測定定位精度方法如下： a.選擇同型號之機器 5 台進行評量； b.依 ISO 230-2:1988(1,2)測量線性軸； c.測定每一台機器之定位精度(A)。計算精度值之方式記載於 ISO 230-2:1988(1,2) 標準內； d.測定每一軸之平均定位精度	Technical Note: Stated positioning accuracy levels derived under the following procedures from measurements made according to ISO 230-2:1988 (1) or national equivalents may be used for each machine tool model if provided to, and accepted by, national authorities instead of individual machine tests. Determination of stated positioning accuracy: a. Select five machines of a model to be evaluated; b. Measure the linear axis	Technical Note: Stated positioning accuracy levels derived under the following procedures from measurements made according to ISO 230-2:1988 (1) or national equivalents may be used for each machine tool model if provided to, and accepted by, national authorities instead of individual machine tests. Determination of stated positioning accuracy: a. Select five machines of a model to be evaluated; b. Measure the linear axis accuracies according to ISO 230-2:1988 (1); c. Determine the accuracy values (A) for each axis of each machine. The method of calculating the accuracy value is described in the ISO

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	值。此平均值即為此機型之每一軸(^Ax ^Ay…) 定位精度之聲明值； e.由於 2B201 涉及每一線性軸，因此有多少線性軸即有多少個定位精度聲明值 f.若一機器型號之任一軸其定位精度聲明值雖不在 2B201.a.、2B201.a.或 2B201.c.管制內，但研磨型機器依 ISO 230-2:1988 (1)測得之定位精度聲明值等於或小於(優於) 6 μm、銑削及車削型機器依 ISO 230-2:1988 (1)測得之定位精度聲明值等於或小於(優於) 8 μm 者，則製造商必須每 18 個月再確認一次其精度等級。 (1)製造商測量定位精度標準係用 ISO230-2:1997 或 ISO230-2:2006 應諮詢成員國權責單位。 (2)本管制項目之定位精度標準係採 ISO230-2:2006，其與 ISO230-2:1988 相同，換算比率約為 4:3。	值。此平均值即為此機型之每一軸(^Ax ^Ay…) 定位精度之聲明值； e.由於 2B201 涉及每一線性軸，因此有多少線性軸即有多少個定位精度聲明值； f.若一機器型號之任一軸其定位精度聲明值雖不在 2B201.a.、2B201.a.或 2B201.c.規範中，但研磨型機器依 ISO 230-2:1988(1,2)測得之定位精度聲明值等於或小於(優於) 6 μm、銑削及車削型機器依 ISO 230-2:19881,2 測得之定位精度聲明值等於或小於(優於) 8 μm 者，則製造商必須每 18 個月再確認一次其精度等級。 (1)製造商測量定位精度標準係用 ISO230-2:1997 或 ISO230-2:2006 應諮詢成員國權責單位。 (2)本管制項目之定位精度標準係採 ISO230-2:2006，其與 ISO230-2:1988 相同，換算比率約為 4:3。	accuracies according to ISO 230-2:1988 (1); c. Determine the accuracy values (A) for each axis of each machine. The method of calculating the accuracy value is described in the ISO 230-2:1988 (1) standard; d. Determine the average accuracy value of each axis. This average value becomes the stated positioning accuracy of each axis for the model (Âx Ây...); e. Since Item 2B201 refers to each linear axis, there will be as many stated positioning accuracy values as there are linear axes; f. If any axis of a machine tool not controlled by 2B201.a., 2B201.b. or 2B201.c. has a stated positioning accuracy of 6 μm or better (less) for grinding machines, and 8 μm or better (less) for milling and turning machines, both according to ISO	230-2:1988 (1) standard; d. Determine the average accuracy value of each axis. This average value becomes the stated positioning accuracy of each axis for the model (Âx Ây…); e. Since Item 2B201 refers to each linear axis, there will be as many stated positioning accuracy values as there are linear axes; f. If any axis of a machine tool not specified in 2B201.a., 2B201.b. or 2B201.c. has a stated positioning accuracy of 6 μm or better (less) for grinding machines, and 8 μm or better (less) for milling and turning machines, both according to ISO 230-2:1988 (1), then the builder should be required to reaffirm the accuracy level once every eighteen months. (1) Manufacturers calculating positioning accuracy in accordance with ISO 230-2:1997 or 2006 should consult the competent authorities of the Member State in which they are established.

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			230-2:1988（1）, then the builder should be required to reaffirm the accuracy level once every eighteen months. （1）Manufacturers calculating positioning accuracy in accordance with ISO 230-2:1997 or 2006 should consult the competent authorities of the Member State in which they are established.	
2B201.b.1	b. 具下列任一特性之研磨用工具機： 1. 依照 ISO 230-2:1988 或等效國家標準，在〝所有補償機制〞下沿任一線性軸之定位精度等於或小於(優於)4 μm；	b. 具下列任一特性之研磨用工具機： 1. 依照 ISO 230-2:1988(1,2)或等效國家標準，在〝所有補償機制〞下沿任一線性軸之定位精度等於或小於(優於)4 μm；	b. Machine tools for grinding, having any of the following characteristics: 1. Positioning accuracies with "all compensations available" equal to or less (better) than 4 μm according to ISO 230-2:1988（1）or national equivalents along any linear axis;	b. Machine tools for grinding, having any of the following characteristics: 1. Positioning accuracies with "all compensations available" equal to or less (better) than 4 μm according to ISO 230-2:1988（1）or national equivalents along any linear axis;
2B201.b.3 註解 b	b. 無 z 軸或 w 軸之工模研磨機，且依照 ISO 230-2:1988 或等效國家標準，其總定位精確度小於(優於) 4 μm。	b. 無 z 軸或 w 軸之工模研磨機，且依照 ISO 230-2:1988(1,2)或等效國家標準，其總定位精確度小於(優於) 4 μm。	b. Jig grinders that do not have a z-axis or a w-axis with an overall positioning accuracy less (better) than 4 μm according to ISO 230-2:1988 1 or national	b. Jig grinders that do not have a z-axis or a w-axis with an overall positioning accuracy less (better) than 4 μm according to ISO 230-2:1988（1）or national equivalents.

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			equivalents.	
2B206.c.2	2.標準溫度和標準壓力情況下，在±1 K 溫度下保持至少 12 小時，全部如下： a. 〝解析度〞在全尺度情況下等於或優於 0,1 μm；及 b. 〝量測不準度〞等於或小於(優於) (0,2 + L/2,000) μm (L 係以 mm 為單位之可量測長度)。	2. 標準溫度和標準壓力下，能夠在±1 K (± 1 ˚C)溫度下維持至少 12 小時，具下列所有特性： a. 〝解析度〞在全尺度情況下等於或優於 0,1 μm；及 b. 〝量測不準度〞等於或小於(優於) (0,2 + L/2,000) μm (L 係以 mm 為單位之可量測長度)。	2. Maintaining, for at least 12 hours, at a temperature of ± 1 K around a standard temperature and standard pressure, all of the following: a. A "resolution" over their full scale of 0,1 μm or better; and b. With a "measurement uncertainty" equal to or better (less) than (0,2 + L/2 000) μm (L is the measured length in millimeters).	2. Capable of maintaining, for at least 12 hours, at a temperature of ± 1 K (± 1 ˚C); around a standard temperature and standard pressure, all of the following: a. A "resolution" over their full scale of 0,1 μm or better; and b. With a "measurement uncertainty" equal to or better (less) than (0,2 + L/2 000) μm (L is the measured length in mm).
2B206.d	無	d. 線性電壓差動轉換器(LVDT)系統具下列兩項特性： 技術註解： 就 2B206.d.之目的而言，`線性位移´指量測探針與被測物體間之距離變化 。 1. 具下列任一特性： a. 操作範圍達到 5 mm 的 LVDT，在 0 至全部操作範圍內測量之〝線性度〞等於或小於(優於) 0.1%；或 b. 操作範圍超過 5 mm 的	-	d. Linear variable differential transformer (LVDT) systems having both of the following characteristics: Technical Note: For the purpose of 2B206.d. 'linear displacement' means the change of distance between the measuring probe and the measured object. 1. Having any of the following: a. "Linearity" equal to or less (better) than 0,1 % measured from 0 to the full operating range,

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		LVDT，在 0 至 5 mm 操作範圍內測量之〝線性度〞等於或小於(優於) 0.1%； 2. 在標準周圍環境測試室溫±1 K(± 1 ˚C)下，每日之漂移等於或小於(優於) 0.1%；		for LVDTs with an operating range up to 5 mm; or b. "Linearity" equal to or less (better) than 0,1 % measured from 0 to 5 mm for LVDTs with an operating range greater than 5 mm; and 2. Drift equal to or better (less) than 0,1 % per day at a standard ambient test room temperature ± 1 K (± 1 ˚C).
2B227	2B227 真空或其他控制氣壓冶金熔爐及鑄造爐，及相關設備，如下： a. 具下列 2 項特性之電弧再熔爐及鑄造爐： 1. 可消耗之電極容量介於 1,000 cm^3 至 20,000 cm^3 之間；及 2. 可於熔化溫度超過 1,973 K(1,700 °C)下操作； b. 具下列 2 項特性之電子束熔爐及電漿原子化及熔爐： 1. 功率為 50 kW 或以上；及 2. 可於熔化溫度超過 1,473 K(1,200 °C)下操作。	2B227 真空或其他控制氣壓冶金熔爐及鑄造爐，及相關設備，如下： a.電弧再熔爐、電弧熔爐與電弧熔煉及鑄造爐，具下列 2 項特性： 1. 可消耗之電極容量介於 1,000 cm^3 至 20,000 cm^3 之間；及 2. 可於熔化溫度超過 1,973 K(1,700 °C)下操作； b. 電子束熔爐、電漿原子化熔爐及電漿熔爐，具下列 2 項特性： 1. 功率為 50 kW 或以上；及 2. 可於熔化溫度超過 1,473 K(1,200 °C)下操作。	2B227 Vacuum or other controlled atmosphere metallurgical melting and casting furnaces and related equipment as follows: a. Arc remelt and casting furnaces having both of the following characteristics: 1. Consumable electrode capacities between 1 000 cm^3 and 20 000 cm^3; and 2. Capable of operating with melting temperatures above 1 973 K (1 700 ˚C); b. Electron beam melting furnaces and plasma atomization and melting furnaces, having both of the following characteristics:	2B227 Vacuum or other controlled atmosphere metallurgical melting and casting furnaces and related equipment as follows: a. Arc remelt furnaces, arc melt furnaces and arc melt and casting furnaces having both of the following characteristics: 1. Consumable electrode capacities between 1 000 cm^3 and 20 000 cm^3; and 2. Capable of operating with melting temperatures above 1 973 K (1 700 ˚C); b. Electron beam melting furnaces, plasma atomization furnaces and plasma melting furnaces, having both of the following characteristics: 1. A power of 50 kW or greater; and 2. Capable of operating with melting temperatures above 1 473 K (1 200 ˚C);

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			1. A power of 50 kW or greater; and 2. Capable of operating with melting temperatures above 1 473 K (1 200 °C);	
2B350.a 說明	無	說明：用於預製維修組件，參閱2B350.k.。	-	N.B. For prefabricated repair assemblies, see 2B350.k.
2B350.c 說明	無	說明：用於預製維修組件，參閱2B350.k.。	-	N.B. For prefabricated repair assemblies, see 2B350.k.
2B350.k	無	k. 預製維修組件之金屬表面，其與處理化學品直接接觸，由鉭或鉭合金製造，以及為其專門設計之零件： 1. 設計用於機械性連結 2B350.a. 所述之玻璃襯裏反應容器或反應器；或 2. 設計用於機械性連結 2B350.c. 所述之玻璃襯裏儲槽、容器或接收器。	-	k. Prefabricated repair assemblies having metallic surfaces that come in direct contact with the chemical(s) being processed which are made from tantalum or tantalum alloys as follows, and specially designed components therefor: 1. Designed for mechanical attachment to glass-lined reaction vessels or reactors specified in 2B350.a.; or 2. Designed for mechanical attachment to glass-lined storage tanks, containers or receivers specified in 2B350.c.
2B351	2B351 除 1A004 所述以外之毒性氣體監控系統，以及其專用偵測器，與為此用途之偵測器、感測器設備，以及可替換之感測器卡匣：	2B351 除 1A004 所述以外之毒性氣體監控器與監控系統，以及其專用偵測器，與為此用途之偵測器、感測器設備，以及可替換之感測器卡匣：	2B351 Toxic gas monitoring systems and their dedicated detecting components, other than those specified in 1A004, as follows; and detectors; sensor devices; and	2B351 Toxic gas monitors and monitoring systems and their dedicated detecting components, other than those specified in 1A004, as follows; and detectors; sensor devices; and replaceable sensor cartridges therefor:

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			replaceable sensor cartridges therefor:	
2B352	2B352 可用於處理生物材料之設備，如下： a. 防護設施與相關設備，如下： 1. 防護級別為 P3、P4 之完全防護設施(BL3, BL4, L3, L4) ，記載於世界衛生組織實驗室生物安全手冊(第三版，日內瓦，2004 年)。 2. 為在固定安裝於 2B352.a.管制之防護設施而設計的設備，如下： a.雙門穿越式消毒高壓滅菌器； b.呼吸空氣服裝消毒淋浴系統； c.機械式密封或充氣式密封門； b. 發酵器及零件，如下： 1. 發酵器能夠培養〝微生物〞，或活細胞用於生產病毒或毒素，其不需藉由噴霧劑之傳播，且其總容量為 20 公升或以上； 2. 設計用於 2B352.b.1.之發酵器零件，如下：	2B352 生物製造及處理設備，如下： a. 防護設施與相關設備，如下： 1. 防護級別為 P3、P4 之完全防護設施(BL3, BL4, L3, L4) ，記載於世界衛生組織實驗室生物安全手冊(第三版，日內瓦，2004 年)。 2. 為在固定安裝於 2B352.a.所述防護設施而設計之設備，如下： a.雙門穿越式消毒高壓滅菌器； b.呼吸空氣服裝消毒淋浴系統； c.機械式密封或充氣式密封門； b. 發酵器及零件，如下： 1. 發酵器能夠培養〝微生物〞，或活細胞用於生產病毒或毒素，其不需藉由噴霧劑之傳播，且其內部總容量為 20 公升或以上； 2. 設計用於 2B352.b.1.所述之發酵器零件，如下：	2B352 Equipment capable of use in handling biological materials, as follows: a. Containment facilities and related equipment as follows: 1. Complete containment facilities that meet the criteria for P3 or P4 (BL3, BL4, L3, L4) containment as specified in the WHO Laboratory Biosafety Manual (3 rd edition Geneva, 2004); 2. Equipment designed for fixed installation in containment facilities controlled in 2B352.a., as follows: a. Double-door pass-through decontamination autoclaves; b. Breathing air suit decontamination showers; c. Mechanical-seal or inflatable-seal walkthrough doors;	2B352 Biological manufacturing and handling equipment, as follows: a. Containment facilities and related equipment as follows: 1. Complete containment facilities that meet the criteria for P3 or P4 (BL3, BL4, L3, L4) containment as specified in the WHO Laboratory Biosafety Manual (3 rd edition Geneva, 2004); 2. Equipment designed for fixed installation in containment facilities specified in 2B352.a., as follows: a. Double-door pass-through decontamination autoclaves; b. Breathing air suit decontamination showers; c. Mechanical-seal or inflatable-seal walkthrough doors; b. Fermenters and components as follows: 1. Fermenters capable of cultivation of "microorganisms" or of live cells for the production of viruses or toxins, without the propagation of aerosols, having a total internal volume of 20 litres or more;

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			b. Fermenters and components as follows: 1. Fermenters capable of cultivation of "microorganisms" or of live cells for the production of viruses or toxins, without the propagation of aerosols, having a total capacity of 20 litres or more; 2. Components designed for fermenters in 2B352.b.1. as follows:	2. Components designed for fermenters specified in 2B352.b.1. as follows:
2B352.i	無	i.核酸組合與合成裝置，部分或全自動，設計用於產生長度超過 1.5 千鹼基對(kbp)的連續性核酸，其單次運行的錯誤率低於 5%。	-	i. Nucleic acid assemblers and synthesisers, which are partly or entirely automated, and designed to generate continuous nucleic acids greater than 1,5 kilobases in length with error rates less than 5 % in a single run.
2E003	2E003 其他〝技術〞，如下： a.〝開發〞互動式繪圖之〝技術〞，以製作或修改其零件加工程式，作為〝數值控制〞單元之整合部分。 b. 金屬加工製造程序〝技術〞，如下： 1. 用以設計專為下列任一程序而	2E003 其他〝技術〞，如下： a. 刪除； b. 金屬加工製造程序〝技術〞，如下： 1. 用以設計專為下列任一程序而特別設計之工具、模具或夾具之〝技術〞：	2E003 Other "technology", as follows: a. "Technology" for the "development" of interactive graphics as an integrated part in "numerical control" units for preparation or modification of	2E003 Other "technology", as follows: a. Not used; b. "Technology" for metal-working manufacturing processes, as follows: 1. "Technology" for the design of tools, dies or fixtures specially designed for any of the following processes:

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	特別設計之工具、模具或夾具之〝技術〞： a. 〝超塑性成形〞； b. 〝擴散結合〞；或 c. 〝直接作用液壓成形〞； 2. 包含於下列程序方法或參數，且用於控制之技術資料： a. 鋁合金、鈦合金或〝超合金〞之〝超塑性成形〞： 1. 表面預處理； 2. 應變率； 3. 溫度； 4. 壓力； b. 〝超合金〞或鈦合金之〝擴散結合〞： 1. 表面預處理； 2. 溫度； 3. 壓力； c. 鋁合金或鈦合金之〝直接作用液壓成形〞： 1. 壓力； 2. 循環時間； d. 鈦合金、鋁合金或〝超合金〞之〝熱均壓緻密化〞：	a. 〝超塑性成形〞； b. 〝擴散結合〞；或 c. 〝直接作用液壓成形〞； 2. 包含於下列程序方法或參數，且用於控制之技術資料： a. 鋁合金、鈦合金或〝超合金〞之〝超塑性成形〞： 1. 表面預處理； 2. 應變率； 3. 溫度； 4. 壓力； b. 〝超合金〞或鈦合金之〝擴散結合〞： 1. 表面預處理； 2. 溫度； 3. 壓力； c. 鋁合金或鈦合金之〝直接作用液壓成形〞： 1. 壓力； 2. 循環時間； d. 鈦合金、鋁合金或〝超合金〞之〝熱均壓緻密化〞： 1. 溫度； 2. 壓力；	part programs; b. "Technology" for metal-working manufacturing processes, as follows: 1. "Technology" for the design of tools, dies or fixtures specially designed for any of the following processes: a. "Superplastic forming"; b. "Diffusion bonding"; or c. "Direct-acting hydraulic pressing"; 2. Technical data consisting of process methods or parameters as listed below used to control: a. "Superplastic forming" of aluminium alloys, titanium alloys or "superalloys": 1. Surface preparation; 2. Strain rate; 3. Temperature; 4. Pressure; b. "Diffusion bonding" of "superalloys" or titanium alloys: 1. Surface preparation; 2. Temperature; 3. Pressure; c. 'Direct-acting hydraulic pressing'of aluminium alloys or titanium alloys: 1. Pressure; 2. Cycle time; d. 'Hot isostatic densification' of titanium alloys, aluminium alloys or "superalloys": 1. Temperature; 2. Pressure;	a. "Superplastic forming"; b. "Diffusion bonding"; or c. 'Direct-acting hydraulic pressing'; 2. Technical data consisting of process methods or parameters as listed below used to control: a. "Superplastic forming" of aluminium alloys, titanium alloys or "superalloys": 1. Surface preparation; 2. Strain rate; 3. Temperature; 4. Pressure; b. "Diffusion bonding" of "superalloys" or titanium alloys: 1. Surface preparation; 2. Temperature; 3. Pressure; c. 'Direct-acting hydraulic pressing'of aluminium alloys or titanium alloys: 1. Pressure; 2. Cycle time; d. 'Hot isostatic densification' of titanium alloys, aluminium alloys or "superalloys": 1. Temperature; 2. Pressure;

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	1. 溫度； 2. 壓力； 3. 循環時間； c. 為製造機身結構而〝開發〞或〝生產〞之液壓伸展成型機及模具之〝技術〞； d. 用存於〝數值控制〞單元內之設計資料，以〝開發〞工具機指令(如零件加工程式)產生器之〝技術〞；	3. 循環時間； 技術註解： 1.〝直接作用液壓成形〞係指一種變形過程，使用充滿液體之彈性囊袋直接與工作物件接觸。 2.〝熱均壓緻密化〞係指在密閉腔室中以超過375K(102 °C)加壓鑄造之過程，利用不同介質(氣體、液體、固態粒子等)在各方向產生相同力量，以減少或消除鑄造物之內在空隙。 c. 為製造機身結構而〝開發〞或〝生產〞之液壓伸展成型機及模具之〝技術〞； d. 刪除；	1. Surface preparation; 2. Temperature; 3. Pressure; c. "Direct-acting hydraulic pressing" of aluminium alloys or titanium alloys: 1. Pressure; 2. Cycle time; d. "Hot isostatic densification" of titanium alloys, aluminium alloys or "superalloys": 1. Temperature; 2. Pressure; 3. Cycle time; c. "Technology" for the "development" or "production" of hydraulic stretch-forming machines and dies therefor, for the manufacture of airframe structures; d. "Technology" for the "development" of generators of machine tool instructions (e.g., part programs) from design data	3. Cycle time; Technical Notes: 1. 'Direct-acting hydraulic pressing' is a deformation process which uses a fluid-filled flexible bladder in direct contact with the workpiece. 2. 'Hot isostatic densification' is a process of pressurising a casting at temperatures exceeding 375 K (102 °C) in a closed cavity through various media (gas, liquid, solid particles, etc.) to create equal force in all directions to reduce or eliminate internal voids in the casting c. "Technology" for the "development" or "production" of hydraulic stretch-forming machines and dies therefor, for the manufacture of airframe structures; d. Not used;

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			residing inside "numerical control" units;	
表-沉積技術 B3	無	類鑽碳(17)	-	Diamond-like carbon (17)
3A 註解	註解 1：3A001 或 3A002 中除 3A001.a.3.至 3A001.a.10.、3A001.a.12.或 3A001.a.14.所述以外之設備與零件管制狀況，專為其他設備所設計或具有與其他設備相同功能特徵者，由其他設備之管制狀況所決定。 註解 2：3A001.a.3.至 3A001.a.9.、3A001.a.12.或 3A001.a.14.所述為其他設備之特定功能所作不可變更之設定或設計之積體電路管制狀況，由其他設備之管制狀況所決定。 說明：當製造者或申請人不能決定其他設備之管制狀況時，其積體電路的管制狀況由 3A001.a.3.至 3A001.a.9.，3A001.a.12.及 3A001.a.14.所決定。	註解 1：3A001 或 3A002 中除 3A001.a.3.至 3A001.a.10.、3A001.a.12.至 3A001.a.14.所述以外之設備與零件管制狀況，專為其他設備所設計或具有與其他設備相同功能特徵者，由其他設備之管制狀況所決定。 註解 2：3A001.a.3.至 3A001.a.9.或 3A001.a.12.至 3A001.a.14.所述為其他設備之特定功能所作不可變更之設定或設計之積體電路管制狀況，由其他設備之管制狀況所決定。 說明：當製造者或申請人不能決定其他設備之管制狀況時，其積體電路的管制狀況由 3A001.a.3.至 3A001.a.9.，以及 3A001.a.12.至 3A001.a.14.所決定。	Note 1: The control status of equipment and components described in 3A001 or 3A002, other than those described in 3A001.a.3. to 3A001.a.10., 3A001.a.12. or 3A001.a.14, which are specially designed for or which have the same functional characteristics as other equipment is determined by the control status of the other equipment. Note 2: The control status of integrated circuits described in 3A001.a.3. to 3A001.a.9., 3A001.a.12. or 3A001.a.14 which are unalterably programmed or designed for a specific function for another equipment is determined by the control status of the other equipment.	Note 1: The control status of equipment and components described in 3A001 or 3A002, other than those described in 3A001.a.3. to 3A001.a.10., or 3A001.a.12. to 3A001.a.14., which are specially designed for or which have the same functional characteristics as other equipment is determined by the control status of the other equipment. Note 2: The control status of integrated circuits described in 3A001.a.3. to 3A001.a.9., or 3A001.a.12. to 3A001.a.14. which are unalterably programmed or designed for a specific function for another equipment is determined by the control status of the other equipment. N.B. When the manufacturer or applicant cannot determine the control status of the other equipment, the control status of the integrated circuits is determined in 3A001.a.3. to 3A001.a.9., and 3A001.a.12. to 3A001.a.14.

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			N.B. When the manufacturer or applicant cannot determine the control status of the other equipment, the control status of the integrated circuits is determined in 3A001.a.3. to 3A001.a.9., 3A001.a.12 and 3A001.a.14.	
3A001.a.2	2.〝微處理器微電路〞、〝微電腦微電路〞、微控制器微電路、由化合物半導體所製造之儲存積體電路、類比－數位轉換器、包含數位－類比轉換器並可儲存與處理數位資料的積體電路、數位－類比轉換器、為〝訊號處理〞所設計之光電或〝光學積體電路〞、現場可程式邏輯元件、客戶訂製之積體電路之功能未知或使用該積體電路之設備之控制狀況不明、快速傅立葉轉換(FFT)處理器、電抹除式可編程唯讀記憶體 (EEPROMs)、快閃記憶體或靜態隨機存取記憶體 (SRAMs) ，具下列任一特性： a. 被評定為可於 398 K (125 °C)	2.〝微處理器微電路〞、〝微電腦微電路〞、微控制器微電路、由化合物半導體所製造之儲存積體電路、類比－數位轉換器、包含數位－類比轉換器並可儲存與處理數位資料的積體電路、數位－類比轉換器、為〝訊號處理〞所設計之光電或〝光學積體電路〞、現場可程式邏輯元件、客戶訂製之積體電路之功能未知或使用該積體電路之設備之控制狀況不明、快速傅立葉轉換(FFT)處理器或〝非揮發性記憶體〞，具下列任一特性： a. 被評定為可於 398 K (125 °C) 以上之環境溫度下操作； b. 被評定為可於 218 K (-55 °C)	2. "Microprocessor microcircuits", "microcomputer microcircuits", microcontroller microcircuits, storage integrated circuits manufactured from a compound semiconductor, analogue-to-digital converters, integrated circuits that contain analogue-to-digital converters and store or process the digitised data, digital-to-analogue converters, electro-optical or "optical integrated circuits" designed for "signal processing", field programmable logic devices, custom integrated circuits for	2. "Microprocessor microcircuits", "microcomputer microcircuits", microcontroller microcircuits, storage integrated circuits manufactured from a compound semiconductor, analogue-to-digital converters, integrated circuits that contain analogue-to-digital converters and store or process the digitised data, digital-to-analogue converters, electro-optical or "optical integrated circuits" designed for "signal processing", field programmable logic devices, custom integrated circuits for which either the function is unknown or the control status of the equipment in which the integrated circuit will be used is unknown, Fast Fourier Transform (FFT) processors, Static Random-Access Memories

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	以上之環境溫度下操作； b. 被評定為可於 218 K (-55 °C) 以下之環境溫度下操作；或 c. 評定為可於 218 K (-55 °C)至 398 K (125 °C)整個環境溫度範圍內操作者； 註解：3A.001.a.2.不管制民用汽車或火車應用之積體電路。	以下之環境溫度下操作；或 c. 評定為可於 218 K (-55 °C)至 398 K (125 °C)整個環境溫度範圍內操作者； 註解：3A.001.a.2.不管制民用汽車或火車應用之積體電路。 技術註解： ‵非揮發性記憶體‵為電源關閉後儲存的資料在一陣時間內不會消失者的記憶體。	which either the function is unknown or the control status of the equipment in which the integrated circuit will be used is unknown, Fast Fourier Transform (FFT) processors, Electrical Erasable Programmable Read-Only Memories (EEPROMs), flash memories, Static Random-Access Memories (SRAMs), or Magnetic Random Access Memories (MRAMs), having any of the following: a. Rated for operation at an ambient temperature above 398 K (125 °C); b. Rated for operation at an ambient temperature below 218 K (-55 °C); or c. Rated for operation over the entire ambient temperature range from 218 K (-55 °C) to 398 K (125 °C); Note: 3A001.a.2. does not control integrated circuits for civil	(SRAMs), or 'non-volatile memories', having any of the following: a. Rated for operation at an ambient temperature above 398 K (125 °C); b. Rated for operation at an ambient temperature below 218 K (- 55 °C); or c. Rated for operation over the entire ambient temperature range from 218 K (- 55 °C) to 398 K (125 °C); Note: 3A001.a.2. does not control integrated circuits for civil automobiles or railway train applications. Technical Note: 'Non-volatile memories' are memories with data retention over a period of time after a power shutdown.EN 14.12.2018 Official Journal of the European Union L 319/105

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			automobiles or railway train applications.	
3A001.a.5	5. 類比－數位轉換器(ADC)及數位－類比轉換器(DAC)積體電路，如下： a. 具下列任一特性之類比－數位轉換器： 說明：參照 3A101。 1. 解析度為 8 位元或以上，但小於 10 位元，輸出率大於每秒 1.3 十億次取樣(GSPS)； 2. 解析度為 10 位元或以上，但小於 12 位元，輸出率大於每秒 600 百萬次取樣(MSPS)； 3. 解析度為 12 位元或以上，但小於 14 位元，輸出率大於每秒 400 百萬次取樣(MSPS)； 4. 解析度為 14 位元或以上，但小於或等於 16 位元，輸出率大於每秒 250 百萬次取樣(MSPS)；或 5. 解析度為 16 位元或以上，輸出率大於每秒 65 百萬次取樣(MSPS)； 說明：包含數位－類比轉換器並可	5. 類比－數位轉換器(ADC)及數位－類比轉換器(DAC)積體電路，如下： a. 具下列任一特性之類比－數位轉換器： 說明：參照 3A101。 1. 解析度為 8 位元或以上，但小於 10 位元，〝取樣率〞大於每秒 1.3 十億次取樣(GSPS)； 2. 解析度為 10 位元或以上，但小於 12 位元，〝取樣率〞大於每秒 600 百萬次取樣(MSPS)； 3. 解析度為 12 位元或以上，但小於 14 位元，〝取樣率〞大於每秒 400 百萬次取樣(MSPS)； 4. 解析度為 14 位元或以上，但小於或等於 16 位元，〝取樣率〞大於每秒 250 百萬次取樣(MSPS)；或 5. 解析度為 16 位元或以上，〝取樣率〞大於每秒 65 百萬次取樣(MSPS)；	5. Analogue-to-Digital Converter (ADC) and Digital-to-Analogue Converter (DAC) integrated circuits, as follows: a. ADCs having any of the following: N.B. SEE ALSO 3A101 1. A resolution of 8 bit or more, but less than 10 bit, with an output rate greater than 1.3 giga samples per second (GSPS); 2. A resolution of 10 bit or more, but less than 12 bit, with an output rate greater than 600 mega samples per second (MSPS); 3. A resolution of 12 bit or more, but less than 14 bit, with an output rate greater than 400 mega samples per second (MSPS); 4. A resolution of 14 bit or more, but less than 16 bit, with an output rate greater than 250 mega samples	5. Analogue-to-Digital Converter (ADC) and Digital-to-Analogue Converter (DAC) integrated circuits, as follows: a. ADCs having any of the following: N.B. SEE ALSO 3A101 1. A resolution of 8 bit or more, but less than 10 bit, with a "sample rate" greater than 1,3 Giga Samples Per Second (GSPS); 2. A resolution of 10 bit or more, but less than 12 bit, with a "sample rate" greater than 600 Mega Samples Per Second (MSPS); 3. A resolution of 12 bit or more, but less than 14 bit, with a "sample rate" greater than 400 MSPS; 4. A resolution of 14 bit or more, but less than 16 bit, with a "sample rate" greater than 250 MSPS; or 5. A resolution of 16 bit or more with a "sample rate" greater than 65 MSPS; N.B. For integrated circuits that contain analogue-to-digital converters and store or process the digitized data, see 3A001.a.14.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	儲存與處理數位資料的積體電路，參考 3A001.a.14.。 技術註解： 1. n 位元之解析度係對應於一個量子化的 2n 種狀態。 3A001　　(續) 2. 輸出字的位元數相等於數位－類比轉換器之解析度。 3. 輸出率即為轉換器的最大輸出速率，不論其結構為何或是否超取樣。亦有廠商以取樣率、轉換率或產出率稱之。其單位為百萬赫(MHz)或每秒百萬取樣(MSPS)。 4. 對於｀多頻道 ADCs｀而言，輸出率非為加總，且輸出率是指任何單一頻道之最大輸出率。 5. 對於｀交錯式 ADCs｀或｀多頻道 ADCs｀而言，指運作時有一交錯模式，其輸出將匯總，其輸出率為結合全部輸出之最大組合。 6. 供應商可能標示輸出率為取樣率、轉換率或生產率，其常以兆赫(MHz)或每秒百萬次取樣(MSPS)標示。	說明：包含數位－類比轉換器並可儲存與處理數位資料的積體電路，參考 3A001.a.14.。 技術註解： 1. n 位元之解析度係對應於一個量子化的 2n 種狀態。 2. 輸出字的位元數相等於數位－類比轉換器之解析度，有效位元數(ENOB)不用於判讀 ADC 之解析度。 3. 對於｀多頻道 ADCs｀而言，〝取樣率〞非為匯總結果，且〝取樣率〞是指任何單一頻道之最大輸出率。 4. 對於｀交錯式 ADCs｀或｀多頻道 ADCs｀而言，〝取樣率〞為匯總結果，〝取樣率〞為所有交錯頻道之最大輸出率組合。 b. 具下列任一特性之數位－類比轉換器： 1. 解析度至少為 10 位元或以上，且｀調整更新速率｀大於 3,500 每秒百萬次取樣(MSPS)；或 2. 解析度至少為 12 位元或以上，	per second (MSPS); or 5. A resolution of 16 bit or more with an output rate greater than 65 mega samples per second (MSPS); N.B. For integrated circuits that contain analogue-to-digital converters and store or process the digitized data, see 3A001.a.14. Technical Notes: 1. A resolution of n bit corresponds to a quantisation of 2 n levels. 2. The number of bits in the output word is equal to the resolution of the ADC. 3. The output rate is the maximum output rate of the converter, regardless of the architecture or oversampling. 4. For 'multiple channel ADCs', the outputs are not aggregated and the output rate is the maximum output rate of any single channel. 5. For 'interleaved ADCs' or for	Technical Notes: 1. A resolution of n bit corresponds to a quantisation of 2 n levels. 2. The resolution of the ADC is the number of bits of the digital output that represents the measured analogue input. Effective Number of Bits (ENOB) is not used to determine the resolution of the ADC. 3. For "multiple channel ADCs", the "sample rate" is not aggregated and the "sample rate" is the maximum rate of any single channel. 4. For "interleaved ADCs" or for "multiple channel ADCs" that are specified to have an interleaved mode of operation, the "sample rates" are aggregated and the "sample rate" is the maximum combined total rate of all of the interleaved channels. b. Digital-to-Analogue Converters (DAC) having any of the following: 1. A resolution of 10 bit or more with an 'adjusted update rate' of greater than 3 500 MSPS; or 2. A resolution of 12 bit or more with an 'adjusted update rate' of greater than 1 250 MSPS

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	7. 測量輸出率時，每秒一次取樣相當於 1 赫 (Hz)或每秒輸出 1 個字。 8. ｀多頻道 ADCs｀被定義為整合超過一個 ADC 的裝置，設計為每個 ADC 具有獨立之類比輸入。 9. ｀交錯式 ADCs｀被定義為多個 ADC 單元其對於同一個類比輸入在不同時間進行取樣，當輸出匯總時，類比輸入已得到有效率的取樣與轉換成一個更高的取樣率。 b. 具下列任一特性之數位－類比轉換器： 1. 解析度至少為 10 位元或以上，且｀調整更新速率｀大於 3,500 每秒百萬次取樣(MSPS)；或 2. 解析度至少為 12 位元或以上，｀調整更新速率｀等於或大於 1,250 每秒百萬次取樣(MSPS)，且具下列任一種特性： a. 從全尺度大小到全尺度大小之 0.024 %所需要的穩定時間，小於 9 ns；或	｀調整更新速率｀等於或大於 1,250 每秒百萬次取樣(MSPS)，且具下列任一種特性： a. 從全尺度大小到達全尺度大小之 0.024 %或之內所需要的穩定時間小於 9 ns；或	'multiple channel ADCs' that are specified to have an interleaved mode of operation, the outputs are aggregated and the output rate is the maximum combined total output rate of all of the outputs. 6. Vendors may also refer to the output rate as sampling rate, conversion rate or throughput rate. It is often specified in megahertz (MHz), mega words per second or mega samples per second (MSPS). 7. For the purpose of measuring output rate, one sample per second is equivalent to one Hertz or one output word per second. 8. 'Multiple channel ADCs' are defined as devices which integrate more than one ADC, designed so that each ADC has a separate analogue input. 9. 'Interleaved ADCs' are defined as devices which have multiple ADC	and having any of the following: a. A settling time less than 9 ns to arrive at or within 0,024 % of full scale from a full scale step; or

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			units that sample the same analogue input at different times such that when the outputs are aggregated, the analogue input has been effectively sampled and converted at a higher sampling rate. b. Digital-to-Analogue Converters (DAC) having any of the following: 1. A resolution of 10 bit or more with an 'adjusted update rate' of greater than 3 500 MSPS; or 2. A resolution of 12 bit or more with an 'adjusted update rate' of greater than 1 250 MSPS and having any of the following: a. A settling time less than 9 ns to 0,024 % of full scale from a full scale step; or	
3A001.a.14	14. 積體電路執行下列所有特性： a. 類比－數位轉換器具下列任一特性： 1. 解析度為 8 位元或以上，但小於 10 位元，取樣輸入率大於每秒 1.3 十億次取樣(GSPS)；	14. 積體電路執行或可程式化執行下列所有特性： a. 類比－數位轉換器具下列任一特性： 1. 解析度為 8 位元或以上，但小於 10 位元，〝取樣率〞大於每秒	14. Integrated circuits that perform all of the following: a. Analogue-to-digital conversions meeting any of the following: 1. A resolution of 8 bit or more,	14. Integrated circuits that perform or are programmable to perform all of the following: a. Analogue-to-digital conversions meeting any of the following: 1. A resolution of 8 bit or more, but less than 10 bit, with a "sample rate" greater than 1,3 Giga

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	2. 解析度為 10 位元或以上，但小於 12 位元，取樣輸入率大於每秒 1.0 十億次取樣(GSPS)； 3. 解析度為 12 位元或以上，但小於 14 位元，取樣輸入率大於每秒 1.0 十億次取樣(GSPS)； 4. 解析度為 14 位元或以上，但小於 16 位元，取樣輸入率大於每秒 400 百萬次取樣(MSPS)；或 5. 解析度為 16 位元或以上，取樣輸入率大於每秒 180 百萬次取樣(MSPS)；及 b.具下列任一特性者： 1. 儲存數位化資料；或 2. 處理數位化資料； 說明 1：類比－數位轉換器積體電路，參考 3A001.a.5.a.。 說明 2：現場可程式邏輯元件，參考 3A001.a.7.。 b. 微波或毫米波項目，如下： 技術註解： 1. 就 3A001.b.目的，飽和參數峰值輸出功率亦可以為產品數據表中所提及之輸出功率、飽和輸出功	1.3 十億次取樣(GSPS)； 2. 解析度為 10 位元或以上，但小於 12 位元，〝取樣率〞大於每秒 1.0 十億次取樣(GSPS)； 3. 解析度為 12 位元或以上，但小於 14 位元，〝取樣率〞大於每秒 1.0 十億次取樣(GSPS)； 4. 解析度為 14 位元或以上，但小於 16 位元，〝取樣率〞大於每秒 400 百萬次取樣(MSPS)；或 5. 解析度為 16 位元或以上，〝取樣率〞大於每秒 180 百萬次取樣(MSPS)；及 b.具下列任一特性者： 1. 儲存數位化資料；或 2. 處理數位化資料； 說明 1：類比－數位轉換器積體電路，參考 3A001.a.5.a.。 說明 2：現場可程式邏輯元件，參考 3A001.a.7.。 技術註解： 1.n 位元之解析度係對應於一個量子化的 2n 種狀態。 2. 輸出字的位元數相等於數位－	but less than 10 bit, with an input sample rate greater than 1,3 giga samples per second (GSPS); 2. A resolution of 10 bit or more, but less than 12 bit, with an input sample rate greater than 1,0 giga samples per second (GSPS); 3. A resolution of 12 bit or more, but less than 14 bit, with an input sample rate greater than 1,0 giga samples per second (GSPS); 4. A resolution of 14 bit or more, but less than 16 bit, with an input sample rate greater than 400 mega samples per second (MSPS); or 5. A resolution of 16 bit or more with an input sample rate greater than 180 mega samples per second (MSPS); and b. Any of the following: 1. Storage of digitised data; or 2. Processing of digitised data; N.B.1. For analogue-to-digital converter integrated circuits see	Samples Per Second (GSPS); 2. A resolution of 10 bit or more, but less than 12 bit, with a "sample rate" greater than 1,0 GSPS; 3. A resolution of 12 bit or more, but less than 14 bit, with a "sample rate" greater than 1,0 GSPS; 4. A resolution of 14 bit or more, but less than 16 bit, with a "sample rate" greater than 400 Mega Samples Per Second (MSPS); or 5. A resolution of 16 bit or more with a "sample rate" greater than 180 MSPS; and b. Any of the following: 1. Storage of digitised data; or 2. Processing of digitised data; N.B.1. For analogue-to-digital converter integrated circuits see 3A001.a.5.a. N.B.2. For field programmable logic devices see 3A001.a.7. Technicals Notes: 1. A resolution of n bit corresponds to a quantisation of 2 n levels. 2. The resolution of the ADC is the number of bits of the digital output of the ADC that represents

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	率、最大輸出功率、峰值輸出功率，或包絡線峰值輸出功率。 2. 就 3A001.b.1 目的，｀真空電子元件｀為基於電子束與電磁波在真空電路中傳遞的相互作用，或與無線電頻率真空空腔共振器的相互作用。｀真空電子設備｀包括調速管、行波管及其衍生物。	類比轉換器之解析度，有效位元數(ENOB)不用於判讀 ADC 之解析度。 3. 對於積體電路具非交錯式〝多頻道 ADCs〞而言，〝取樣率〞非匯總結果，且〝取樣率〞是指任何單一頻道之最大輸出率。 4. 對於積體電路具〝交錯式 ADCs〞或〝多頻道 ADCs〞其操作具有交錯模式者，〝取樣率〞為匯總結果，〝取樣率〞為所有交錯頻道之最大輸出率組合。	3A001.a.5.a. N.B.2. For field programmable logic devices see 3A001.a.7. b. Microwave or millimetre wave items as follows: Technical Notes: 1. For purposes of 3A001.b., the parameter peak saturated power output may also be referred to on product data sheets as output power, saturated power output, maximum power output, peak power output, or peak envelope power output. 2. For purposes of 3A001.b.1., 'vacuum electronic devices' are electronic devices based on the interaction of an electron beam with an electromagnetic wave propagating in a vacuum circuit or interacting with radio- frequency vacuum cavity resonators. 'Vacuum electronic devices' include klystrons, travelling-wave tubes,	the measured analogue input. Effective Number of Bits (ENOB) is not used to determine the resolution of the ADC. 3. For integrated circuits with non-interleaving "multiple channel ADCs", the "sample rate" is not aggregated and the "sample rate" is the maximum rate of any single channel. 4. For integrated circuits with "interleaved ADCs "or with "multiple channel ADCs" that are specified to have an interleaved mode of operation, the "sample rates" are aggregated and the "sample rate" is the maximum combined total rate of all of the interleaved channels.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			and their derivatives.	
3A001.b.2 註解	註解 2：額定操作頻率範圍橫跨一個以上 3A001.b.2.a.至 3A001.b.2.h.所定義頻率範圍之單晶微波積體電路(MMIC)，其管制狀況是根據其最低飽和峰值輸出功率之管制標準所決定。 註解 3:根據第 3 類 A 部分之註解 1 與註解 2，指 3A001.b.2.不管制專為其它用途(如電信、雷達、汽車)所設計之微波單晶積體電路。	註解 2：額定操作頻率範圍橫跨一個以上 3A001.b.2.a.至 3A001.b.2.h.所定義頻率範圍之單晶微波積體電路(〝MMIC〞)，其管制狀況是根據其最低飽和峰值輸出功率之管制標準所決定。 註解 3:根據第 3 類 A 部分之註解 1 與註解 2，指 3A001.b.2.不管制專為其它用途(如電信、雷達、汽車)所設計之微波單晶積體電路(〝MMIC〞)。	Note 2: The control status of the MMIC whose rated operating frequency includes frequencies listed in more than one frequency range, as defined by 3A001.b.2.a. to 3A001.b.2.h., is determined by the lowest peak saturated power output threshold. Note 3: Notes 1 and 2 in 3A mean that 3A001.b.2. does not control MMICs if they are specially designed for other applications, e.g., telecommunications, radar, automobiles.	Note 2: The control status of the "MMIC" whose rated operating frequency includes frequencies listed in more than one frequency range, as defined by 3A001.b.2.a. to 3A001.b.2.h., is determined by the lowest peak saturated power output threshold. Note 3: Notes 1 and 2 in 3A mean that 3A001.b.2. does not control "MMICs" if they are specially designed for other applications, e.g., telecommunications, radar, automobiles.
3A001.b.4 註解	說明 1：單晶微波積體電路(MMIC)放大器，參考 3A001.b.2.。 說明 2:、傳輸/接收模組ˊ與、傳輸模組ˊ，參考 3A001.b.12.。	說明 1：單晶微波積體電路(〝MMIC〞)放大器，參考 3A001.b.2.。 說明 2:、傳輸/接收模組ˊ與、傳輸模組ˊ，參考 3A001.b.12.。 說明 3：用於轉換器與諧波混合器，設計用於延伸訊號分析儀、訊號產生器、延伸網路分析儀、微波測試接收器等之操作或頻率範	N.B.1. MMIC amplifiers see 3A001.b.2. N.B.2. For 'transmit/receive modules' and 'transmit modules' see 3A001.b.12.	N.B.1. For "MMIC" amplifiers see 3A001.b.2. N.B.2. For 'transmit/receive modules' and 'transmit modules' see 3A001.b.12. N.B.3. For converters and harmonic mixers, designed to extend the operating or frequency range of signal analysers, signal generators, network analysers or microwave test receivers, see 3A001.b.7.

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		圍，參考 3A001.b.7.。		
3A001.b.11	11. 〝頻率合成器〞 〝電子組裝〞其具〝頻率切換時間〞如下任一所述： a. 低於 143 ps； b. 任何頻率變動超過 2.2 GHz，合成頻率範圍超過 4.8 GHz 但未超過 31.8 GHz 時，低於 100 μs； c. 刪除； d. 任何頻率變動超過 550 MHz，合成頻率範圍超過 31.8 GHz 但未超過 43.5 GHz 時，低於 500 μs； e. 任何頻率變動超過 2.2 GHz，合成頻率範圍超過 37 GHz 但未超過 90 GHz 時，低於 100 μs； f. 刪除；或 g. 合成頻率範圍超過 90 GHz 時，低於 1 ms； 說明：關於一般用途之〝訊號分析儀〞、訊號產生器、網路分析儀和微波測試接收器之定義，分別參見 3A002.c.、3A002.d.、 3A002.e.和 3A002.f.。	11. 〝頻率合成器〞 〝電子組裝〞其具〝頻率切換時間〞如下任一所述： a.低於 143 ps； b.任何頻率變動超過 2.2 GHz，合成頻率範圍超過 4.8 GHz 但未超過 31.8 GHz 時，低於 100 μs； c.刪除； d.任何頻率變動超過 550 MHz，合成頻率範圍超過 31.8 GHz 但未超過 43.5 GHz 時，低於 500 μs； e.任何頻率變動超過 2.2 GHz，合成頻率範圍超過 37 GHz 但未超過 90 GHz 時，低於 100 μs； f. 刪除；或 g. 合成頻率範圍超過 90 GHz 時，低於 1 ms； 技術註解： 〝頻率合成器〞係指任何種類頻率來源不論實際使用之技術，能由多個輸出提供多個同步或交替之輸出頻率，而該等頻率由較少數之標準(或主要)頻率所控制、產生或規	11. "Frequency synthesiser" "electronic assemblies" having a "frequency switching time" as specified by any of the following: a. Less than 143 ps; b. Less than 100 μs for any frequency change exceeding 2,2 GHz within the synthesised frequency range exceeding 4,8 GHz but not exceeding 31,8 GHz; c. Not used; d. Less than 500 μs for any frequency change exceeding 550 MHz within the synthesised frequency range exceeding 31,8 GHz but not exceeding 37 GHz; e. Less than 100 μs for any frequency change exceeding 2,2 GHz within the synthesised frequency range exceeding 37 GHz but not exceeding 90 GHz; f. Not used; or g. Less than 1 ms within the	11. 'Frequency synthesiser' "electronic assemblies" having a "frequency switching time" as specified by any of the following: a. Less than 143 ps; b. Less than 100 μs for any frequency change exceeding 2,2 GHz within the synthesised frequency range exceeding 4,8 GHz but not exceeding 31,8 GHz; c. Not used; d. Less than 500 μs for any frequency change exceeding 550 MHz within the synthesised frequency range exceeding 31,8 GHz but not exceeding 37 GHz; e. Less than 100 μs for any frequency change exceeding 2,2 GHz within the synthesised frequency range exceeding 37 GHz but not exceeding 90 GHz; or f. Not used; g. Less than 1 ms within the synthesized frequency range exceeding 90 GHz; Technical Note: A 'frequency synthesiser' is any kind of frequency source, regardless of the actual

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		範。	synthesized frequency range exceeding 90 GHz;	technique used, providing a multiplicity of simultaneous or alternative output frequencies, from one or more outputs, controlled by, derived from or disciplined by a lesser number of standard (or master) frequencies.
3A001.e.1	e. 如下之高能量元件： 1. 如下之｀電池芯｀； a. 在 20 °C 下｀能量密度｀超過 550 Wh/kg 之｀一次電池芯｀； b. 在 20 °C 下｀能量密度｀超過 350 Wh/kg 之｀二次電池芯｀。	e. 如下之高能量元件： 1. ｀電池芯｀，如下： a. ｀一次電池芯｀在 20℃時具下列任一特性； 1.｀能量密度｀超過 550 Wh/kg 及｀連續功率密度｀超過 50 W/kg；或 2.｀能量密度｀超過 50 Wh/kg 及｀連續功率密度｀超過 350 W/kg；或	e. High energy devices as follows: 1. 'Cells' as follows: a. 'Primary cells' having an 'energy density' exceeding 550 Wh/kg at 20 °C; b. 'Secondary cells' having an 'energy density' exceeding 350 Wh/kg at 20 °C;	e. High energy devices as follows: 1. 'Cells' as follows: a. 'Primary cells' having any of the following at 20 °C; 1. 'Energy density' exceeding 550 Wh/kg and a 'continuous power density' exceeding 50 W/kg; or 2. 'Energy density' exceeding 50 Wh/kg and a 'continuous power density' exceeding 350 W/kg; or
3A001.e.1 技術註解	無	5. 3A001.e.1.a.所述之｀連續功率密度｀(W/kg)，其計算方式是以額定電壓(伏特)乘以指定之最大連續放電電流(安培)除以重量(公斤)。｀連續功率密度｀也稱為比功率。	-	5. For the purpose of 3A001.e.1.a., 'continuous power density' (W/kg) is calculated from the nominal voltage multiplied by the specified maximum continuous discharge current in ampere (A) divided by the mass in kilograms. 'Continuous power density' is also referred to as specific power.
3A001.i	無	i. 強度，振幅或相位電光調變器，設計用於類比訊號，具下列任一特	-	i. Intensity, amplitude, or phase electro-optic modulators, designed for analogue signals and

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		性者： 1. 最大操作頻率超過 10 GHz 但未超過 20 GHz，光學介入損失等於或小於 3 dB，且具下列任一特性： a. ｀ 半波電壓´(｀Vπ´)在頻率 1 GHz 或以下時測量小於 2.7 V；或 b. ｀ 半波電壓´(｀Vπ´)在頻率 1 GHz 或以上時測量小於 4 V；或 2. 最大操作頻率等於或超過 20 GHz，光學介入損失等於或小於 3 dB，且具下列任一特性： a. ｀ 半波電壓´(｀Vπ´)在頻率 1 GHz 或以下時測量小於 3.3 V；或 b. ｀ 半波電壓´(｀Vπ´)在頻率 1 GHz 或以上時測量小於 5 V。 註解：3A001.i.包括具有光學輸入及輸出連接器的電光調變器(例如：光纖引線)。 技術註解： 3A001.i.所述之｀ 半波電壓´		having any of the following: 1. A maximum operating frequency of more than 10 GHz but less than 20 GHz, an optical insertion loss equal to or less than 3 dB and having any of the following: a. A 'half-wave voltage' ('Vπ') less than 2,7 V when measured at a frequency of 1 GHz or below; or b. A 'Vπ' of less than 4 V when measured at a frequency of more than 1 GHz; or 2. A maximum operating frequency equal to or greater than 20 GHz, an optical insertion loss equal to or less than 3 dB and having any of the following: a. A 'Vπ' less than 3,3 V when measured at a frequency of 1 GHz or below; or b. A 'Vπ' less than 5 V when measured at a frequency of more than 1 GHz. Note: 3A001.i. includes electro-optic modulators having optical input and output connectors (e.g., fibre-optic pigtails). Technical Note: For the purposes of 3A001.i., a 'half-wave voltage' ('Vπ') is the applied voltage

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		(｀Vπ｀)，指光通過光調變器時光波長產生 180 度相位改變所需要施加的電壓。		necessary to make a phase change of 180 degrees in the wavelength of light propagating through the optical modulator.
3A002.c	c. 如下之〝訊號分析儀〞： 1. 〝訊號分析儀〞 在任何地方超過 10 MHz 且具有 3 dB 解析頻寬(RBW)，其頻率超過 31.8 GHz，但不超過 37 GHz； 2. 〝訊號分析儀〞具有平均顯示雜訊位準(DNAL)在任何地方低於(優於)-150 dBm/Hz，其頻率超過 43.5 GHz 但不超過 90 GHz； 3. 〝訊號分析儀〞頻率超過 90 GHz； 4. 〝訊號分析儀〞具有下列所有特性： a.〝即時頻寬〞超過 170 MHz；及 b. 具下列任一特性： 1. 具 100%的發現率，於間隙或訊號的開窗效應持續時間為 15 μs 或以下，全振幅降低小於 3 dB； 2. 具有〝頻率遮罩觸發〞功能，其 100 %觸發(捕獲)訊號機率之持續時間為 15 μs 或以下；	c. 如下之〝訊號分析儀〞： 1. 〝訊號分析儀〞 在任何地方超過 40 MHz 且具有 3 dB 解析頻寬(RBW)，其頻率超過 31.8 GHz，但不超過 37 GHz； 2. 〝訊號分析儀〞具有平均顯示雜訊位準(DNAL)在任何地方低於(優於)-150 dBm/Hz，其頻率超過 43.5 GHz 但不超過 90 GHz； 3. 〝訊號分析儀〞頻率超過 90 GHz； 4. 〝訊號分析儀〞具有下列所有特性： a. ｀即時頻寬｀超過 170 MHz；及 b. 具下列任一特性： 1. 具 100%的發現率，於間隙或訊號的開窗效應持續時間為 15 μs 或以下，全振幅降低小於 3 dB； 2. 具有｀頻率遮罩觸發｀功能，其 100 %觸發(捕獲)訊號機率之持	c. "Signal analysers" as follows: 1. "Signal analysers" having a 3 dB resolution bandwidth (RBW) exceeding 10 MHz anywhere within the frequency range exceeding 31,8 GHz but not exceeding 37 GHz; 2. "Signal analysers" having Displayed Average Noise Level (DANL) less (better) than -150 dBm/Hz anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz; 3. "Signal analysers" having a frequency exceeding 90 GHz; 4. "Signal analysers" having all of the following: a. "Real-time bandwidth" exceeding 170 MHz; and b. Having any of the following; 1. 100 % probability of discovery with less than a 3 dB reduction from	c. "Signal analysers" as follows: 1. "Signal analysers" having a 3 dB resolution bandwidth (RBW) exceeding 40 MHz anywhere within the frequency range exceeding 31,8 GHz but not exceeding 37 GHz; 2. "Signal analysers" having Displayed Average Noise Level (DANL) less (better) than -150 dBm/Hz anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz; 3. "Signal analysers" having a frequency exceeding 90 GHz; 4. "Signal analysers" having all of the following: a. 'Real-time bandwidth' exceeding 170 MHz; and b. Having any of the following: 1. 100 % probability of discovery with less than a 3 dB reduction from full amplitude due to gaps or windowing effects of signals having a duration of 15 μs or less; or 2. A 'frequency mask trigger' function with 100 % probability of trigger (capture) for signals

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	技術註解： 1. 3A002.c.4.b.1.中之發現率也被稱為攔截率或捕獲率。 2.就 3A002.c.4.b.1.目的，100%發現率的持續時間，即指定量測不確定度所需之最低訊號持續時間。 註解：3A002.c.4.不管制僅使用固定比例頻寬濾波器(又稱倍頻或分倍頻濾波器)之〝訊號分析儀〞。	續時間為 15 μs 或以下； 技術註解： 1. 〝即時頻寬〞指分析儀可持續傳送時域數據轉換為頻域結果之最大頻寬範圍，利用傅立葉或其他離散時間轉換，其處理每一個輸入時間點，無因間隙或窗口效應，使測量振幅低於實際訊號振幅超過 3dB。 2. 3A002.c.4.b.1.中之發現率也被稱為攔截率或捕獲率。 3.就 3A002.c.4.b.1.目的，100%發現率的持續時間，即指定量測不確定度所需之最低訊號持續時間。 4. 〝頻率遮罩觸發〞指訊號分析儀之一個機制，其觸發功能可選擇一個頻率範圍作為擷取頻寬的一個子集，而可忽略其他可能在同一擷取頻寬內之信號。一個〝頻率遮罩觸發〞可能有多於一個獨立限制的設置。	full amplitude due to gaps or windowing effects of signals having a duration of 15 μs or less; or 2. A "frequency mask trigger" function with 100 % probability of trigger (capture) for signals having a duration of 15 μs or less; Technical Notes: 1. Probability of discovery in 3A002.c.4.b.1. is also referred to as probability of intercept or probability of capture. 2. For the purposes of 3A002.c.4.b.1., the duration for 100 % probability of discovery is equivalent to the minimum signal duration necessary for the specified level measurement uncertainty.	having a duration of 15 μs or less; Technical Notes: 1. 'Real-time bandwidth' is the widest frequency range for which the analyser can continuously transform time-domain data entirely into frequency-domain results, using a Fourier or other discrete time transform that processes every incoming time point, without a reduction of measured amplitude of more than 3 dB below the actual signal amplitude caused by gaps or windowing effects, while outputting or displaying the transformed data. 2. Probability of discovery in 3A002.c.4.b.1. is also referred to as probability of intercept or probability of capture. 3. For the purposes of 3A002.c.4.b.1., the duration for 100 % probability of discovery is equivalent to the minimum signal duration necessary for the specified level measurement uncertainty. 4. A 'frequency mask trigger' is a mechanism where the trigger function is able to select a frequency range to be triggered on as a subset of the acquisition bandwidth while ignoring

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				other signals that may also be present within the same acquisition bandwidth. A 'frequency mask trigger' may contain more than one independent set of limits.
3A002.h	h. 〝電子組裝〞、模組或設備，特別為執行下列所有特性者： 1. 類比-數位轉換符合下列任一者： a. 解析度為 8 位元或以上，但小於 10 位元，輸入率大於每秒 1,300 百萬字； b. 解析度為 10 位元或以上，但小於 12 位元，輸入率大於每秒 1,000 百萬字； c. 解析度為 12 位元或以上，但小於 14 位元，輸入率大於每秒 1,000 百萬字； d. 解析度大於 14 位元，但小於或等於 16 位元，輸入率大於每秒 400 百萬字；或 e. 解析度大於 16 位元，輸入率大於每秒 180 百萬字；及	h. 〝電子組裝〞、模組或設備，特別為執行下列所有特性者： 1. 類比－數位轉換符合下列任一者： a. 解析度為 8 位元或以上，但小於 10 位元，〝取樣率〞大於每秒 1.3 十億次取樣(GSPS)； b. 解析度為 10 位元或以上，但小於 12 位元，〝取樣率〞大於每秒 1.0 十億次取樣(GSPS)； c. 解析度為 12 位元或以上，但小於 14 位元，〝取樣率〞大於每秒 1.0 十億次取樣(GSPS)； d. 解析度大於 14 位元，但小於或等於 16 位元，〝取樣率〞大於每秒 400 百萬次取樣(MSPS)；或 e. 解析度大於 16 位元，〝取樣率〞大於每秒 180 百萬次取樣(MSPS)；及	h. "Electronic assemblies", modules, or equipment, specified to perform all of the following: 1. Analogue-to-digital conversions meeting any of the following: a. A resolution of 8 bit or more, but less than 10 bit, with an input sample rate greater than 1 300 million samples per second; b. A resolution of 10 bit or more, but less than 12 bit, with an input sample rate greater than 1 000 million samples per second; c. A resolution of 12 bit or more, but less than 14 bit, with an input sample rate greater than 1 000 million samples per second; d. A resolution of 14 bit or more but less than 16 bit, with an input	h. "Electronic assemblies", modules, or equipment, specified to perform all of the following: 1. Analogue-to-digital conversions meeting any of the following: a. A resolution of 8 bit or more, but less than 10 bit, with a "sample rate" greater than 1,3 Giga Samples Per Second (GSPS); b. A resolution of 10 bit or more, but less than 12 bit, with a "sample rate" greater than 1,0 GSPS; c. A resolution of 12 bit or more, but less than 14 bit, with a "sample rate" greater than 1,0 GSPS; d. A resolution of 14 bit or more but less than 16 bit, with a "sample rate" greater than 400 Mega Samples Per Second (MSPS); or e. A resolution of 16 bit or more with a "sample rate" greater than 180 MSPS; andEN

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			sample rate greater than 400 million samples per second; or e. A resolution of 16 bit or more with an input sample rate greater than 180 million samples per second; and	
3A002.h 技術註解	技術註解： 多頻道〝電子組裝〞或模組之管制狀態由單一頻道最高性能決定。	技術註解： 1.n 位元之解析度係對應於一個量子化的 2n 種狀態。 2. 輸出字的位元數相等於數位一類比轉換器之解析度，有效位元數(ENOB)不用於判讀 ADC 之解析度。 3. 對於非交錯式多頻道〝電子組裝〞、模組或設備而言，〝取樣率〞非匯總結果，且〝取樣率〞是指任何單一頻道之最大輸出率。 4. 對於交錯式多頻道〝電子組裝〞、模組或設備而言，〝取樣率〞為匯總結果，〝取樣率〞為所有交錯頻道之最大輸出率組合。	Technical Note: For multiple-channel "electronic assemblies" or modules, control status is determined by the highest single-channel specified performance.	Technical Notes: 1. A resolution of n bit corresponds to a quantisation of 2 n levels. 2. The resolution of the ADC is the number of bits of the digital output of the ADC that represents the measured analogue input. Effective Number of Bits (ENOB) is not used to determine the resolution of the ADC. 3. For non-interleaved multiple-channel "electronic assemblies", modules, or equipment, the "sample rate" is not aggregated and the "sample rate" is the maximum rate of any single-channel. 4. For interleaved channels on multiple-channel "electronic assemblies", modules, or equipment, the "sample rates" are aggregated and the "sample rate" is the maximum combined total rate of all the interleaved channels.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
3A233	3A233　除 0B002.g.所述以外之如下質譜儀,能夠量測 230 原子質量單位或以上之離子,且其解析度優於 2/230，及其離子源：	3A233　除 0B002.g.所述以外之如下質譜儀，能夠量測 230 u 或以上之離子，且其解析度優於 2/230，及其離子源：	3A233 Mass spectrometers, other than those specified in 0B002.g., capable of measuring ions of 230 atomic mass units or greater and having a resolution of better than 2 parts in 230, as follows, and ion sources therefor:	3A233 Mass spectrometers, other than those specified in 0B002.g., capable of measuring ions of 230 u or greater and having a resolution of better than 2 parts in 230, as follows, and ion sources therefor:
3B001	h. 具相位移層之多層光罩，未由 3B001.g.規範且具有下列任一特性： 1. 以玻璃光罩〝空白基板〞製成其雙折射小於 7 nm/cm；或 2. 設計用於微影製程設備其光源波長小於 245 nm； 註解：3B001.h.不管制為製造不受 3A001 所管制之記憶體元件而設計具相位移層之多層光罩。 i. 設計用於 3A001 所述之積體電路之壓模微影模板。	h. 具相位移層之多層光罩，未在 3B001.g.中規範且具下列任一特性： 1. 以玻璃光罩〝空白基板〞製成其雙折射小於 7 nm/cm；或 2. 設計用於微影製程設備其光源波長小於 245 nm； 註解：3B001.h.不管制為製造不受 3A001 所管制之記憶體元件而設計具相位移層之多層光罩。 i. 設計用於 3A001 所述之積體電路之壓模微影模板； j. 光罩〝毛坯基板〞具由鉬與矽製成的多層反射結構,且具下列所有特性： 1. 特別設計為〝極紫外線(EUV)〞微影製程；及	h. Multi-layer masks with a phase shift layer not specified by 3B001.g. and having any of the following: 1. Made on a mask "substrate blank" from glass specified as having less than 7 nm/cm birefringence; or 2. Designed to be used by lithography equipment having a light source wavelength less than 245 nm; Note: 3B001.h. does not control multi-layer masks with a phase shift layer designed for the fabrication of memory devices not controlled by 3A001. i. Imprint lithography templates	h. Multi-layer masks with a phase shift layer not specified in 3B001.g. and having any of the following: 1. Made on a mask "substrate blank" from glass specified as having less than 7 nm/cm birefringence; or 2. Designed to be used by lithography equipment having a light source wavelength less than 245 nm; Note: 3B001.h. does not control multi-layer masks with a phase shift layer designed for the fabrication of memory devices not specified in 3A001. i. Imprint lithography templates designed for integrated circuits specified in 3A001. j. Mask "substrate blanks" with multilayer reflector structure consisting of molybdenum and

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		2. 符合 SEMI 之 P37 標準。 技術註解： ｀極紫外線(EUV) ´指大於 5 nm 而小於 124 nm 的電磁譜波長。	designed for integrated circuits specified in 3A001.	silicon, and having all of the following: 1. Specially designed for 'Extreme Ultraviolet' ('EUV') lithography; and 2. Compliant with SEMI Standard P37. Technical Note: 'Extreme Ultraviolet' ('EUV') refers to electromagnetic spectrum wavelengths greater than 5 nm and less than 124 nm.
3B002	a. 為測試頻率超過 31.8 GHz 電晶體元件之 S-參數者； b. 刪除； c. 為測試 3A001.b.2.所述之微波積體電路者。	a. 為測試 3A001.b.3 所述項目之 S-參數者； b. 刪除； c. 為測試 3A001.b.2.所述項目者。	a. For testing S-parameters of transistor devices at frequencies exceeding 31,8 GHz; b. Not used; c. For testing microwave integrated circuits specified in 3A001.b.2.	a. For testing S-parameters of items specified in 3A001.b.3.; b. Not used; c. For testing items specified in 3A001.b.2.
3C002.a	1. 特別調整(最佳化)之正光阻，其使適用於波長小於 245 nm，但等於或大於 15 nm；	1. 特別調整(最佳化)之正光阻，其使適用於波長小於 193 nm，但等於或大於 15 nm；	1. Positive resists adjusted (optimised) for use at wavelengths less than 245 nm but equal to or greater than 15 nm;	1. Positive resists adjusted (optimised) for use at wavelengths less than 193 nm but equal to or greater than 15 nm;
3C005	3C005　碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)或氮化鋁鎵(AlGaN)之半導體〝基板〞，或錠、圓柱狀、其它型態之上述材料，在 20 °C 時電阻率大於 10,000	3C005　高電阻材料，如下： a. 碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)或氮化鋁鎵(AlGaN)之半導體〝基板〞，或錠、圓柱狀、其它型態之上述材料，在	3C005 Silicon carbide (SiC), gallium nitride (GaN), aluminium nitride (AlN) or aluminium gallium nitride (AlGaN) semiconductor "substrates", or ingots, boules,	3C005 High resistivity materials as follows: a. Silicon carbide (SiC), gallium nitride (GaN), aluminium nitride (AlN) or aluminium gallium nitride (AlGaN) semiconductor "substrates", or ingots, boules, or other preforms of those

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	ohm-cm 者。	20 °C 時電阻率大於 10,000 ohm-cm 者； b. 多晶〝基板〞或多晶陶瓷〝基板〞，在 20 °C 時電阻率大於 10,000 ohm-cm，且〝基板〞表面具至少一層矽(Si)、碳化矽晶圓(SiC)、氮化鎵(GaN)、氮化鋁(AlN)或氮化鋁鎵(AlGaN)的非外延單晶層。	or other preforms of those materials, having resistivities greater than 10 000 ohm-cm at 20 °C.	materials, having resistivities greater than 10 000 ohm-cm at 20 °C; b. Polycrystalline "substrates" or polycrystalline ceramic "substrates", having resistivities greater than 10 000 ohm-cm at 20 °C and having at least one non-epitaxial single-crystal layer of silicon (Si), silicon carbide (SiC), gallium nitride (GaN), aluminium nitride (AlN), or aluminium gallium nitride (AlGaN) on the surface of the "substrate".
3C006	3C006　3C005 所述〝基板〞，至少有一個磊晶層為碳化矽，氮化鎵，氮化鋁或氮化鋁鎵。	3C006　未在 3C001 中所述之材料，含有 3C005 所述〝基板〞，至少有一個磊晶層為碳化矽，氮化鎵，氮化鋁或氮化鋁鎵。	3C006 "Substrates" specified in 3C005 with at least one epitaxial layer of silicon carbide, gallium nitride, aluminium nitride or aluminium gallium nitride.	3C006 Materials, not specified in 3C001, consisting of a "substrate" specified in 3C005 with at least one epitaxial layer of silicon carbide, gallium nitride, aluminium nitride or aluminium gallium nitride.
3E001 註解	無	註解 3：3E001 不管制〝製程設計套件〞(〝PDKs〞) 除非其包括可實現 3A001 所述項目之功能或技術者。	-	Note 3: 3E001 does not control 'Process Design Kits' ('PDKs') unless they include libraries implementing functions or technologies for items specified in 3A001.
3E001 技術註解	無	技術註解： 〝製程設計套件〞(〝PDKs〞)為半導體製造商所提供之軟體工具，用以確保必要的設計作法與規則，以能在特定半導體製程中根據	-	Technical Note: A 'Process Design Kit' ('PDK') is a software tool provided by a semiconductor manufacturer to ensure that the required design practices and rules are taken into account in order to

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		技術和製造限制，成功的生產積體電路(每個半導體製程都有其特定的〝PDK〞)。		successfully produce a specific integrated circuit design in a specific semiconductor process, in accordance with technological and manufacturing constraints (each semiconductor manufacturing process has its particular 'PDK').
4A 註解	註解 2：直接與中央處理器之匯流排或通道、〝主儲存體〞或磁碟控制器連結之控制單元，不被視為第 5 類第 1 部分(電信)所述之電信設備。	註解 2：直接與中央處理器之匯流排或通道、〝主儲存體〞或磁碟控制器連結之控制單元，不被視為第 5 類第 1 部分(電信)所述之電信設備。	Note 2: Control units which directly interconnect the buses or channels of central processing units, "main storage" or disk controllers are not regarded as telecommunications equipment described in Category 5, Part 1 (Telecommunications).	Note 2: Control units which directly interconnect the buses or channels of central processing units, 'main storage' or disk controllers are not regarded as telecommunications equipment described in Category 5, Part 1 (Telecommunications).
4A 技術註解	無	技術註解： 〝主儲存體〞指由中央處理器快速存取之主要資料或指令儲存裝置。其由〝數位電腦〞內部儲存裝置及其分級延伸部分所組成，如高速緩衝儲存裝置或非序列存取延伸儲存裝置。	-	Technical Note: 'Main storage' is the primary storage for data or instructions for rapid access by a central processing unit. It consists of the internal storage of a "digital computer" and any hierarchical extension thereto, such as cache storage or non-sequentially accessed extended storage.
4A003.b	b. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過每秒 16 加權兆(10^{12})浮點運算(WT)者；	b. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過每秒 29 加權兆(10^{12})浮點運算(WT)者；	b. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 16 Weighted	b. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 29 Weighted TeraFLOPS (WT);

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			TeraFLOPS (WT);	
4A004	4A004　電腦及特別設計之相關設備、〝電子組件〞及其零件如下： a. 〝脈動陣列電腦〞； b. 〝類神經電腦〞； c. 〝光學電腦〞。	4A004　電腦及特別設計之相關設備、〝電子組件〞及其零件如下： a. ｀脈動陣列電腦｀； b. ｀類神經電腦｀； c. ｀光學電腦｀。 技術註解： 1. ｀脈動陣列電腦｀指可由使用者在邏輯閘層次機動控制資料流通與修改之電腦。 2. ｀類神經電腦｀指設計或修改以模仿神經細胞或一群神經細胞之行為之計算裝置，即此計算裝置以其硬體性能區別其特色，而此硬體可依據以往資料調整多重計算組件之重量與其互連數目。 3. ｀光學電腦｀指設計或修改以使用光呈現資料之電腦，其邏輯運算元件以直接耦合光學裝置為基礎。	4A004 Computers as follows and specially designed related equipment, "electronic assemblies" and components therefor: a. "Systolic array computers"; b. "Neural computers"; c. "Optical computers". Technical Notes: 1. 'Systolic array computers' are computers where the flow and modification of the data is dynamically controllable at the logic gate level by the user. 2. 'Neural computers' are computational devices designed or modified to mimic the behaviour of a neuron or a collection of neurons, i.e., computational devices which are distinguished by their hardware capability to modulate the weights and numbers of the interconnections of a multiplicity of computational components based on previous data. 3. 'Optical computers' are computers designed or modified to use light to represent data and whose computational logic elements are based on directly coupled optical devices.	4A004 Computers as follows and specially designed related equipment, "electronic assemblies" and components therefor: a. 'Systolic array computers'; b. 'Neural computers'; c. 'Optical computers'. Technical Notes: 1. 'Systolic array computers' are computers where the flow and modification of the data is dynamically controllable at the logic gate level by the user. 2. 'Neural computers' are computational devices designed or modified to mimic the behaviour of a neuron or a collection of neurons, i.e., computational devices which are distinguished by their hardware capability to modulate the weights and numbers of the interconnections of a multiplicity of computational components based on previous data. 3. 'Optical computers' are computers designed or modified to use light to represent data and whose computational logic elements are based on directly coupled optical devices.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
4D001.b.1	1. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過 8.0 加權兆浮點運算(WT)者；	1. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過 15 加權兆浮點運算(WT)者；	1. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 8,0 Weighted TeraFLOPS (WT);	1. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 15 Weighted TeraFLOPS (WT);
4D004 註解	無	註解： 4D004 不管制特別設計僅限於提供〝軟體〞更新或升級之〝軟體〞，具下列所有特性： a. 更新與升級操作僅在系統所有者或管理員授權下進行；及 b. 在更新與升級後，〝軟體〞之更新或升級不具下列任一特性： 1. 4D004 所述之〝軟體〞，或 2. 〝入侵軟體〞	-	Note: 4D004 does not control "software" specially designed and limited to provide "software" updates or upgrades meeting all the following: a. The update or upgrade operates only with the authorisation of the owner or administrator of the system receiving it; and b. After the update or upgrade, the "software" updated or upgraded is not any of the following: 1. "Software" specified in 4D004; or 2. "Intrusion software".
4E001.b.1	1. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過 8.0 加權兆浮點運算(WT)者；	1. 〝數位電腦〞具有〝調整尖峰效能〞(〝APP〞)超過 15 加權兆浮點運算(WT)者；	1. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 8,0 Weighted TeraFLOPS (WT);	1. "Digital computers" having an "Adjusted Peak Performance" ("APP") exceeding 15 Weighted TeraFLOPS (WT);
4E001 註解	無	註解 1：4E001.a.與 4E001.c.不管制〝弱點公開〞或〝網路事件應變〞。 註解 2：註解 1 不會減損會員國主管機關之權利，出口商應確立符合	-	Note 1: 4E001.a. and 4E001.c. do not control 'vulnerability disclosure' or 'cyber incident response'. Note 2: Note 1 does not diminish the rights of the competent authority of the Member State in

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		4E001.a.與 4E001.c.規範。		which the exporter is established to ascertain compliance with 4E001.a. and 4E001.c.
4E001 技術註解	無	技術註解： 1. ｀弱點公開｀指以解決漏洞為目的，由負責處理的個人或組織或協同處者進行識別，報告或傳播漏洞或分析漏洞的過程。 2. ｀網路事件應變｀指解決網路安全事件時，由負責處理的個人或組織或協同處者在網路安全事件上交換必要訊息的過程。	-	Technical Notes: 1. 'Vulnerability disclosure' means the process of identifying, reporting, or communicating a vulnerability to, or analysing a vulnerability with, individuals or organizations responsible for conducting or coordinating remediation for the purpose of resolving the vulnerability. 2. 'Cyber incident response' means the process of exchanging necessary information on a cyber security incident with individuals or organizations responsible for conducting or coordinating remediation to address the cyber security incident.
5A001	3. 為在溫度 218 K (-55 ˚C)至 397 K (124 ˚C)範圍之外操作而特別設計者。 註解:5A001.a.2.及 5A001.a.3.不管制為衛星上使用而設計或修改之設備。	3. 為在溫度低於 218 K (-55 ˚C)操作而特別設計者；或 4. 為在溫度高於 397 K (124 ˚C)操作而特別設計者； 註解 1：5A001.a.3.與 5A001.a.4.僅管制電子設備。 註解 2：5A001.a.2.、5A001.a.3.及 5A001.a.4.不管制設計或改裝用於衛星上使用之設備。	3. Specially designed to operate outside the temperature range from 218 K (- 55 ˚C) to 397 K (124 ˚C); Note: 5A001.a.3. applies only to electronic equipment. Note: 5A001.a.2. and 5A001.a.3. do not control equipment designed or modified for use on board satellites.	3. Specially designed to operate below 218 K (-55 ˚C); or 4. Specially designed to operate above 397 K (124 ˚C); Note 1: 5A001.a.3. and 5A001.a.4. control only electronic equipment. Note 2: 5A001.a.2., 5A001.a.3. and 5A001.a.4. do not control equipment designed or modified for use on board satellites.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
5A001.d	d. 〝電子操控相位陣列天線〞，如下：	d. 〝電子操控相位陣列天線〞，如下：	d. "Electronically steerable phased array antennae" as follows:	d. 'Electronically steerable phased array antennae' as follows:
5A001.d 註解	註解：5A001.d.不管制包含微波著陸系統(MLS)，符合 ICAO 標準之儀器的著陸系統用〝電子操控相位陣列天線〞。	註解 1：5A001.d.不管制包含微波著陸系統(MLS)，符合 ICAO 標準之儀器的著陸系統用〝電子操控相位陣列天線〞。 註解 2：5A001.d.不管制天線，其特別設計為下列任一者： a. 民用蜂巢式或 WLAN 無線電通信系統； b. IEEE 802.15 或無線 HDMI；或 c.商業民用電信用固定或移動式衛星地面接收站。	Note: 5A001.d. does not control "electronically steerable phased array antennae" for landing systems with instruments meeting ICAO standards covering Microwave Landing Systems (MLS).	Note 1: 5A001.d. does not control 'electronically steerable phased array antennae' for landing systems with instruments meeting ICAO standards covering Microwave Landing Systems (MLS). Note 2: 5A001.d. does not control antennae specially designed for any of the following: a. Civil cellular or WLAN radio-communications systems; b. IEEE 802.15 or wireless HDMI; or c. Fixed or mobile satellite earth stations for commercial civil telecommunications.
5A001.d 技術註解	無	技術註解： 就 5A001.d. 而言，〝電子操控相位陣列天線〞指以相位耦合方式形成波束之天線，例如波束方向由輻射元件之複雜激發係數控制，且應用電子訊號之傳輸與接收，波束方向之方位或高度，或二者均可改變。	-	Technical Note: For the purposes of 5A001.d. 'electronically steerable phased array antenna' is an antenna which forms a beam by means of phase coupling, (i.e., the beam direction is controlled by the complex excitation coefficients of the radiating elements) and the direction of that beam can be varied (both in transmission and reception) in azimuth or in elevation, or both, by application of an electrical signal.

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5A002.a	a. 設計或修改用於〝資料機密性密碼學〞，其具等於或超過 56 位元對稱金鑰長度，其密碼能夠在不需〝密碼啟用〞下使用或已經被啟用，如下：	a. 設計或修改用於〝資料機密性密碼學〞，其具等於或超過 56 位元對稱金鑰長度，其密碼功能能夠以不使用安全機制的〝密碼啟用〞進行使用、已經啟用或能夠啟用，如下：	a. Designed or modified to use 'cryptography for data confidentiality' having' in excess of 56 bits of symmetric key length, or equivalent', where that cryptographic capability is usable without "cryptographic activation" or has been activated, as follows:	a. Designed or modified to use 'cryptography for data confidentiality' having' in excess of 56 bits of symmetric key length, or equivalent', where that cryptographic capability is usable, has been activated, or can be activated by means of "cryptographic activation" not employing a secure mechanism, as follows:
5A002.b	b. 透過〝密碼啟用〞設計或改裝，使原本未達到 5A002.a.所述之項目能夠超過管制之性能水準。	b. 透過〝密碼啟用〞設計或改裝用於轉換者，未由第 5 類第 2 部分所述之項目，至 5A002.a.或 5D002.c.1.所述之項目，且非由密碼註解所發布者(第 5 類第 2 部分註解 3)，或是透過〝密碼啟用〞附加功能進行啟動，其由 5A002.a.所述之項目，已在第 5 類第 2 部分中所述。	b. Designed or modified to enable, by means of "cryptographic activation" an item to achieve or exceed the controlled performance levels for functionality specified in 5A002.a. that would not otherwise be enabled.	b. Designed or modified for converting, by means of "cryptographic activation", an item not specified in Category 5 - Part 2 into an item specified in 5A002.a. or 5D002.c.1., and not released by the Cryptography Note (Note 3 in Category 5 - Part 2), or for enabling, by means of "cryptographic activation", additional functionality specified in 5A002.a. of an item already specified in Category 5 - Part 2;
5D002.b	b. 設計或改裝之〝軟體〞由〝密碼啟用〞所啟動，項目符合 5A002.a.所管制之功能性規範，否則無法運作；	b. 透過〝密碼啟用〞設計或改裝用於轉換之〝軟體〞，其未由第 5 類第 2 部分所述之項目，至 5A002.a.或 5D002.c.1.所述之項目，且非由密碼註解所發布者(第 5 類第 2 部分註解 3)，或是透過〝密	b. "Software" designed or modified to enable, by means of "cryptographic activation", an item to meet the criteria for functionality specified by 5A002.a., that would not otherwise	b. "Software" designed or modified for converting, by means of "cryptographic activation", an item not specified in Category 5 - Part 2 into an item specified in 5A002.a. or 5D002.c.1., and not released by the Cryptography Note (Note 3 in Category 5 - Part

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		碼啟用〞附加功能進行啟動，其由5A002.a.所述之項目，已在第5類第2部分中所述。	be met;	2), or for enabling, by means of "cryptographic activation", additional functionality specified in 5A002.a. of an item already specified in Category 5 - Part 2;
5E002.b	b. 透過〝密碼啟用〞設計或改裝之〝技術〞，使原本無法達到5A002.a.所述之功能標準的項目，能夠達到管制的標準。	b. 透過〝密碼啟用〞用於轉換之〝技術〞，其未由第5類第2部分所述之項目，至5A002.a.或5D002.c.1.所述之項目，且非由密碼註解所發布者(第5類第2部分註解3)，或是透過〝密碼啟用〞附加功能進行啟動，其由5A002.a.所述之項目，已在第5類第2部分中所述。	b. "Technology" to enable, by means of "cryptographic activation", an item to meet the criteria for functionality specified by 5A002.a., that would not otherwise be met.	b. "Technology" for converting, by means of "cryptographic activation", an item not specified in Category 5 - Part 2 into an item specified in 5A002.a. or 5D002.c.1., and not released by the Cryptography Note (Note 3 in Category 5 - Part 2), or for enabling, by means of "cryptographic activation", additional functionality specified in 5A002.a. of an item already specified in Category 5 - Part 2;
6A002.f	無	f. 〝讀出積體電路〞(〝ROIC〞)特別設計用於6A002.a.3.所述之〝焦面陣列〞。 註解：6A002.f.不管制特別設計為民用汽車應用的〝讀出積體電路〞者。 技術註解： 〝讀出積體電路〞(〝ROIC〞)指積體電路設計用於支持或結合〝焦面陣列〞(〝FPA〞)，其使用於讀出(即擷取與暫存)探測元件所產	-	f. 'Read-out integrated circuits' ('ROIC') specially designed for "focal plane arrays" specified in 6A002.a.3. Note: 6A002.f. does not control 'read-out integrated circuits' specially designed for civil automotive applications. Technical Note: A 'Read-Out Integrated Circuit' ('ROIC') is an integrated circuit designed to underlie or be bonded to a "focal plane array" ("FPA") and used to read-out (i.e., extract and register) signals

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		生的訊號，最低限度的｀ROIC´能透過擷取方式由探測元件讀取電荷，與應用多工功能方式維持探測元件中相對空間位置與方向資訊，以利在｀ROIC´內部或外部進行處理。		produced by the detector elements. At a minimum the 'ROIC' reads the charge from the detector elements by extracting the charge and applying a multiplexing function in a manner that retains the relative spatial position and orientation information of the detector elements for processing inside or outside the 'ROIC'.
6A003.a	a. 儀器用照相機及其特別設計之零件，如下： 註解：6A003.a.3.至 6A003.a.5.所述，具有模組構造之儀器用照相機，需根據該照相機製造商之產品規格，以外接物件所提供之最大功能來評量。	a. 儀器用照相機及其特別設計之零件，如下： 註解：6A003.a.3.至 6A003.a.5.所述，具有模組構造之儀器用照相機，需根據該照相機製造商之產品規格，以外接物件所提供之最大功能來評量。 1. 刪除； 2. 刪除； 3. 電子式高速掃描攝影機時間解析度優於 50 ns；	a. Instrumentation cameras and specially designed components therefor, as follows: Note: Instrumentation cameras, specified in 6A003.a.3. to 6A003.a.5., with modular structures should be evaluated by their maximum capability, using plug-ins available according to the camera manufacturer's specifications.	a. Instrumentation cameras and specially designed components therefor, as follows: Note: Instrumentation cameras, specified in 6A003.a.3. to 6A003.a.5., with modular structures should be evaluated by their maximum capability, using plug-ins available according to the camera manufacturer's specifications. 1. Not used; 2. Not used; 3. Electronic streak cameras having temporal resolution better than 50 ns;
6A004.a.1	1. 〝可變形鏡面〞主動光學孔徑大於 10 mm 及具下列任一特性者，以及為其特別設計之零件：	1. ｀可變形鏡面´主動光學孔徑大於 10 mm 及具下列任一特性者，以及為其特別設計之零件：	1. "Deformable mirrors" having an active optical aperture greater than 10 mm and having any of the following,, and specially designed components therefor,	1. 'Deformable mirrors' having an active optical aperture greater than 10 mm and having any of the following, and specially designed components therefor,
6A004.a.1	無	技術註解：	-	Technical Note:

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
技術註解		〝可變形鏡面〞為鏡片具下列任一特性者： a. 對單一連續光反射表面施加個別扭力或力，產生動態變形，以補償因光波投射於鏡面所引起之變形；或 b. 具有多重光反射元件，經由施加扭力或力，可單獨且機動地重新定位，以補償因光波投射於鏡面所引起之變形。 〝可變形鏡面〞亦稱為自動補償光學鏡面。		'Deformable mirrors' are mirrors having any of the following: a. A single continuous optical reflecting surface which is dynamically deformed by the application of individual torques or forces to compensate for distortions in the optical waveform incident upon the mirror; or b. Multiple optical reflecting elements that can be individually and dynamically repositioned by the application of torques or forces to compensate for distortions in the optical waveform incident upon the mirror. 'Deformable mirrors' are also known as adaptive optic mirrors.
6A004.f	無	f. 動態波前測量設備，具下列所有特性： 1. 〝成幀速率〞等於或大於 1 KHz；及 2. 在設計波長處波前準確度等或小(優)於λ/20。 技術註解： 6A004.f.所述之〝成幀速率〞為在〝焦面陣列〞中整合所有〝主動像素〞，由波前光學感知器投射以錄	-	f. Dynamic wavefront measuring equipment having all of the following: 1. 'Frame rates' equal to or more than 1 kHz; and 2. A wavefront accuracy equal to or less (better) than λ/20 at the designed wavelength. Technical Note: For the purposes of 6A004.f., 'frame rate' is a frequency at which all "active pixels" in the "focal plane array" are integrated for recording images projected by the wavefront sensor optics.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		製影像的頻率。		
6A005.a.6.b.2 註解	註解 1：6A005.a.6.b.不管制多橫向模式、輸出功率超過 2 kW，但不超過 6 kW，且總質量大於 1,200 kg 之工業用〝雷射〞。就此註解之目的而言，總質量包括操作〝雷射〞所需所有之零件，例如〝雷射〞、電源供應器、熱交換器，但不包括光束調整及/或傳送之外接光學儀器。	註解 1：6A005.a.6.b.不管制多橫向模式、輸出功率超過 2 kW，但不超過 6 kW，且總質量大於 1,200 kg 之工業用〝雷射〞。就此註解之目的而言，總質量包括操作〝雷射〞所需所有之零件，例如〝雷射〞、電源供應器、熱交換器，但不包括光束調整或傳送之外接光學儀器。	Note 1: 6A005.a.6.b. does not control multiple transverse mode, industrial "lasers" with output power exceeding 2 kW and not exceeding 6 kW with a total mass greater than 1 200 kg. For the purpose of this note, total mass includes all components required to operate the "laser", e.g., "laser", power supply, heat exchanger, but excludes external optics for beam conditioning and/or delivery.	Note 1: 6A005.a.6.b. does not control multiple transverse mode, industrial "lasers" with output power exceeding 2 kW and not exceeding 6 kW with a total mass greater than 1 200 kg. For the purpose of this note, total mass includes all components required to operate the "laser", e.g., "laser", power supply, heat exchanger, but excludes external optics for beam conditioning or delivery.
6A005.d.5.c	c. 〝移轉雷射〞，如下： 1. 氧-碘(O2-I)〝雷射〞； 2. 氟化氘-二氧化碳(DF-CO2)〝雷射〞；	c. ｀移轉雷射´，如下： 1. 氧-碘(O2-I)〝雷射〞； 2. 氟化氘-二氧化碳(DF-CO2)〝雷射〞； 技術註解： ｀移轉雷射´指具雷射發光性能之原子或分子碰撞不具雷射發光性能之原子或分子，產生之能量移轉而激發的一種〝雷射〞。	c. "Transfer lasers" as follows: 1. Oxygen Iodine (O 2 -I) "lasers"; 2. Deuterium Fluoride-Carbon dioxide (DF-CO 2) "lasers";	c. 'Transfer lasers' as follows: 1. Oxygen Iodine (O 2 -I) "lasers"; 2. Deuterium Fluoride-Carbon dioxide (DF-CO 2) "lasers"; Technical Note: 'Transfer lasers' are "lasers" in which the lasing species are excited through the transfer of energy by collision of a non- lasing atom or molecule with a lasing atom or molecule species.
6A005.f	f. 光學設備，如下：	f. 光學設備，如下：	f. Optical equipment as follows:	f. Optical equipment as follows:

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	說明：可操作於〝超高功率雷射〞(〝SHPL〞)之應用的共用孔徑光學元件，參照軍用貨品管制。 1. 能在光束波前映射至少 50 個位置之動態波前(相位)測量設備，具有以下任一特性： a. 成幀速率等於或大於 100 Hz，且相位區分至少為光束波長的 5 %；或 b. 成幀速率等於或大於 1,000 Hz，且相位區分至少為光束波長的 20 %； 2. 〝雷射〞診斷設備，能測量〝SHPL〞系統之角向光束操縱誤差值等於或小於 10 μrad； 3. 特別設計為相位陣列〝SHPL〞系統之光學設備及零件，在特定波長下，其同調光束組合之〝準確度(或稱〝精度〞)〞為 1/10 波長或 0.1 μm 兩者之較小值者； 4. 為與〝SHPL〞系統共同使用而特別設計之投影式望遠鏡。	說明：可操作於〝超高功率雷射〞(〝SHPL〞)之應用的共用孔徑光學元件，參照軍用貨品管制。 1. 刪除； 2. 〝雷射〞診斷設備，特別設計為動態測量〝SHPL〞系統之角向光束操縱誤差值，且測量〝準確度(或稱〝精度〞)〞等於或小於(優於) 10 μrad (微弧度)； 3. 光學設備及零件，特別設計為相位陣列〝SHPL〞系統之同調光束組合，且具下列任一特性： a. 波長大於 1 μm 時，其〝準確度(或稱〝精度〞)〞等於或小於 0.1 μm； b. 波長等於小於 1 μm 時，在設計波長下，其〝準確度(或稱〝精度〞)〞等於或小於(優於) λ/10；	N.B. For shared aperture optical elements, capable of operating in "Super-High Power Laser" ("SHPL") applications, see the Military Goods Controls. 1. Dynamic wavefront (phase) measuring equipment capable of mapping at least 50 positions on a beam wavefront and any of the following: a. Frame rates equal to or more than 100 Hz and phase discrimination of at least 5 % of the beam's wavelength; or b. Frame rates equal to or more than 1 000 Hz and phase discrimination of at least 20 % of the beam's wavelength; 2. "Laser" diagnostic equipment capable of measuring "SHPL" system angular beam steering errors of equal to or less than 10 μrad; 3. Optical equipment and components, specially designed for	N.B. For shared aperture optical elements, capable of operating in "Super-High Power Laser" ("SHPL") applications, see the Military Goods Controls. 1. Not used; 2. "Laser" diagnostic equipment specially designed for dynamic measurement of "SHPL" system angular beam steering errors and having an angular "accuracy" of 10 μrad (microradians) or less (better); 3. Optical equipment and components, specially designed for coherent beam combination in a phased-array "SHPL" system and having any of the following: a. An "accuracy" of 0,1 μm or less, for wavelengths greater than 1 μm; or b. An "accuracy" of λ/10 or less (better) at the designed wavelength, for wavelengths equal to or less than 1 μm;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			a phased-array "SHPL" system for coherent beam combination to an "accuracy" of λ/10 at the designed wavelength, or 0,1 μm, whichever is the smaller; 4. Projection telescopes specially designed for use with "SHPL" systems;	
6A007.b.2	2. 作業(操作中) 〝準確度(或稱〝精度〞)〞小於(優於)0.7 mGal，在伴隨矯正補償及移動影響之任何組合下，其到達〝穩定狀態時間〞小於 2 分鐘；	2. 作業(操作中) 〝準確度(或稱〝精度〞)〞小於(優於) 0.7 mGal，在伴隨矯正補償及移動影響之任何組合下,其到達〝穩定狀態時間〞小於 2 分鐘；	2. An in-service (operational) "accuracy" of less (better) than 0,7 mGal having a 'time-to-steady-state registration' of less than 2 minutes under any combination of attendant corrective compensations and motional influences; Technical Note: For the purposes of 6A007.b., 'time-to-steady-state registration' (also referred to as the gravimeter's response time) is the time over which the disturbing effects of platform induced accelerations (high	2. An in-service (operational) "accuracy" of less (better) than 0,7 mGal having a "time-to-steady- state registration" of less than 2 minutes under any combination of attendant corrective compensations and motional influences;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			frequency noise) are reduced.	
6A008.e	e. 含有電子操控陣列天線；	e. 含有電子掃描陣列天線； 技術註解： 電子掃描陣列天線亦稱為電子操控陣列天線。	e. Incorporating electronically steerable array antennae;	e. Incorporating electronically scanned array antennae; Technical Note: Electronically scanned array antennae are also known as electronically steerable array antennae.
6A008.l	l. 具有下列任一特性之資料處理子系統： 1. 在任何天線旋轉下，具有〝自動目標追蹤〞能力，且其預測目標位置超越下一天線光束途徑出現時間；或 註解：6A008.l.1.不管制飛航交通管制(ATC)系統之衝突警報能力、或〝船用雷達〞。 2. 刪除； 3. 刪除； 4. 在 6 秒鐘之內，可由 2 個或以上〝地理分散〞雷達感測器提供重疊與關聯建立，或融合目標資料之組態設定，使其感測器能提升整體性能，超過 6A008.f.或 6A008.i.所述之單一感測器性能。	l. 具有下列任一特性之資料處理子系統： 1. 在任何天線旋轉下，具有〝自動目標追蹤〞能力，且其預測目標位置超越下一天線光束途徑出現時間；或 註解：6A008.l.1.不管制飛航交通管制(ATC)系統之衝突警報能力、或〝船用雷達〞。 技術註解： 〝自動目標追蹤〞乃一種處理技術，可自動決定並提供目標最可能的即時位置之推測值。 2. 刪除； 3. 刪除； 4. 在 6 秒鐘之內，可由 2 個或以上〝地理分散〞雷達感測器提供	l. Having data processing sub-systems and having any of the following: l. "Automatic target tracking" providing, at any antenna rotation, the predicted target position beyond the time of the next antenna beam passage; or Note: 6A008.l.l. does not control conflict alert capability in ATC systems, or 'marine radar'. 2. Not used; 3. Not used; 4. Configured to provide superposition and correlation, or fusion, of target data within six seconds from two or more	l. Having data processing sub-systems and having any of the following: l. 'Automatic target tracking' providing, at any antenna rotation, the predicted target position beyond the time of the next antenna beam passage; or Note: 6A008.l.l. does not control conflict alert capability in ATC systems, or 'marine radar'. Technical Note: 'Automatic target tracking' is a processing technique that automatically determines and provides as output an extrapolated value of the most probable position of the target in real time. 2. Not used; 3. Not used; 4. Configured to provide superposition and

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	說明：參照軍用貨品管制。 註解：6A008.l.4.不管制用於｀船舶交通服務´之系統、設備及零件。	重疊與關聯建立，或融合目標資料之組態設定，使其感測器能提升整體性能，超過 6A008.f.或 6A008.i.中所述之單一感測器性能。 技術註解： 〝地理分散〞指感應器相對位置在任一方向之距離均大於過1,500 公尺。活動式感應器通常被視為〝地理分散〞。	"geographically dispersed" radar sensors to improve the aggregate performance beyond that of any single sensor specified by 6A008.f. or 6A008.i. N.B. See also Military Goods Controls. Note: 6A008.l.4. does not control systems, equipment and assemblies used for 'vessel traffic service'.	correlation, or fusion, of target data within six seconds from two or more 'geographically dispersed' radar sensors to improve the aggregate performance beyond that of any single sensor specified in 6A008.f. or 6A008.i. Technical Note: Sensors are considered 'geographically dispersed' when each location is distant from any other more than 1 500 m in any direction. Mobile sensors are always considered 'geographically dispersed'.
6A108 註解	註解： 6A108.a.包括下列各項： a. 地形等高線繪圖設備； b. 影像感應設備； c. 景象繪圖及關聯比對(數位及類比)設備； d. 都卜勒導航雷達設備。	註解： 6A108.a.包括下列各項： a. 地形等高線繪圖設備； b. 景象繪圖及關聯比對(數位及類比)設備； c. 都卜勒導航雷達設備； d. 被動干涉儀設備； e. 影像感應設備(主動式及被動式)。	Note: 6A108.a. includes the following: a. Terrain contour mapping equipment; b. Imaging sensor equipment; c. Scene mapping and correlation (both digital and analogue) equipment; d. Doppler navigation radar equipment.	Note: 6A108.a. includes the following: a. Terrain contour mapping equipment; b. Scene mapping and correlation (both digital and analogue) equipment; c. Doppler navigation radar equipment; d. Passive interferometer equipment; e. Imaging sensor equipment (both active and passive).
6A203 註解	註解：6A203.a.至 6A203.c.不管制控制照相機或影像元件，其硬體、〝軟體〞或〝技術〞限制其性能低	註解：6A203.a.至 6A203.c.不管制控制照相機或影像元件，其硬體、〝軟體〞或〝技術〞限制其性能低	Note: 6A203.a. to 6A203.c. does not control cameras or imaging devices if they have hardware, "software"	Note: 6A203.a. to 6A203.c. does not control cameras or imaging devices if they have hardware, "software" or "technology" constraints that

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	於上述規範，符合下列任一特性：	於如後規範，符合下列任一特性：	or "technology" constraints that limit the performance to less than that specified above, provided they meet any of the following:	limit the performance to less than that specified below, provided they meet any of the following:
6A205.d	d. 脈衝二氧化碳〝雷射器〞，具有下列所有特性：	d. 脈衝二氧化碳(CO_2)〝雷射器〞，具有下列所有特性：	d. Pulsed carbon dioxide "lasers" having all of the following characteristics:	d. Pulsed carbon dioxide (CO_2) "lasers" having all of the following characteristics:
6A205.g	g. 未由 6A005.d.2.規範之一氧化碳雷射，具下列所有特性：	g. 未由 6A005.d.2.規範之一氧化碳(CO)雷射，具下列所有特性：	g. Pulsed carbon monoxide lasers, other than those specified in 6A005.d.2., having all of the following:	g. Pulsed carbon monoxide (CO) "lasers", other than those specified in 6A005.d.2., having all of the following:
6D003.h	2. 為設計或〝生產〞天線罩之〝軟體〞，具有下列所有特性： a. 特別設計為保護 6A008.e.所述之〝電子操控相位陣列天線〞；及	2. 為設計或〝生產〞天線罩之〝軟體〞具有下列所有特性： a. 特別設計為保護 6A008.e.所述之電子操控相位陣列天線；及	2. "Software" for the design or "production" of radomes and having all of the following: a. Specially designed to protect the "electronically steerable phased array antennae" specified in 6A008.e.; and	2. "Software" for the design or "production" of radomes having all of the following: a. Specially designed to protect the electronically scanned array antennae specified in 6A008.e.; and
7A006	7A006 工作頻率為 4.2 至 4.4 GHz(含)以外操作之航空高度計，具下列任一特性： 說明：參照 7A106。 a.〝功率管理〞；或 b. 使用相位偏移調變。	7A006 工作頻率為 4.2 至 4.4 GHz(含)以外操作之航空高度計，具下列任一特性： 說明：參照 7A106。 a. ˋ功率管理ˊ；或 b. 使用相位偏移調變。	7A006 Airborne altimeters operating at frequencies other than 4,2 to 4,4 GHz inclusive and having any of the following: N.B. SEE ALSO 7A106. a. "Power management"; or	7A006 Airborne altimeters operating at frequencies other than 4,2 to 4,4 GHz inclusive and having any of the following: N.B. SEE ALSO 7A106. a. 'Power management'; or b. Using phase shift key modulation.

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		技術註解： 〝功率管理〞指改變高度計訊號之傳輸功率，以致使〝航空器〞高度之接收功率總是在決定高度之最小需求。	b. Using phase shift key modulation.	Technical Note: 'Power management' is changing the transmitted power of the altimeter signal so that received power at the "aircraft" altitude is always at the minimum necessary to determine the altitude.
7A105	7A105 除 7A005 所述外之全球衛星導航系統(GNSS，例如：GPS、GLONASS 或 Galileo)接收設備，具下列任一特性，及特別設計之零件： a. 設計或修改為用於 9A004 所述之太空發射載具、9A104 所述之探空火箭或 9A012 或 9A112.a.所述之無人飛行載具；或 b. 設計或修改為航空應用，且具下列任一特性： 1. 可於速度超過 600 m/s 下提供導航資訊； 2. 使用為軍事或政府用而設計或修改之解密技術，以取得 GNSS 保密訊號/資料；或 3. 特別設計使用反干擾裝置(例如零向調轉(零點可控)天線或電子式操縱方向性天線)於主動或被動	7A105 除 7A005 所述外之〝衛星導航系統〞接收設備，具下列任一特性，及特別設計之零件： a. 設計或修改為用於 9A004 所述之太空發射載具、9A104 所述之探空火箭或 9A012 或 9A112.a.所述之無人飛行載具；或 b. 設計或修改為航空應用，且具下列任一特性： 1. 可於速度超過 600 m/s 下提供導航資訊； 2. 使用為軍事或政府用而設計或修改之解密技術，以取得〝衛星導航系統〞保密訊號/資料；或 3. 特別設計使用反干擾裝置(例如零向調轉(零點可控)天線或電子式操縱方向性天線)於主動或被動反制環境下運作。 註解：7A105.b.2.及 7A105.b.3.不	7A105 Receiving equipment for Global Navigation Satellite Systems (GNSS; e.g. GPS, GLONASS, or Galileo), other than those specified in 7A005, having any of the following characteristics, and specially designed components therefor: a. Designed or modified for use in space launch vehicles specified in 9A004, sounding rockets specified in 9A104 or unmanned aerial vehicles specified in 9A012 or 9A112.a; or b. Designed or modified for airborne applications and having any of the following: 1. Capable of providing navigation information at speeds in excess of	7A105 Receiving equipment for 'navigation satellite systems', other than those specified in 7A005, having any of the following characteristics, and specially designed components therefor: a. Designed or modified for use in space launch vehicles specified in 9A004, sounding rockets specified in 9A104 or unmanned aerial vehicles specified in 9A012 or 9A112.a; or b. Designed or modified for airborne applications and having any of the following: 1. Capable of providing navigation information at speeds in excess of 600 m/s; 2. Employing decryption, designed or modified for military or governmental services, to gain access to a 'navigation satellite system' secured signal/data; or 3. Being specially designed to employ anti-jam features (e.g. null steering antenna or

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	反制環境下運作。 註解：7A105.b.2.及 7A105.b.3.不管制為商業、民用或｀人命安全｀(例如資料完整性、飛行安全)用途之 GNSS 服務而設計之設備。	管制為商業、民用或｀人命安全｀(例如資料完整性、飛行安全)用途之｀衛星導航系統｀服務而設計之設備。 技術註解： 7A105 中之｀衛星導航系統｀包括全球衛星導航系統(GNSS，例如 GPS、GLONASS、Galileo 或 BeiDou)與區域衛星導航系統(RNSS，例如 NavIC、QZSS)。	600 m/s; 2. Employing decryption, designed or modified for military or governmental services, to gain access to GNSS secured signal/data; or 3. Being specially designed to employ anti-jam features (e.g. null steering antenna or electronically steerable antenna) to function in an environment of active or passive countermeasures. Note: 7A105.b.2. and 7A105.b.3. do not control equipment designed for commercial, civil or 'Safety of Life' (e.g., data integrity, flight safety) GNSS services.	electronically steerable antenna) to function in an environment of active or passive countermeasures. Note: 7A105.b.2. and 7A105.b.3. do not control equipment designed for commercial, civil or 'Safety of Life' (e.g., data integrity, flight safety) 'navigation satellite system' services. Technical Note: In 7A105, 'navigation satellite system' includes Global Navigation Satellite Systems (GNSS; e.g. GPS, GLONASS, Galileo or BeiDou) and Regional Navigation Satellite Systems (RNSS; e.g. NavIC, QZSS).
7A115 註解	註解:7A115 包括下列設備之感應器： a. 地形等高線繪圖設備； b. 影像感應器設備(主動式及被動式)； c. 被動式干擾儀設備。	註解：7A105、7A106 與 7A115 中所述之設備，包括下列設備： a. 地形等高線繪圖設備； b. 景象繪圖及關聯比對(數位及類比)設備； c. 都卜勒導航雷達設備； d. 被動干涉儀設備；	Note: 7A115 includes sensors for the following equipment: a. Terrain contour mapping equipment; b. Imaging sensor equipment (both active and passive); c. Passive interferometer	Note: Equipment specified in 7A105, 7A106, and 7A115 includes the following: a. Terrain contour mapping equipment; b. Scene mapping and correlation (both digital and analogue) equipment; c. Doppler navigation radar equipment; d. Passive interferometer equipment;

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		e. 影像感應設備(主動式及被動式)。	equipment.	e. Imaging sensor equipment (both active and passive).
7A116 註解	無	註解:針對將載人航空器改裝成為〝飛彈〞操作者，7A116 包括系統、設備與閥門設計或改裝，其可使載人航空器如同無人飛行載具一般運作。	-	Note: For conversion of manned aircraft to operate as "missiles", 7A116 includes the systems, equipment and valves designed or modified to enable operation of manned aircraft as unmanned aerial vehicles.
7E004.a	5. 特別設計為〝主飛行控制〞之電力致動器(亦即，電力機械致動器、電力流體靜力致動器與整合致動器包裝)； 6. 特別設計為執行〝主動飛行控制系統〞之〝飛行控制光學感應器陣列〞；	5. 特別設計為〝主飛行控制〞之電力致動器(亦即，電力機械致動器、電力流體靜力致動器與整合致動器包裝)； 技術註解： 〝主飛行控制〞指使用力/力矩產生器之〝航空器〞之穩定或操控，即空氣動力控制表面或推進力向量。 6. 特別設計為執行〝主動飛行控制系統〞之〝飛行控制光學感應器陣列〞； 技術註解： 〝飛行控制光學感應器陣列〞指由光學感測器分佈而形成之網路，使用〝雷射〞光束提供即時飛行控制資料於機上處理。	5. Electric actuators (i.e., electromechanical, electrohydrostatic and integrated actuator package) specially designed for "primary flight control"; 6. "Flight control optical sensor array" specially designed for implementing "active flight control systems"; or	5. Electric actuators (i.e., electromechanical, electrohydrostatic and integrated actuator package) specially designed for 'primary flight control'; Technical Note: 'Primary flight control' is "aircraft" stability or manoeuvring control using force/moment generators, i.e. aerodynamic control surfaces or propulsive thrust vectoring. 6. 'Flight control optical sensor array' specially designed for implementing "active flight control systems"; or Technical Note: A 'flight control optical sensor array' is a network of distributed optical sensors, using "laser" beams, to provide real-time flight control data for on-board processing.

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7E004.b.5 註解	註解：7E004.b.5.不管制： a. 將數位飛行控制、導航及推進控制資料整合成一〝最佳飛行路徑〞的數位飛行管理系統之〝技術〞；	註解：7E004.b.5.不管制： a. 將數位飛行控制、導航及推進控制資料整合成一〝飛行路徑最佳化〞的數位飛行管理系統之〝技術〞；	Note: 7E004.b.5. does not control: a. "Technology" for integration of digital flight control, navigation and propulsion control data, into a digital flight management system for "flight path optimisation";	Note: 7E004.b.5. does not control: a. "Technology" for integration of digital flight control, navigation and propulsion control data, into a digital flight management system for 'flight path optimisation';
7E004.b.5 技術註解	無	技術註解： 〝飛行路徑最佳化〞指由4度空間(空間與時間)期望之軌跡達到最小偏差，以最大性能或效果完成任務的程序。	-	Technical Note: 'Flight path optimisation' is a procedure that minimises deviations from a four-dimensional (space and time) desired trajectory based on maximising performance or effectiveness for mission tasks.
7E004.c.3	3. 用於使用個別翼片控制之系統，包含〝可變幾何機翼〞旋翼。	3. 用於使用個別翼片控制之系統，包含〝可變幾何機翼〞旋翼。 技術註解： 〝可變幾何機翼〞指使用後緣襟翼或調整片、前緣襟翼或軸鼻翼，其位置在飛行中可受控制。	3. Rotor blades incorporating "variable geometry airfoils", for use in systems using individual blade control.	3. Rotor blades incorporating 'variable geometry airfoils', for use in systems using individual blade control. Technical Note: 'Variable geometry airfoils' use trailing edge flaps or tabs, or leading edge slats or pivoted nose droop, the position of which can be controlled in flight.
9A002	9A002 依照ISO標準，連續功率額定為24,245 kW或以上，在功率範圍為35至100 %時，特定燃料消耗不超過0.219 kg/ kWh之〝船	9A002 設計使用液態燃料之〝船用燃氣渦輪引擎〞具下列所有特性者，及其特別設計之組件及零件：	9A002 'Marine gas turbine engines' with an ISO standard continuous power rating of 24 245 kW or more and a specific fuel consumption not	9A002 'Marine gas turbine engines' designed to use liquid fuel and having all of the following, and specially designed assemblies and components therefor:

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	用燃氣渦輪引擎〞，及其特別設計之組件及零件。 註解：〝船用燃氣渦輪引擎〞一詞包括為船艦發電或推進而修改之工業用或航空用衍生之燃氣渦輪發動機。	a. 依照ISO 3977-2:1997(或等效國家標準)，在〝穩定狀態模式〞時最大連續功率為 24,245 kW 或以上；或 b. 使用液態燃料，在最大連續功率的 35 %時，〝修正燃料消耗〞不超過 0.219 kg/ kWh。 註解：〝船用燃氣渦輪引擎〞一詞包括為船艦發電或推進而修改之工業用或航空用衍生之燃氣渦輪發動機。 技術註解： 9A002 所述之〝修正燃料消耗〞指引擎校正至海運餾分液態燃料，其淨能源熱值(即淨熱值)為 42MJ/kg (ISO 3977-2:1997)時之燃料消耗率。	exceeding 0,219 kg/kWh in the power range from 35 to 100 %, and specially designed assemblies and components therefor. Note: The term 'marine gas turbine engines' includes those industrial, or aero-derivative, gas turbine engines adapted for a ship's electric power generation or propulsion.	a. Maximum continuous power when operating in "steady state mode" at standard reference conditions specified by ISO 3977-2:1997 (or national equivalent) of 24 245 kW or more; and b. 'Corrected specific fuel consumption' not exceeding 0,219 kg/kWh at 35 % of the maximum continuous power when using liquid fuel. Note: The term 'marine gas turbine engines' includes those industrial, or aero-derivative, gas turbine engines adapted for a ship's electric power generation or propulsion. Technical Note: For the purposes of 9A002, 'corrected specific fuel consumption' is the specific fuel consumption of the engine corrected to a marine distillate liquid fuel having a net specific energy (i.e. net heating value) of 42MJ/kg (ISO 3977-2:1997).
9A004.f	f.特別為〝太空載具〞設計之地面設備，如下： 1.遙測與遙控設備； 2.模擬器。	f.特別為〝太空載具〞設計之地面設備，如下： 1. 遙測與遙控設備，特別設計為下列任一資料處理功能： a. 訊框同步與錯誤校正之遙測資訊處理,用於監控〝太空載具本體〞	f. Terrestrial equipment specially designed for "spacecraft", as follows: 1. Telemetry and telecommand equipment; 2. Simulators.	f. Terrestrial equipment specially designed for "spacecraft", as follows: 1. Telemetry and telecommand equipment specially designed for any of the following data processing functions: a. Telemetry data processing of frame

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		運作狀態(亦稱為健康及安全狀態)；或 b. 為格式化指令資料之資料處理，其被送至〝太空載具〞以控制〝太空載具本體〞； 2.模擬器特別設計用於〝太空載具〞之｀驗證操作程序´。 技術註解： 9A004.f.2.所述之｀驗證操作程序´為下列任一： 1. 確認指令序列； 2. 訓練操作； 3. 操作演練；或 4. 操作分析。		synchronisation and error corrections, for monitoring of operational status (also known as health and safe status) of the "spacecraft bus"; or b. Command data processing for formatting command data being sent to the "spacecraft" to control the "spacecraft bus"; 2. Simulators specially designed for 'verification of operational procedures' of "spacecraft". Technical Note: For the purposes of 9A004.f.2., 'verification of operational procedures' is any of the following: 1. Command sequence confirmation; 2. Operational training; 3. Operational rehearsals; or 4. Operational analysis.
9A101	9A101 除 9A001 所述以外，渦輪噴射發動機及渦輪風扇發動機如下： a. 具有下列 2 項特性之發動機： 1. ｀最大推力值´大於 400 N(在無裝配時達到此值)，但不包括｀最大推力值´大於 8,890 N(在	9A101 除 9A001 所述以外，渦輪噴射發動機及渦輪風扇發動機如下： a. 具有下列所有特性之發動機： 1. ｀最大推力值´大於 400 N(在無裝配時達到此值)，但不包括｀最大推力值´大於 8,890 N(在	9A101 Turbojet and turbofan engines, other than those specified in 9A001, as follows; a. Engines having both of the following characteristics: 1. 'Maximum thrust value' greater than 400 N (achieved un-installed)	9A101 Turbojet and turbofan engines, other than those specified in 9A001, as follows; a. Engines having all of the following characteristics: 1. 'Maximum thrust value' greater than 400 N (achieved un-installed) excluding civil certified engines with a 'maximum thrust value'

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	無裝配時達到此值)，且經認證之民用發動機；及 2. 燃油消耗比為 0.15 kg/N/h 或以下(海平面靜止狀態及使用 ICAO 標準大氣壓狀況下之最大連續功率)； 技術註解： 就 9A101.a.1.目的，｀最大推力值｀為製造商對未安裝發動機展現之最大推力。民間認證之推力值將等於或小於製造商所證明之最大推力。 b. 設計或修改用於〝飛彈〞或 9A012 或 9A112.a.所述之無人飛行載具之發動機。	無裝配時達到此值)，且經認證之民用發動機；及 2. 燃油消耗比為 0.15 kg N-1 hr-1 或以下(在海平面靜止狀態下使用 ICAO 標準大氣壓下之最大連續功率)； 3. ｀乾重｀小於 750 kg；及 4. ｀第一級轉子直徑｀小於 1 m； 技術註解： 1. 9A101.a.1.所述之｀最大推力值｀為在海平面靜止狀態下使用 ICAO 標準大氣壓情況，製造商對未安裝發動機展現之最大推力。民間認證之推力值將等於或小於製造商所證明之最大推力。 2. ｀乾重｀指發動機不含液體(燃料、液壓油、潤滑油等)的重量，且不包括機艙(外殼)。 3. ｀第一級轉子直徑｀指發動機第一階轉子的直徑，無論其為風扇或壓縮機，由葉片尖端前緣處測量。	excluding civil certified engines with a 'maximum thrust value' greater than 8 890 N (achieved un-installed), and 2. Specific fuel consumption of 0,15 kg N -1 hr -1 or less (at maximum continuous power at sea level static conditions using the ICAO standard atmosphere); Technical Note: For the purpose of 9A101.a.1. 'maximum thrust value' is the manufacturer's demonstrated maximum thrust for the engine type un-installed. The civil type certified thrust value will be equal or less than the manufacturer's demonstrated maximum thrust for the engine type.	greater than 8 890 N (achieved un-installed), and 2. Specific fuel consumption of 0,15 kg N -1 hr -1 or less (at maximum continuous power at sea level static conditions using the ICAO standard atmosphere); 3. 'Dry weight' less than 750 kg; and 4. 'First-stage rotor diameter' less than 1 m; Technical Notes: 1. For the purpose of 9A101.a.1. 'maximum thrust value' is the manufacturer's demonstrated maximum thrust for the engine type un-installed at sea level static conditions using the ICAO standard atmosphere. The civil type certified thrust value will be equal to or less than the manufacturer's demonstrated maximum thrust for the engine type. 2. 'Dry weight' is the weight of the engine without fluids (fuel, hydraulic fluid, oil, etc.) and does not include the nacelle (housing). 3. 'First-stage rotor diameter' is the diameter of the first rotating stage of the engine, whether a fan or compressor, measured at the leading edge of the blade tips.
9A115	9A115 發射支援設備如下：	9A115 發射支援設備如下：	9A115 Launch support equipment as	9A115 Launch support equipment as follows:

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	a. 用於處理、控制、啟動或發射，且設計或修改用於 9A004 所述之太空發射載具、9A104 所述之探空火箭之儀器及裝置，或 9A012 或 9A112.a.所述之無人飛行載具； b. 用於運輸、處理、控制、啟動或發射，且設計或修改用於 9A004 所述之太空發射載具或 9A104 所述之探空火箭之載具；	a. 用於處理、控制、啟動或發射，且設計或修改用於 9A004 所述之太空發射載具、9A104 所述之探空火箭之儀器及裝置或｀飛彈´； 技術註解： 9A115.a.所述之｀飛彈´指射程或航程超過 300 km 之完整火箭系統及無人飛行載具系統。 b. 用於運輸、處理、控制、啟動或發射，且設計或修改用於 9A004 所述之太空發射載具或 9A104 所述之探空火箭之載具或｀飛彈´；	follows: a. Apparatus and devices for handling, control, activation or launching, designed or modified for space launch vehicles specified in 9A004, sounding rockets specified in 9A104 or unmanned aerial vehicles specified in 9A012 or 9A112.a.; b. Vehicles for transport, handling, control, activation or launching, designed or modified for space launch vehicles specified in 9A004 or sounding rockets specified in 9A104.	a. Apparatus and devices for handling, control, activation or launching, designed or modified for space launch vehicles specified in 9A004, sounding rockets specified in 9A104 or 'missiles'; Technical Note: In 9A115.a. 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km. b. Vehicles for transport, handling, control, activation or launching, designed or modified for space launch vehicles specified in 9A004, sounding rockets specified in 9A104 or "missiles".
9D001	9D001　特別設計或修改用於〝開發〞9A001 至 9A119、9B 或 9E003 所述之設備或〝技術〞之〝軟體〞。	9D001　未由 9D003 或 9D004 所管制，特別設計或修改用於〝開發〞 9A001 至 9A119、9B 或 9E003 所述之設備或〝技術〞之〝軟體〞。	9D001 "Software" specially designed or modified for the "development" of equipment or "technology", specified in 9A001 to 9A119, 9B or 9E003.	9D001 "Software", not specified in 9D003 or 9D004, specially designed or modified for the "development" of equipment or "technology", specified in 9A001 to 9A119, 9B or 9E003.
9D002	9D002　特別設計或修改用於〝生產〞9A001 至 9A119 或 9B 所述之設備之〝軟體〞。	9D002　未由 9D003 或 9D004 所管制，特別設計或修改用於〝生產〞 9A001 至 9A119 或 9B 所述之設備之〝軟體〞	9D002 "Software" specially designed or modified for the "production" of equipment specified in 9A001 to 9A119 or 9B.	9D002 "Software", not specified in 9D003 or 9D004, specially designed or modified for the "production" of equipment specified in 9A001 to 9A119 or 9B.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
9D004	9D004 其他〝軟體〞如下： a. 用為建立詳細的發動機氣流模式所需之風洞或飛行測試資料，驗證之2維或3維黏性流體〝軟體〞； b. 用於測試航空用燃氣渦輪發動機、組件或零件之〝軟體〞，特別設計為即時收集、簡化及分析資料，且具回授控制能力，包括在測試進行中，測試物件或測試條件之動態調整；	9D004 其他〝軟體〞如下： a. 用為建立詳細的發動機氣流模式所需之風洞或飛行測試資料，驗證之2維或3維黏性流體〝軟體〞； b. 用於測試航空用燃氣渦輪發動機、組件或零件之〝軟體〞，具下列所有特性： 1. 特別設計為測試下列任一者： a. 航空用燃氣渦輪發動機、組件或零件，其含有9E003.a.、9E003.h.或9E003.i.所述之〝技術〞；或 b. 為航空用燃氣渦輪發動機特別設計之多級壓縮機，提供分流或主流量，其含有9E003.a.或9E003.h.所述之〝技術〞；或 2. 特別設計為下列所有者： a. 即時收集與處理資料；及 b. 在測試進行中具調整測試物件或測試條件(例如溫度、壓力、流速)之回授控制能力； 註解：9D004.b.不管制用於操作測試設施或操作者安全(例如超速停機、火災偵測與抑制)之軟體，或生產、維修或維護僅限於確認受測	9D004 Other "software" as follows: a. 2D or 3D viscous "software", validated with wind tunnel or flight test data required for detailed engine flow modelling; b. "Software" for testing aero gas turbine engines, assemblies or components, having all of the following: 1. Specially designed for testing any of the following: a. Aero gas turbine engines, assemblies or components, incorporating "technology" specified in 9E003.a., 9E003.h. or 9E003.i.; or b. Multi-stage compressors providing either bypass or core flow, specially designed for aero gas turbine engines incorporating "technology" specified in 9E003.a. or 9E003.h.; and 2. Specially designed for all of the following: a. Acquisition and processing of data, in real time; and b. Feedback control of the test article or test conditions (e.g. temperature, pressure, flow rate) while the test is in progress; Note: 9D004.b. does not control software for operation of the test facility or operator safety	9D004 Other "software" as follows: a. 2D or 3D viscous "software", validated with wind tunnel or flight test data required for detailed engine flow modelling; b. "Software" for testing aero gas turbine engines, assemblies or components, having all of the following: 1. Specially designed for testing any of the following: a. Aero gas turbine engines, assemblies or components, incorporating "technology" specified in 9E003.a., 9E003.h. or 9E003.i.; or b. Multi-stage compressors providing either bypass or core flow, specially designed for aero gas turbine engines incorporating "technology" specified in 9E003.a. or 9E003.h.; and 2. Specially designed for all of the following: a. Acquisition and processing of data, in real time; and b. Feedback control of the test article or test conditions (e.g. temperature, pressure, flow rate) while the test is in progress; Note: 9D004.b. does not control software for operation of the test facility or operator safety

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		項目正確組裝或維修之軟體。		(e.g. overspeed shutdown, fire detection and suppression), or production, repair or maintenance acceptance-testing limited to determining if the item has been properly assembled or repaired.
9E003.a.2.d 技術註解	2.｀燃燒室出口溫度´為，當發動機在｀穩定狀態模式´下運轉至認證之最大連續操作溫度時，燃燒室出口平面與渦輪機進氣導向葉片尖端(即依照 SAE APR 755A 所定義之 T40 發動機站量測)兩者間之主體平均氣流總(停滯)溫度。	2.｀燃燒室出口溫度´為，當發動機在〝穩定狀態模式〞下運轉至認證之最大連續操作溫度時，燃燒室出口平面與渦輪機進氣導向葉片尖端(即依照 SAE APR 755A 所定義之 T40 發動機站量測)兩者間之主體平均氣流總(停滯)溫度。	2.'Combustor exit temperature' is the bulk average gas path total (stagnation) temperature between the combustor exit plane and the leading edge of the turbine inlet guide vane (i.e., measured at engine station T40 as defined in SAE ARP 755A) when the engine is running in a 'steady state mode' of operation at the certificated maximum continuous operating temperature.	2.'Combustor exit temperature' is the bulk average gas path total (stagnation) temperature between the combustor exit plane and the leading edge of the turbine inlet guide vane (i.e., measured at engine station T40 as defined in SAE ARP 755A) when the engine is running in a "steady state mode" of operation at the certificated maximum continuous operating temperature.
9E003.a.5 技術註解	技術註解： 1.｀燃氣路徑溫度´ 為當發動機在｀穩定狀態模式´下運轉至經認證或指定之最大連續操作溫度時，渦輪機元件前緣平面之主體平均氣流總(停滯)溫度。 2.｀穩定狀態模式｀定義為在發	技術註解： ｀燃氣路徑溫度´ 為當發動機在｀穩定狀態模式´下運轉至經認證或指定之最大連續操作溫度時，渦輪機元件前緣平面之主體平均氣流總(停滯)溫度。	Technical Notes: 1.'Gas path temperature' is the bulk average gas path total (stagnation) temperature at the leading edge plane of the turbine component when the engine is running in a 'steady state mode'	Technical Note: 'Gas path temperature' is the bulk average gas path total (stagnation) temperature at the leading edge plane of the turbine component when the engine is running in a "steady state mode" of operation at the certificated or specified maximum continuous operating temperature.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	動機進氣口四周空氣溫度和壓力固定，推力/輸出比和每分鐘轉數等發動機參數無明顯波動的情況下之發動機操作。		of operation at the certificated or specified maximum continuous operating temperature. 2. The term 'steady state mode' defines engine operation conditions, where the engine parameters, such as thrust/power, rpm and others, have no appreciable fluctuations, when the ambient air temperature and pressure at the engine inlet are constant.	
9E003.c 技術註解	4. 製造 9E003.c.所述孔洞之技術，包括〝雷射〞、水刀、電化學加工(ECM)或放電加工(EDM)方法。	4. 製造 9E003.c.所述孔洞之方法，包括〝雷射〞光束機械加工、水刀機械加工、電化學加工(ECM)或放電加工(EDM)。	4. Techniques for manufacturing holes in 9E003.c include "laser", water jet, Electro-Chemical Machining (ECM) or Electrical Discharge Machining (EDM) methods.	4. Methods for manufacturing holes in 9E003.c. include "laser" beam machining, water jet machining, Electro- Chemical Machining (ECM) or Electrical Discharge Machining (EDM).

第二項：一般軍用貨品清單修正對照表

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
ML4.a 註解	b. 飛彈火箭噴嘴及重返大氣層載具之機頭尖端。	b. 飛彈或火箭噴嘴及重返大氣層載具之機頭尖端。	b. Missile rocket nozzles and re-entry vehicle nosetips.	b. Missile or rocket nozzles and re-entry vehicle nosetips.
ML5	ML5 為軍事用途而特別設計之發射控制及相關之警報與警示設備、相關之系統、測試及校準與反制設備，如下所列，及為其特別設計之零件與配件： a. 武器瞄準具、轟炸模擬機、槍砲鋪設設備及武器控制系統； b. 目標擷取、指定、測距、監視或追蹤系統；偵測、數據結合、辨識或辨認設備，及感應器集成設備；	ML5 為軍事用途而特別設計之發射控制、監控與警示設備、相關之系統、測試及校準與反制設備，如下所列，及為其特別設計之零件與配件： a. 武器瞄準具、轟炸模擬機、槍砲鋪設設備及武器控制系統； b. 其他發射控制、監控與警示設備，與其相關之系統，如下： 1. 目標擷取、指定、測距、監視或追蹤系統； 2. 偵測、辨識或識別設備； 3. 數據結合或感應器集成設備；	ML5 Fire control, and related alerting and warning equipment, and related systems, test and alignment and countermeasure equipment, as follows, specially designed for military use, and specially designed components and accessories therefor: a. Weapon sights, bombing computers, gun laying equipment and weapon control systems; b. Target acquisition, designation, range-finding, surveillance or tracking systems; detection, data fusion, recognition or identification equipment; and sensor integration equipment;	ML5 Fire control, surveillance and warning equipment, and related systems, test and alignment and countermeasure equipment, as follows, specially designed for military use, and specially designed components and accessories therefor: a. Weapon sights, bombing computers, gun laying equipment and weapon control systems; b. Other fire control, surveillance and warning equipment, and related systems, as follows: 1. Target acquisition, designation, range-finding, surveillance or tracking systems; 2. Detection, recognition or identification equipment; 3. Data fusion or sensor integration equipment;
ML6.a 註解	無	註解 1：ML6.a.包括： a. 坦克與其他軍用裝甲車輛與軍	-	Note 1 ML6.a. includes: a. Tanks and other military armed vehicles and

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		用車輛裝置有支架，可裝設ML4所述用於鋪設或發射彈藥之武器或設備； b. 裝甲車輛； c. 兩棲與可涉深水車輛； d. 救援車輛、拖曳或運輸彈藥或武器系統及相關裝載處理設備之車輛； e. 拖車。 註解2：為受ML6.a.管制之軍事用途而進行之地面車輛改裝，該等改裝必須為結構、電氣或機械上之改變，且該改變涉及1件或以上為軍事用途而特別設計之零件。該等零件包括： a. 專門設計用於防彈用途的充氣輪胎外胎； b. 以裝甲保護重要部位 (例如：油箱或座艙)； c. 為武器之特別強化或裝設； d. 遮光照明。		military vehicles fitted with mountings for arms or equipment for mine laying or the launching of munitions specified by ML4; b. Armoured vehicles; c. Amphibious and deep water fording vehicles; d. Recovery vehicles and vehicles for towing or transporting ammunition or weapon systems and associated load handling equipment; e. Trailers. Note 2 Modification of a ground vehicle for military use specified by ML6.a. entails a structural, electrical or mechanical change involving one or more components that are specially designed for military use. Such components include: a. Pneumatic tyre casings of a kind specially designed to be bullet-proof; b. Armoured protection of vital parts (e.g. fuel tanks or vehicle cabs); c. Special reinforcements or mountings for weapons; d. Black-out lighting.
ML6.b.2註解	無	註解1：ML6不管制設計或改裝用於運鈔或貴重物品之民用車	-	Note 1 ML6 does not apply to civil vehicles designed or modified for transporting money or valuables.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		輛。 註解 2：ML6 不管制符合下列所有特性之車輛： a. 於 1946 年之前製造； b. 不具有歐盟一般軍用貨品清單所指之項目及 1945 年後製造者，除原始零件或配件之複製品以外；及 c. 不包含 ML.1、ML.2 或 ML.4 所述之武器，除非其武器失效及卸除彈藥投射物。		Note 2 ML6. does not apply to vehicles that meet all of the following; a. Were manufactured before 1946; b. Do not have items specified by the EU Common Military List and manufactured after 1945, except for reproductions of original components or accessories for the vehicle; and c. Do not incorporate weapons specified in ML1., ML2. or ML4. unless they are inoperable and incapable of discharging a projectile.
ML8. a. 6	6. DADE(1,1-二胺基-2,2-二硝基乙烯、FOX7)(CAS 145250-81-3)；	6. DADE(1,1-二胺基-2,2-二硝基乙烯、FOX-7)(CAS 145250-81-3)；	6. DADE (1,1-diamino-2,2-dinitroethylene, FOX7) (CAS 145250-81-3);	6. DADE (1,1-diamino-2,2-dinitroethylene, FOX-7) (CAS 145250-81-3);
ML8. a. 33	33. 未列於 ML8.a.之別處列出之炸藥且具下列任一特性：	33. 未列於 ML8.a.之別處列出之〝炸藥〞且具下列任一特性：	33. Explosives not listed elsewhere in ML8. a. and having any of the following:	33. "Explosives" not listed elsewhere in ML8. a. and having any of the following:
ML8. a. 43	無	43. TKX-50 (5,5'-聯四唑-1,1'-羥胺鹽)；	-	43. TKX-50 (Dihydroxylammonium 5,5'-bistetrazole-1,1'-diolate);
ML8. c. 5 註解	註解 1：ML8.c.5.管制之〝爆炸物〞與燃料，無論其金屬或合金是否包覆於鋁、鎂、鋯，或鈹。	註解 1：ML8.c.5.管制之〝炸藥〞與燃料，無論其金屬或合金是否包覆於鋁、鎂、鋯，或鈹。	Note 1 ML8. c. 5. applies to "explosives" and fuels, whether or not the metals or alloys are encapsulated in aluminium, magnesium, zirconium, or	Note 1 ML8.c.5. applies to "explosives" and fuels, whether or not the metals or alloys are encapsulated in aluminium, magnesium, zirconium, or beryllium.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			beryllium.	
ML8.c.12 註解	無	註解：ML8.c.12.包括鋁熱劑。	-	Note ML8.c.12. includes thermites.
ML9.a 註解	無	註解:ML9.a.1 包括特別設計或改裝為輸送潛水員之載具。	-	Note ML9.a.1. includes vehicles specially designed or modified for the delivery of divers.
ML.9.a.2	2. ML9.a.1.所述以外之水面船隻，具下列任一項固定於或納入船隻中：	2. 未列於ML9.a.1.所述之水面船隻，在船隻中固定於或納入下列任一項目：	2. Surface vessels, other than those specified in ML9.a.1., having any of the following, fixed or integrated into the vessel:	2. Surface vessels, not specified in ML9.a.1., having any of the following, fixed or integrated into the vessel:
ML.9.b.3	3. 為軍事用途而特別設計之非磁性柴油引擎，具有下列所有特性： a. 功率輸出為37.3 kW(50 馬力)或以上；及 b. 非磁性成分超過總重量之75 %；	3. 柴油引擎具有下列所有特性： a. 功率輸出為37.3 kW(50 馬力)或以上；及 b. ｀非磁性成分｀超過總重量之75 %； 技術註解： ML9.b.3之｀非磁性成分｀指相對磁導率小於2。	3. Non-magnetic diesel engines having all of the following: a. Power output of 37,3 kW (50 hp) or more; and b. Non-magnetic content in excess of 75 % of total mass;	3. Diesel engines having all of the following: a. Power output of 37,3 kW (50 hp) or more; and b. 'Non-magnetic' content in excess of 75 % of total mass; Technical Note For the purpose of ML9.b.3., 'non-magnetic' means the relative permeability is less than 2.
ML.9.h	無	h. 海軍用核子設備與相關設備及零件，如下： 1. 核能發電設備或推進設備，特別設計用於ML.9.a.所述之船隻，與其特別設計或｀改裝｀用	-	h. Naval nuclear equipment and related equipment and components, as follows: 1. Nuclear power generating equipment or propulsion equipment, specially designed for vessels specified in ML9.a. and components

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		於軍事用途之零件； 技術註解： ML9.h.1之｀改裝｀為任何結構、電氣、機械或其他變更，其可使非軍事用途之項目具有與特別設計用於軍事用途者相同之能力。 註解：ML9.h.1.包括〝核子反應器〞。		therefor specially designed or 'modified' for military use. Technical Note For the purpose of ML9.h.1., 'modified' means any structural, electrical, mechanical, or other change that provides a non-military item with military capabilities equivalent to an item which is specially designed for military use. Note ML9.h.1. includes "nuclear reactors".
ML10 註解 5	註解 5：ML10.a.不管制〝航空器〞具下列所有特性：	註解 5：ML10.a.不管制〝航空器〞或〝比空氣輕載具〞具下列所有特性：	Note 5 ML10.a. does not apply to "aircraft" that meet all of the following:	Note 5 ML10.a. does not apply to "aircraft" or "lighter-than-air-vehicles" that meet all of the following:
ML10 註解 6	無	註解 6：ML10.d.不管制在 1946 年之前首次製造之航空發動機。	-	Note 6 ML10.d. does not apply to propulsion aero-engines that were first manufactured before 1946.
ML11.b	b. 全球導航衛星系統(GNSS)之干擾設備及特別為其設計之零件；	b. 〝衛星導航系統〞之干擾設備及特別為其設計之零件；	b. Global Navigation Satellite Systems (GNSS) jamming equipment and specially designed components therefor;	b. "Satellite navigation system" jamming equipment and specially designed components therefor;
ML13 註解 4	註解 4：ML13.所述為廢彈處理人員而特別設計之專用頭盔，特別設計為軍事用途者。	註解 4：ML13.c.所述為廢彈處理人員而特別設計之專用頭盔，特別設計為軍事用途者。	Note 4 The only helmets specially designed for bomb disposal personnel that are	Note 4 The only helmets specially designed for bomb disposal personnel that are specified by ML13.c. are those specially designed for

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			specified by ML13. are those specially designed for military use.	military use.
ML17.g	g. 為軍用而特別設計之核能發電設備或推進設備，包括｀核子反應器´，及其為軍用而特別設計或改裝之零件；	g. 未於其他處列入，為軍用而特別設計之核能發電設備或推進設備，及其為軍用而特別設計或改裝之零件； 註解：ML17.g.包括〝核子反應器〞。	g. Nuclear power generating equipment or propulsion equipment, including "nuclear reactors", specially designed for military use and components therefor specially designed or 'modified' for military use;	g. Nuclear power generating equipment or propulsion equipment, not specified elsewhere, specially designed for military use and components therefor specially designed or 'modified' for military use; Note ML17.g. includes "nuclear reactors".
ML17.h	h. 除歐盟一般軍用貨品清單所管制項目以外，為訊號抑制之塗佈或處理而特別設計之軍用設備與材料；	h. 未列於一般軍用貨品清單管制項目，為訊號抑制之塗佈或處理而特別設計之軍用設備與材料；	h. Equipment and material, coated or treated for signature suppression, specially designed for military use, other than those specified elsewhere in the EU Common Military List;	h. Equipment and material, coated or treated for signature suppression, specially designed for military use, not specified elsewhere in the EU Common Military List;
ML17.i	i. 為軍用｀核子反應器´而特別設計之模擬器；	i. 為軍用〝核子反應器〞而特別設計之模擬器；	i. Simulators specially designed for military "nuclear reactors";	i. Simulators specially designed for military "nuclear reactors";
ML17.m	m. 除歐盟一般軍用貨品清單以外，為軍用而特別設計之渡輪、橋樑及浮箱；	m. 未列於一般軍用貨品清單管制項目，為軍用而特別設計之渡輪、橋樑及浮箱；	m. Ferries, other than those specified elsewhere in the EU Common Military List, bridges	m. Ferries, not specified elsewhere in the EU Common Military List, bridges and pontoons, specially designed for military use;

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			and pontoons, specially designed for military use;	
ML17.p	p. 除歐盟一般軍用貨品清單以外其他｀燃料電池´，其為軍事用途特別設計或改裝者。	p. 未列於一般軍用貨品清單管制項目，為軍事用途特別設計或改裝者之｀燃料電池´。	p. "Fuel cells" other than those specified elsewhere in the EU Common Military List, specially designed or 'modified' for military use.	p. "Fuel cells", not specified elsewhere in the EU Common Military List, specially designed or 'modified' for military use.
術語定義	無	｀使用者可程式化´係指允許使用者插入、修改或更換〝程式〞之設施，不包括下列方法： a. 以佈線或互連改變實體；或 b. 功能控制設定，包括輸入參數。	-	'User-accessible programmability' refers to the facility allowing a user to insert, modify or replace "programs" by means other than: a. A physical change in wiring or interconnections; or b. The setting of function controls including entry of parameters.
	無	ML11 〝衛星導航系統〞 由地面站、衛星與接收器組成之系統，其具有由衛星接收訊號計算接收器位置之能力。包括全球衛星導航系統(GNSS)與區域衛星導航系統(RNSS)。	-	ML11 "Satellite navigation system" A system consisting of ground stations, a constellation of satellites, and receivers, that enables receiver locations to be calculated on the basis of signals received from the satellites. It includes Global Navigation Satellite Systems (GNSS) and Regional Navigation Satellite Systems (RNSS).